

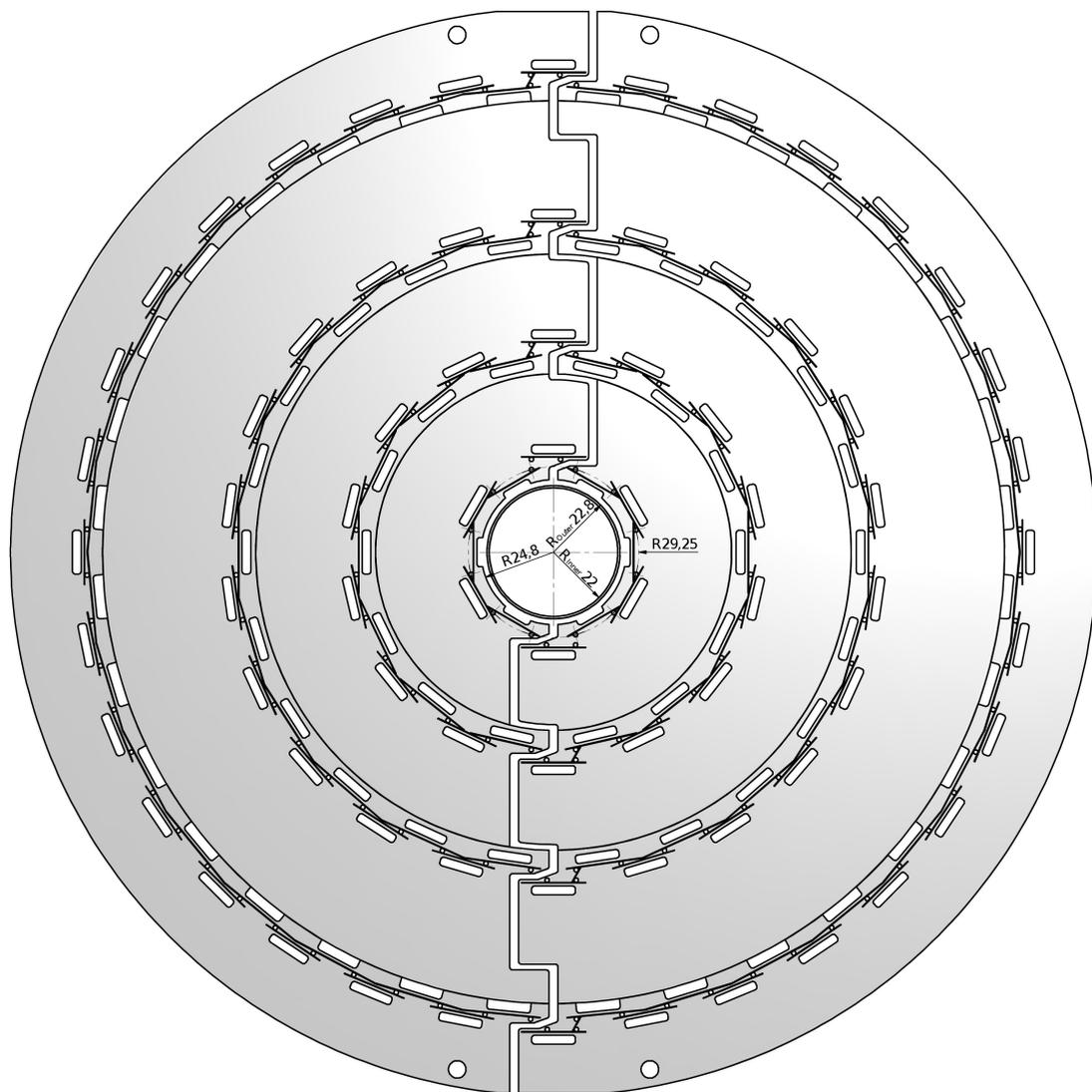


CMS Pixel Detector Upgrade



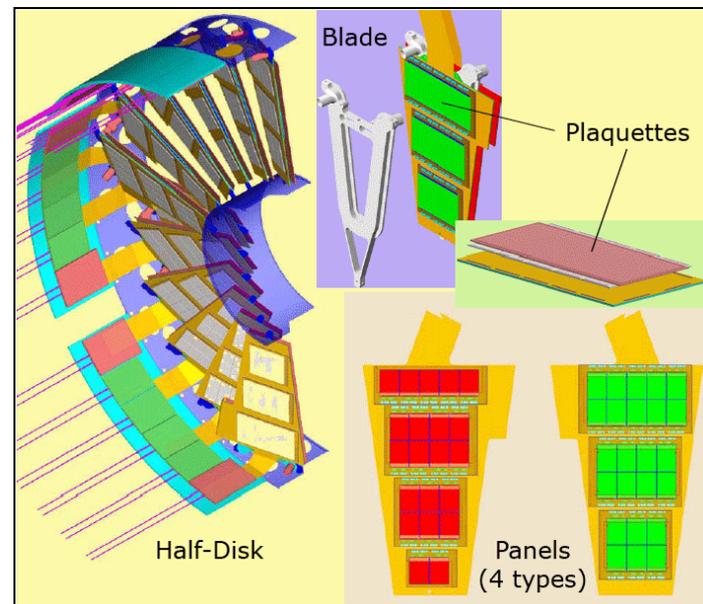
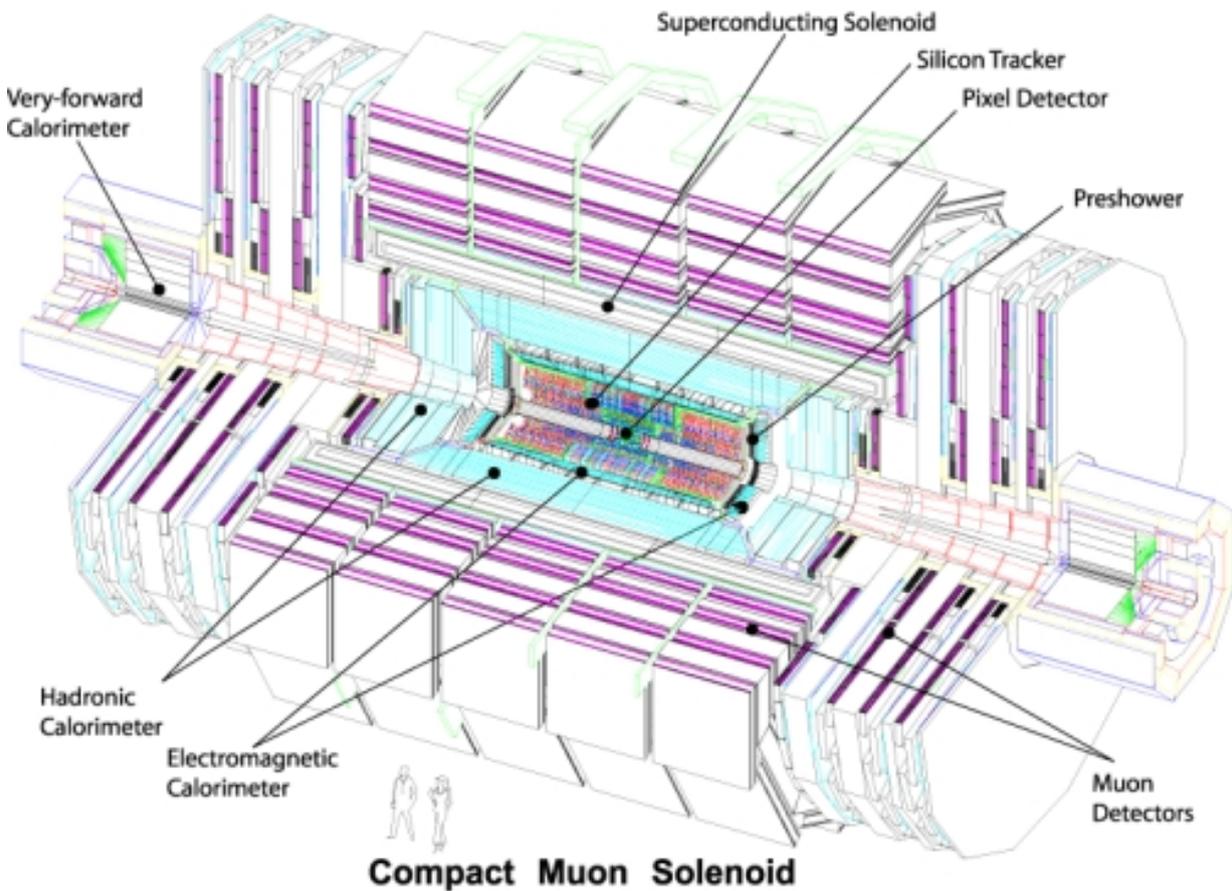
Daniel Pitzl, DESY

DESY Instrumentation Seminar 16.9.2011

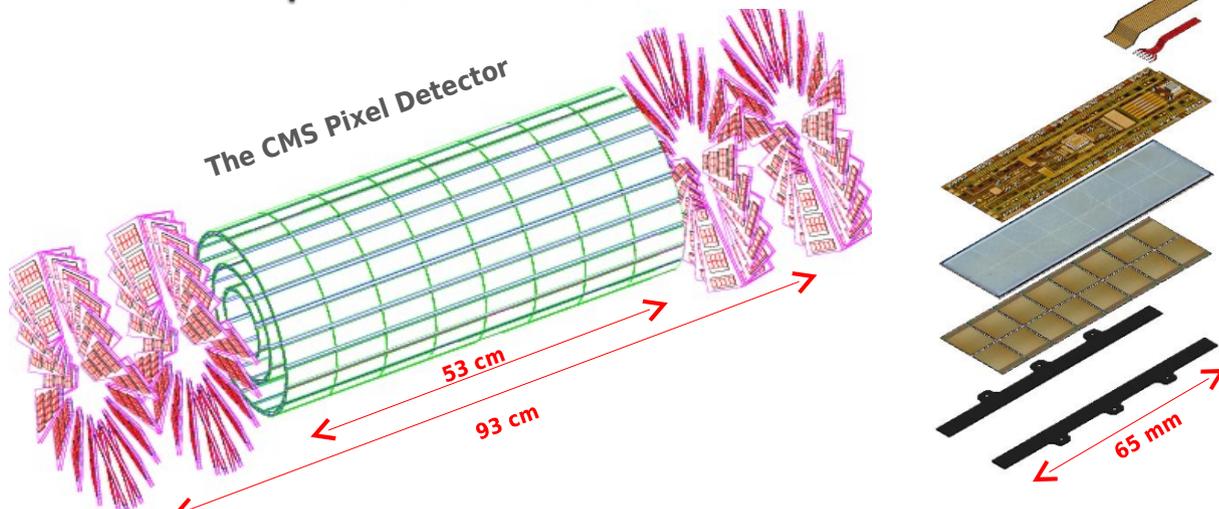


- Present pixel detector
- 4-layer upgrade
- Read out chip modifications
- Module assembly, testing, and calibration
- preparations in Hamburg

CMS and its pixel detectors



Panels of the Forward Pixel Detector

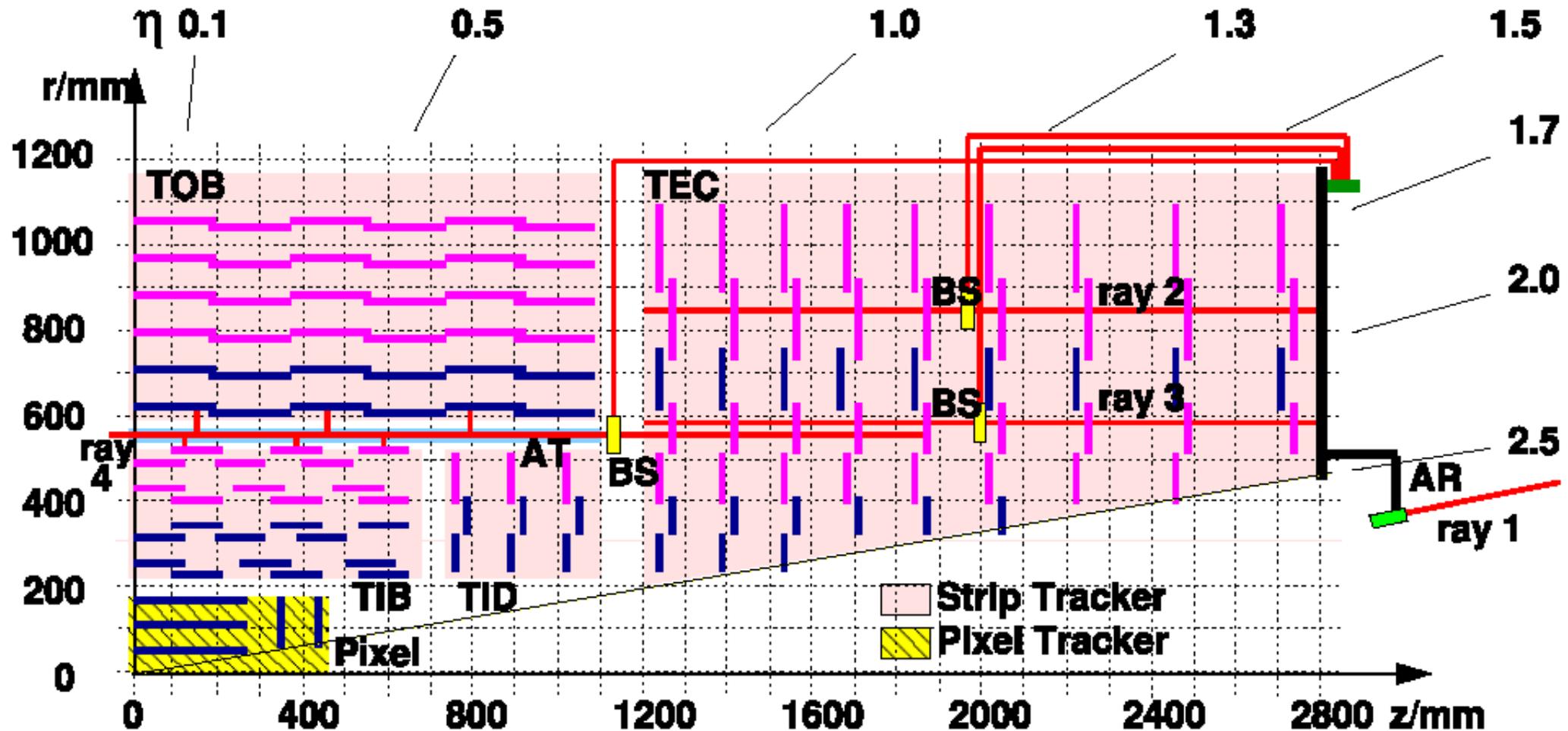


Forward Pixel Detector has 2 disks on each side at $z = 34.5$ cm and 46.5 cm. FPix has 672 modules.

Barrel Pixel Detector has 3 layers at $R = 4.4$ cm, 7.3 cm, and 10.2 cm. BPix has 768 modules.

Total of $\sim 15,840$ readout chips, 66M pixels.

CMS Si Tracker

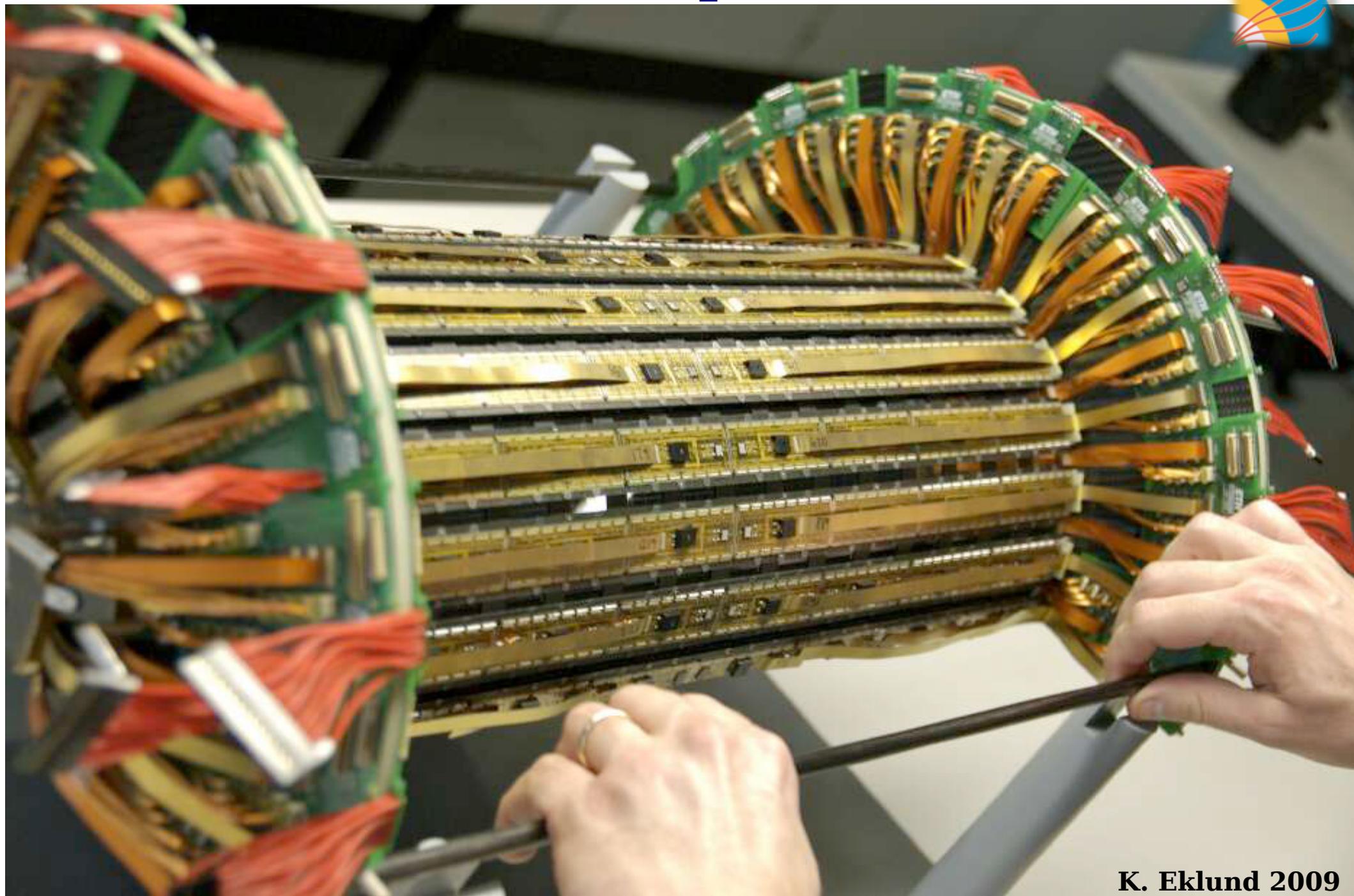


CMS at present: 3 barrel pixel layers



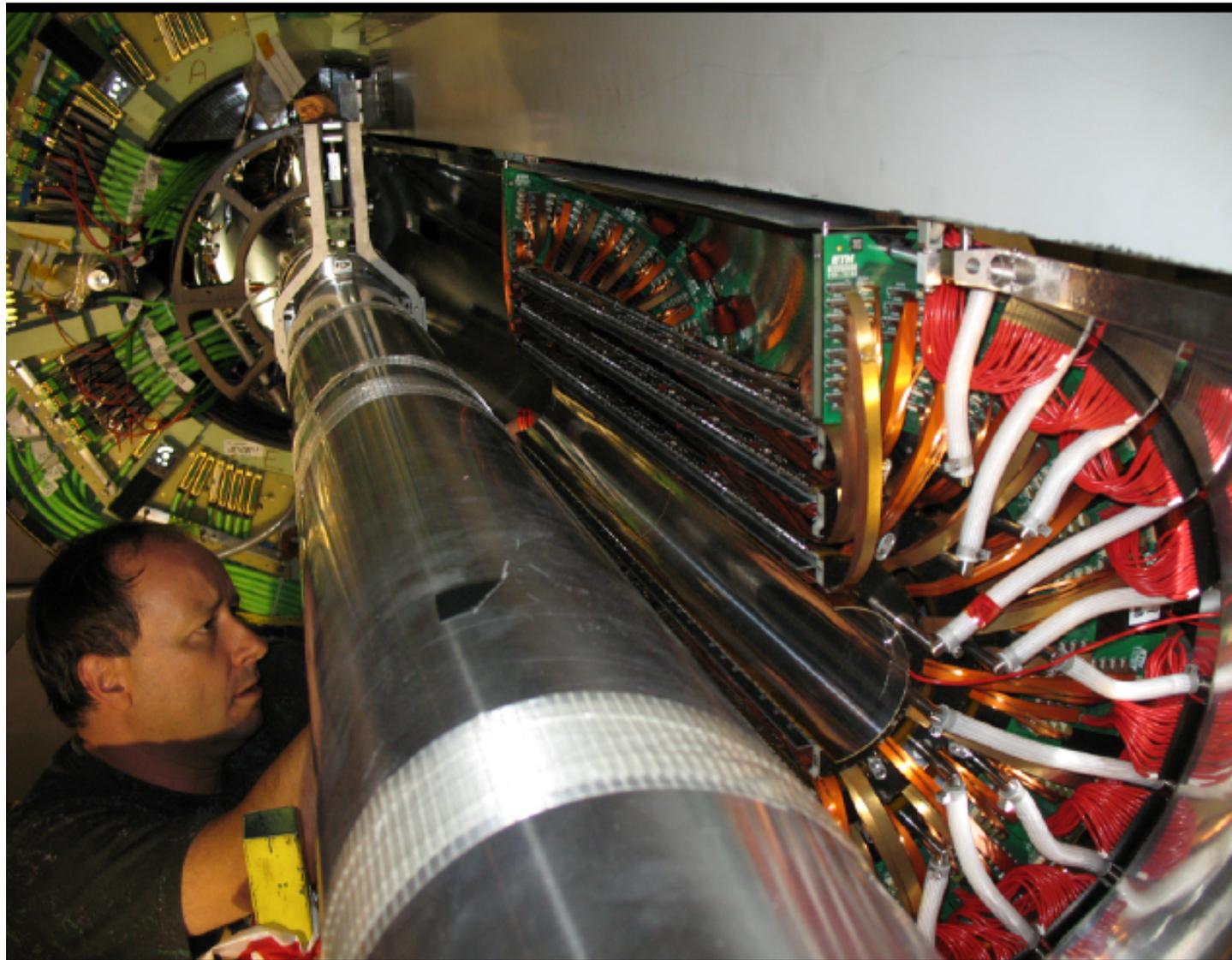
- Developed and built at PSI, CH, 1994 - 2008.
- Active length 52 cm.
- 3 layers:
 - $\langle R \rangle = 4.4, 7.3, 10.2$ cm
- 768 modules
- 12'000 chips
- 51M pixels
- 1.5 kW
- 5.2 kg

Present barrel pixel detector



K. Eklund 2009

Barrel Pixel insertion 2008



- The CMS pixel detector is accessible and removable during extended Christmas maintenance.
- Removal required for beam pipe bake out (vacuum conditioning).
- There is space for a 4th barrel layer.

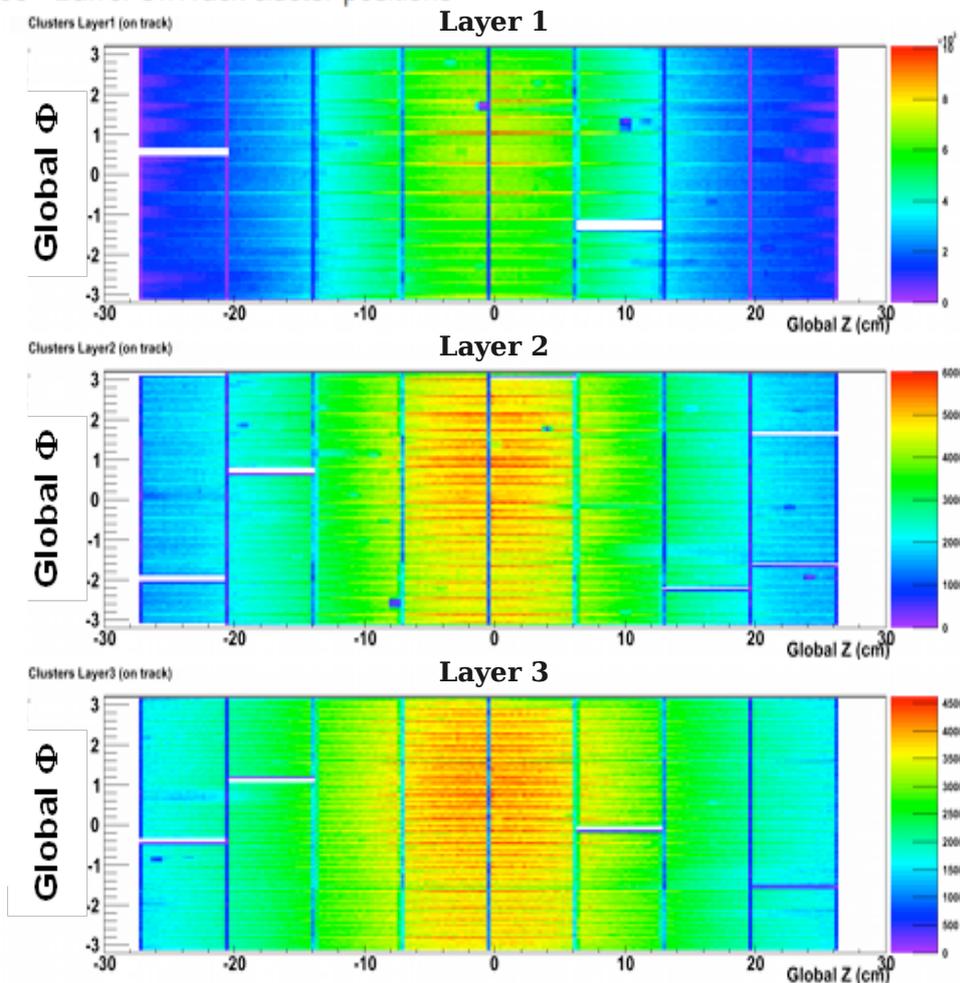
Conical beam pipe: smaller at the IP.

Pixel operation in 2010

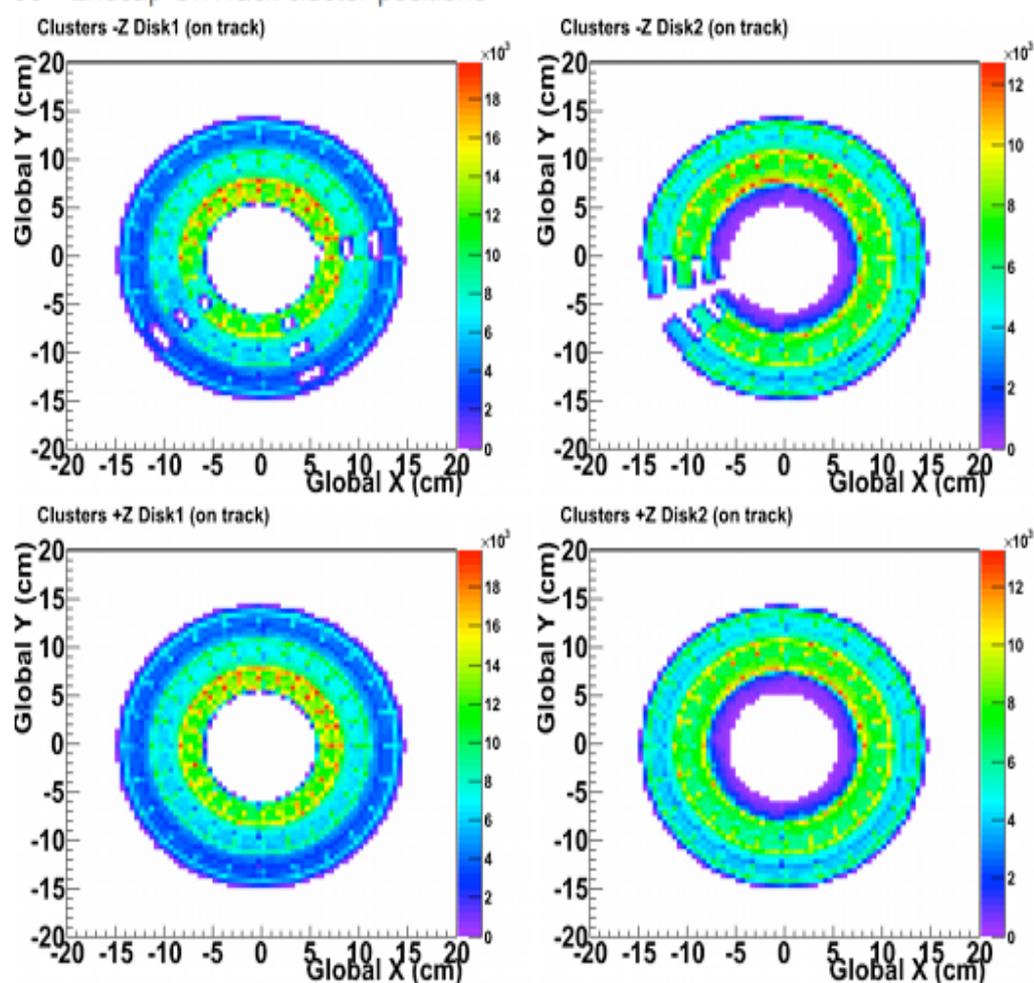


- 98.7% alive barrel modules.
- 96.4% alive forward modules.

05 - Barrel OnTrack cluster positions

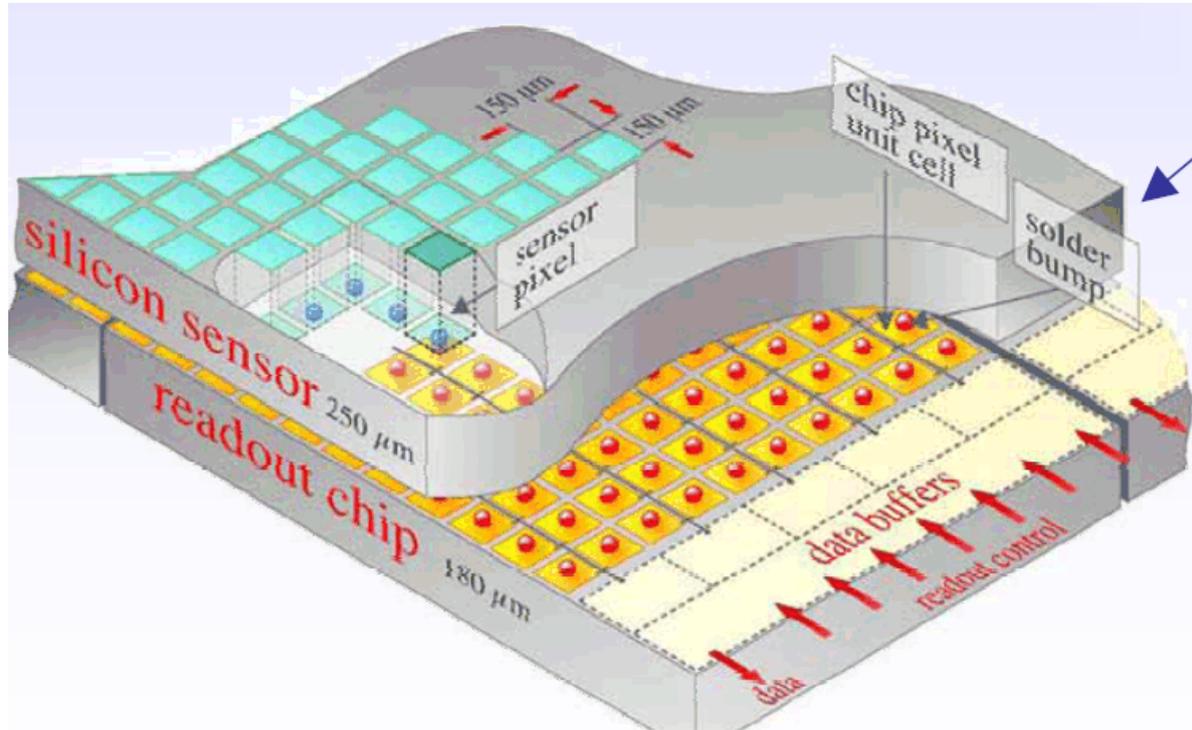


06 - Endcap OnTrack cluster positions



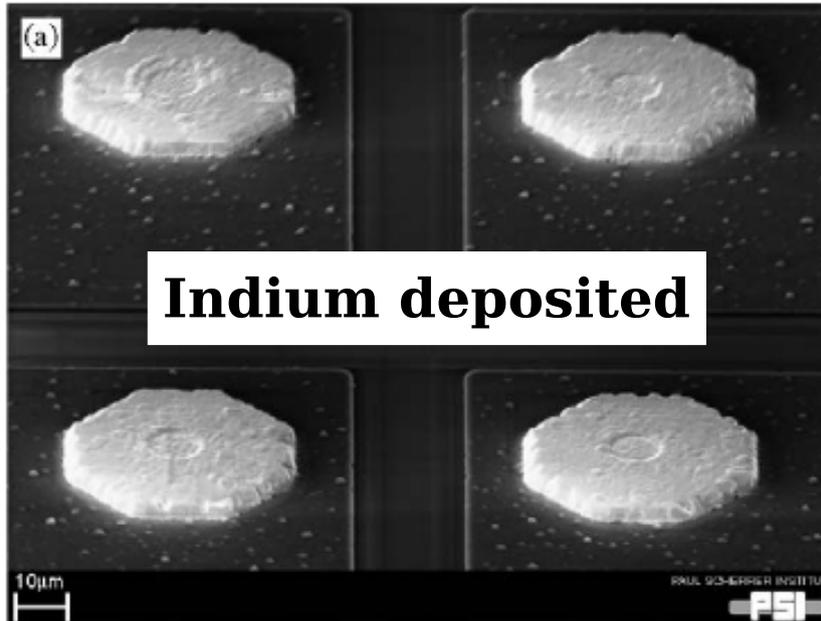
status Aug 2010

Hybrid pixel detectors

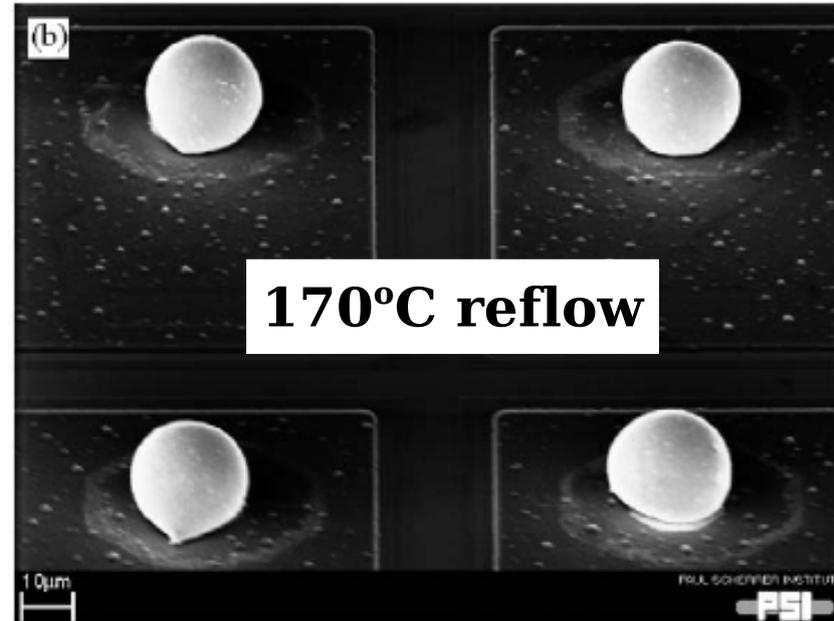


Silicon sensors with $100 \times 150 \mu\text{m}^2$ pixels, bump bonded to CMOS readout chips.

**Requires special bump bond technology.
Cost driver: 2c/bump.**



Indium deposited



170°C reflow

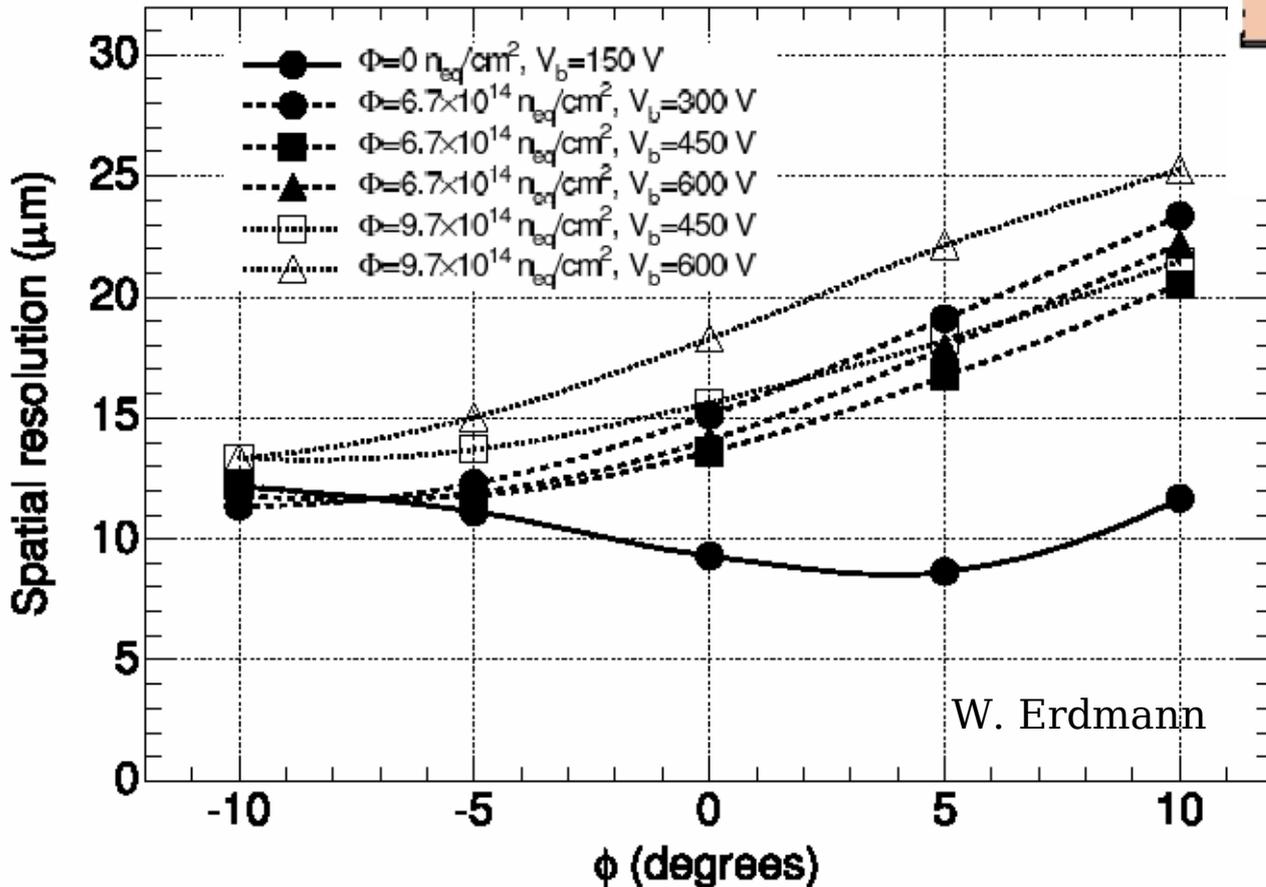
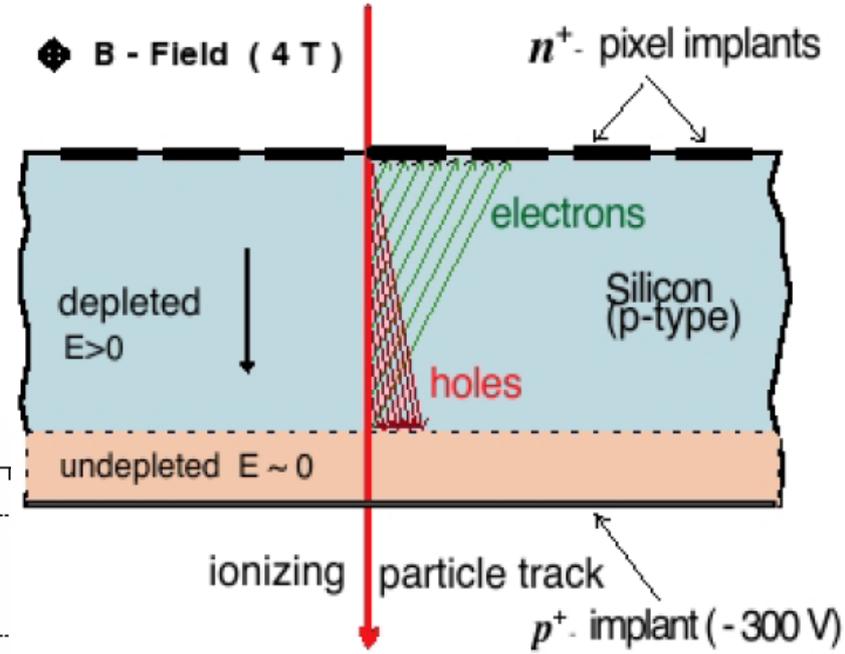
CMS Pixel hit resolution

Drift in crossed E and B fields:

Lorentz angle ($\tan \alpha_L = \mu B$) is

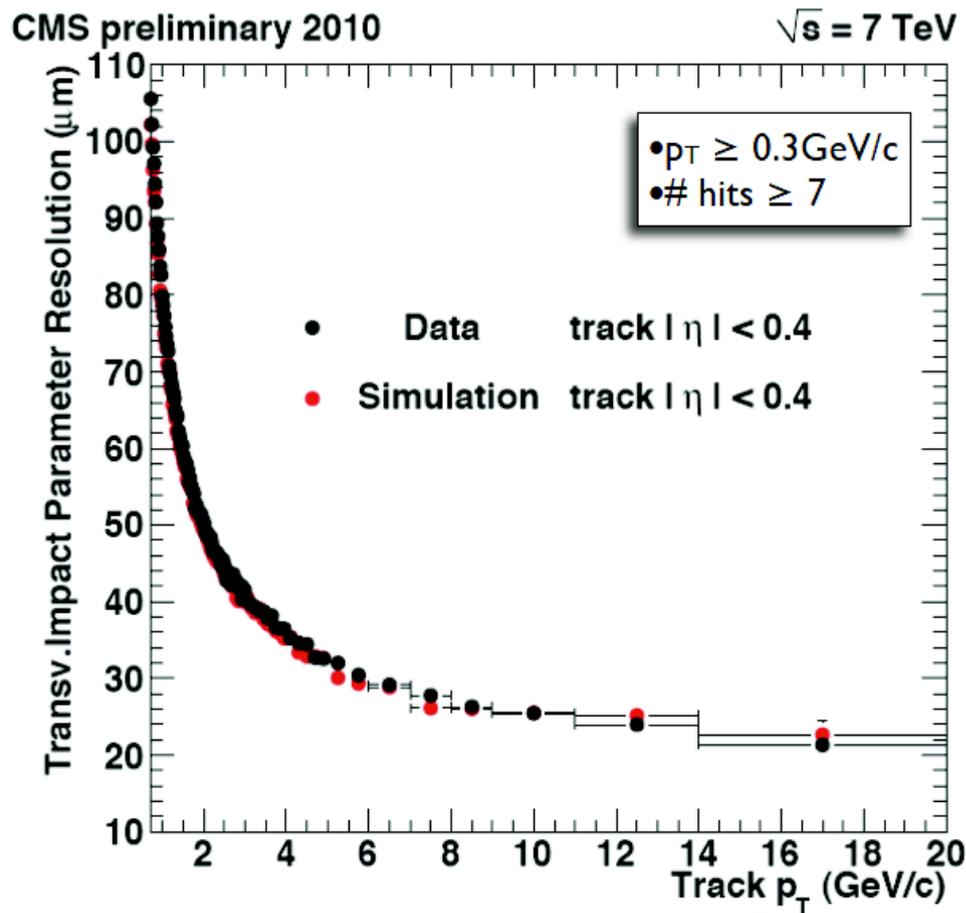
$\sim 28^\circ$ for e in pure Si at 3.8 T.

Leads to beneficial charge sharing.

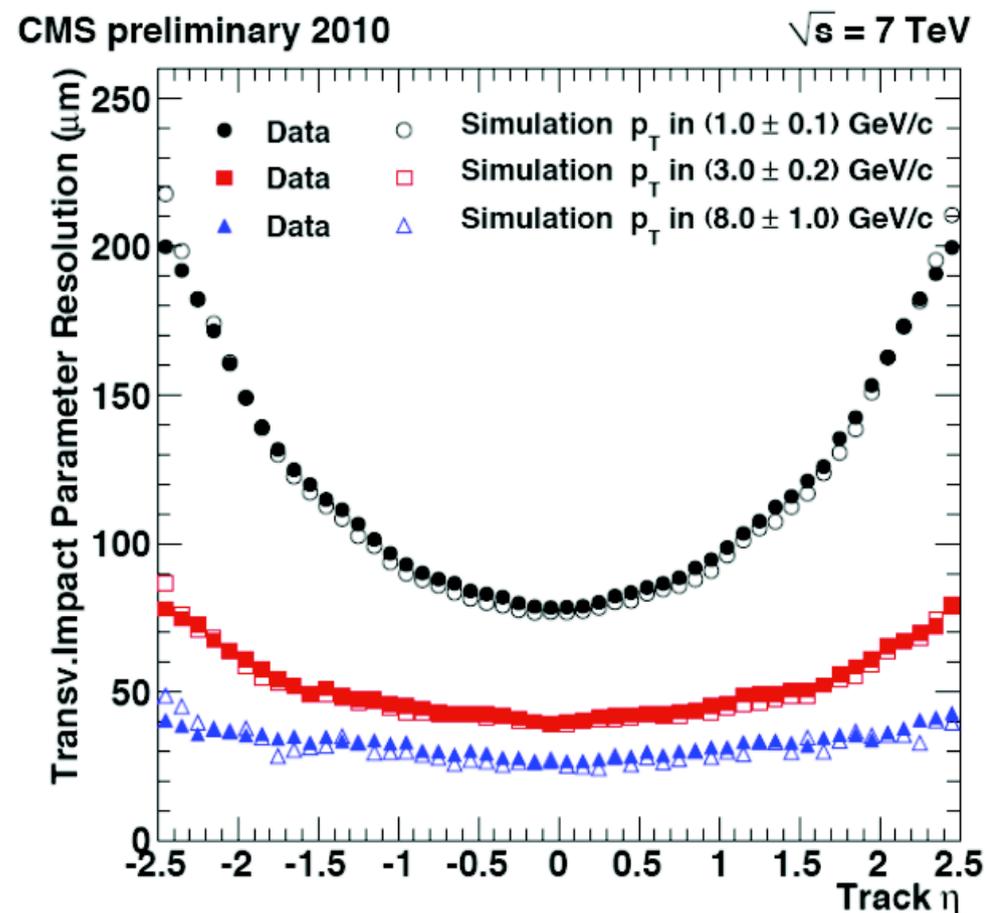


a hit resolution of 12 μm has been achieved in 2010 collision data.

CMS track impact parameter resolution



**Reach 20 μm
at high momentum.
Ultimately expect 12 μm .**



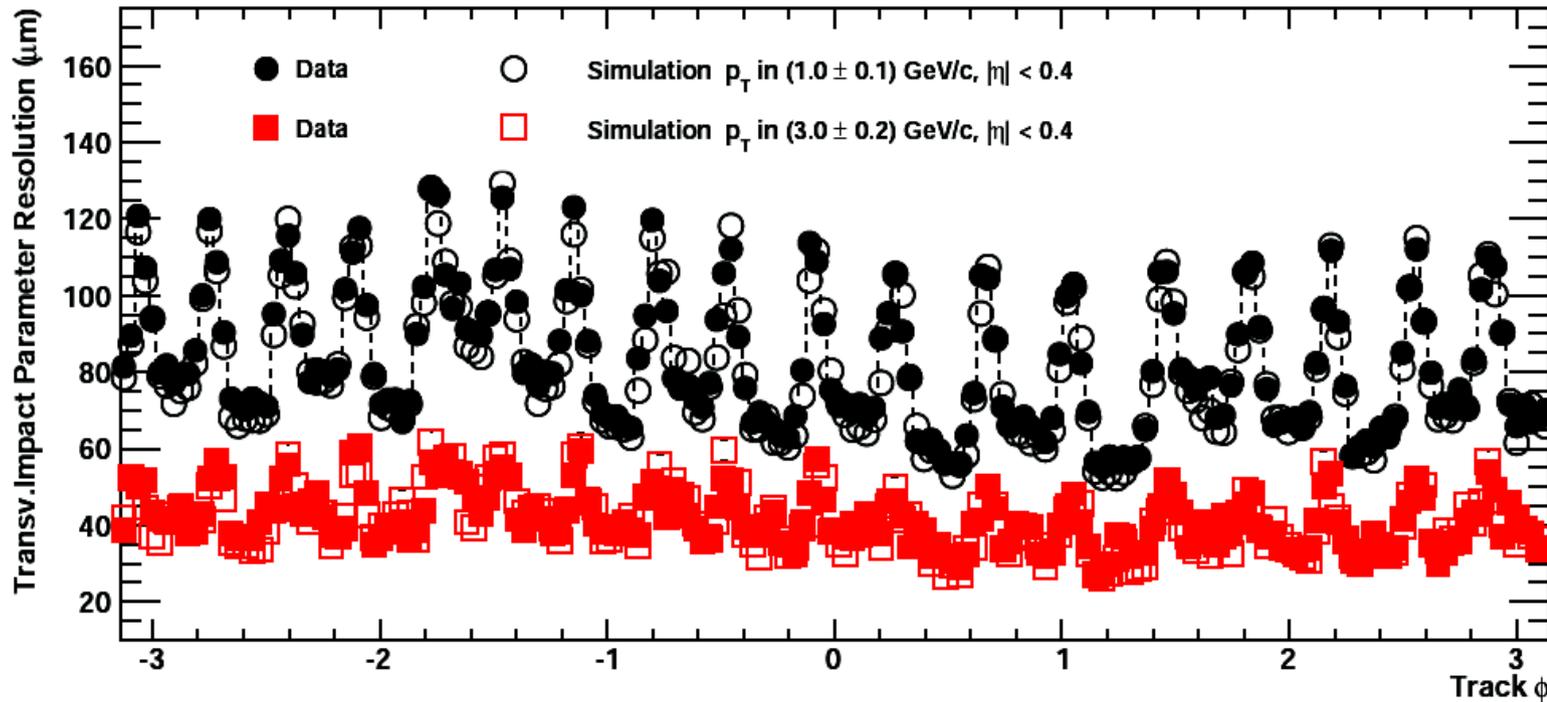
**Limited by multiple
scattering at low momenta
and/or high rapidity.**

CMS impact parameter resolution



CMS preliminary 2010

$\sqrt{s} = 7 \text{ TeV}$

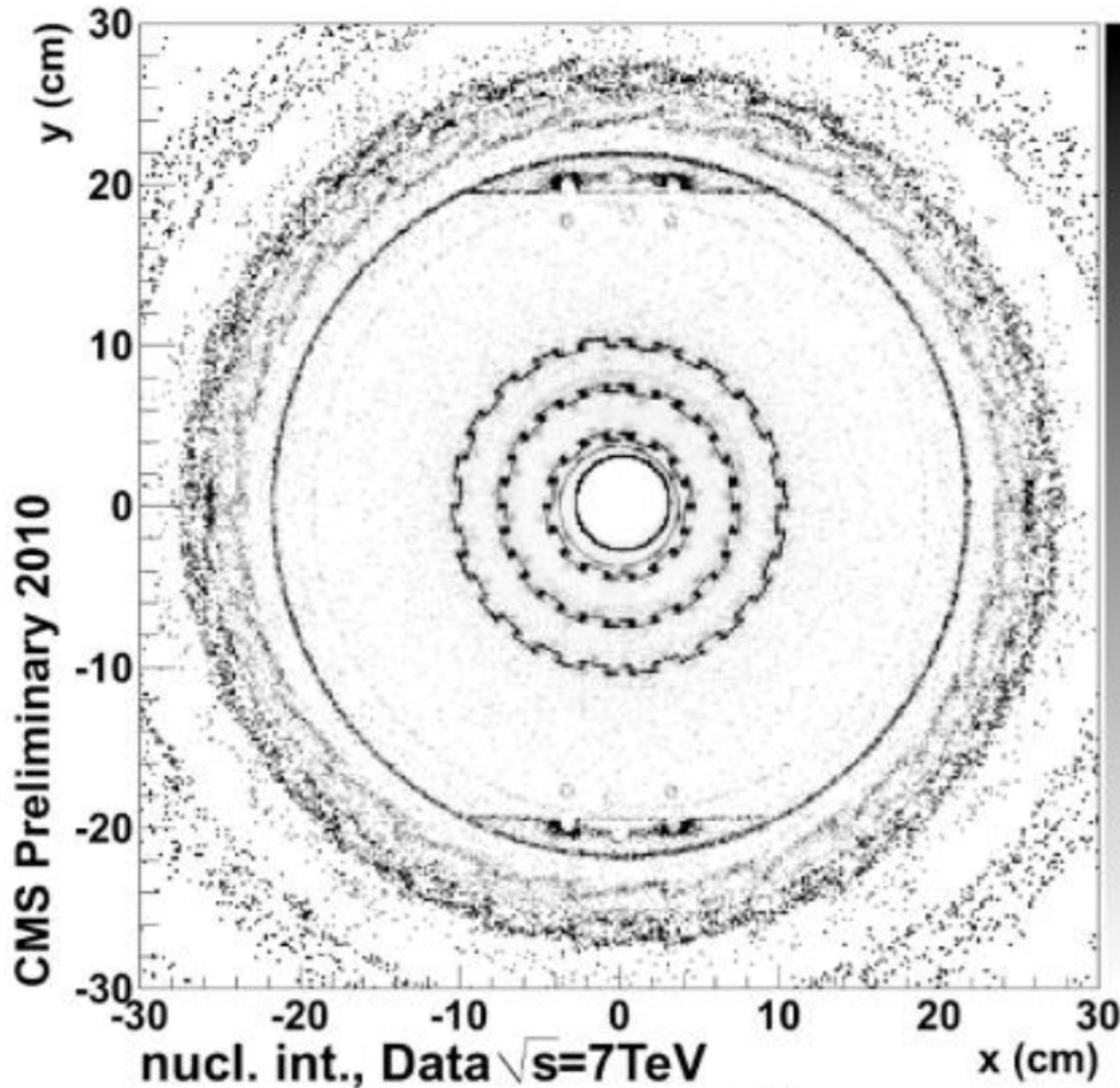


1 GeV

3 GeV

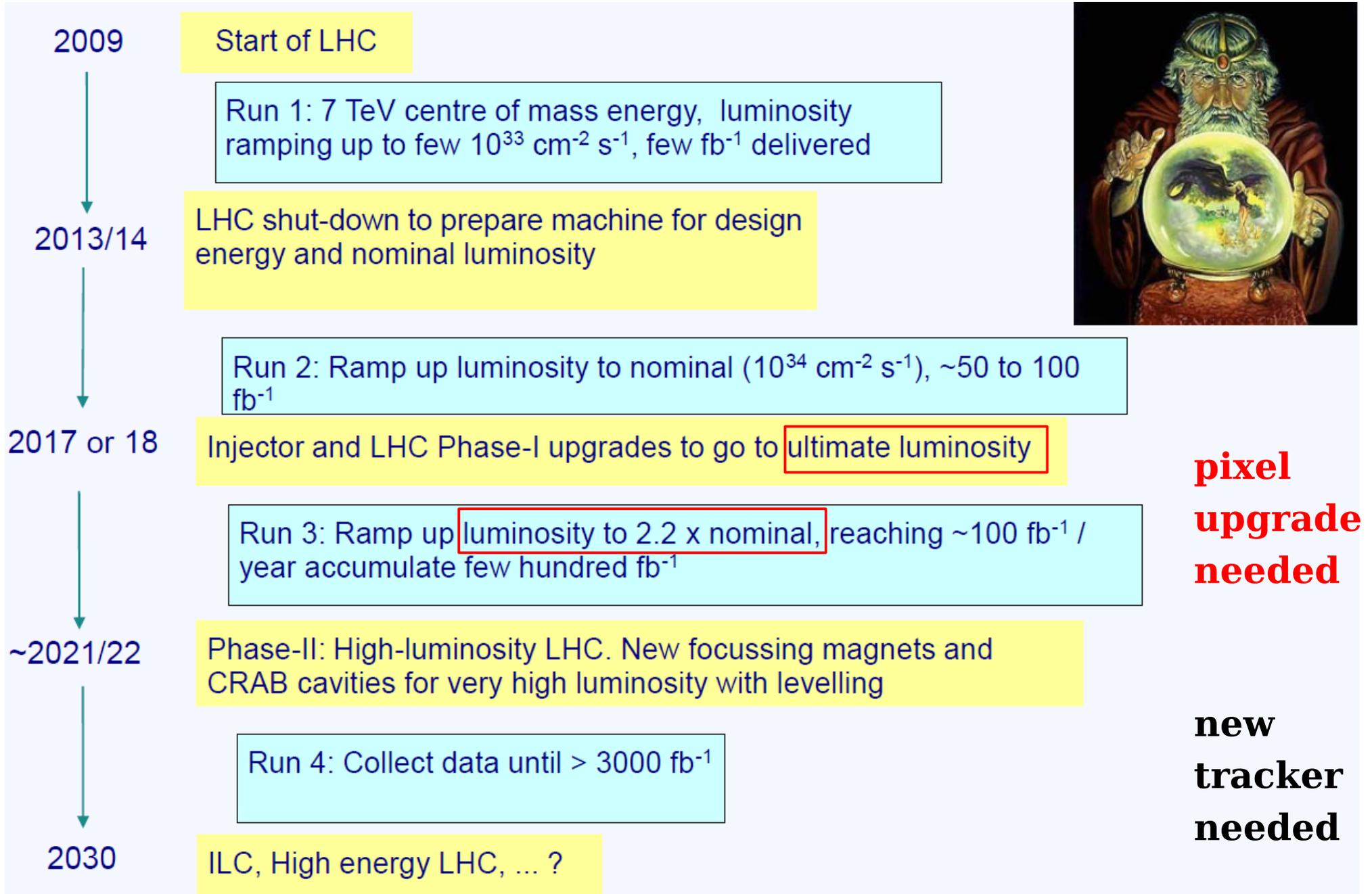
- 18-fold ϕ structure due to pixel cooling pipes visible at low p_T .
- Well described by the detector simulation.

Nuclear imaging

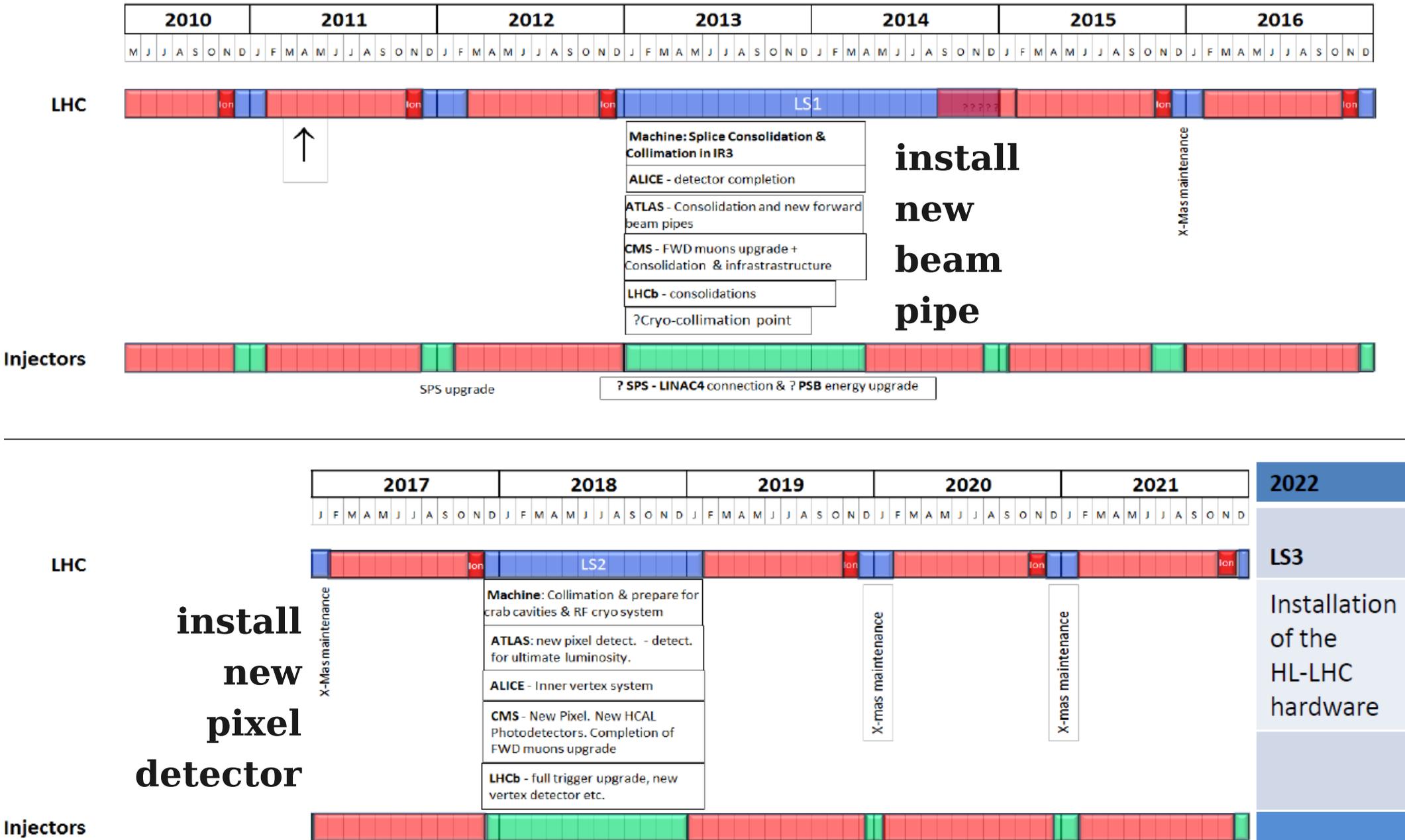


- Reconstructed nuclear interaction vertices.
 - Barrel pixel region.
- CMS tracker is shifted by ~ 3 mm relative to the machine beam pipe.
 - Upgrade: center pixel around pipe!
- Pixel modules, cooling pipes and support rails visible.
 - Upgrade: reduce the material budget!

LHC plan (S. Bertolucci PLHC 2011)



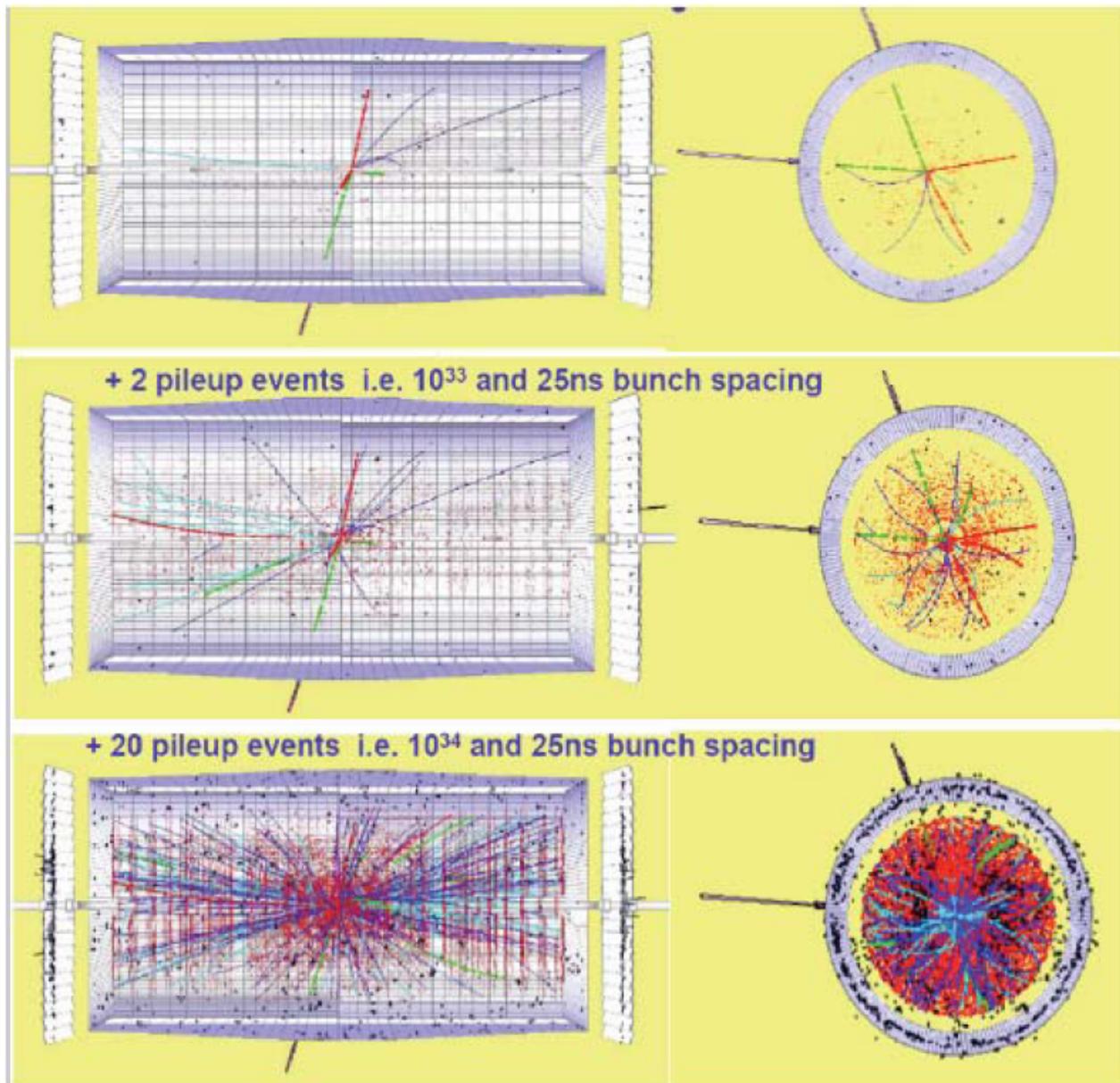
LHC 10 year plan as of June 2011



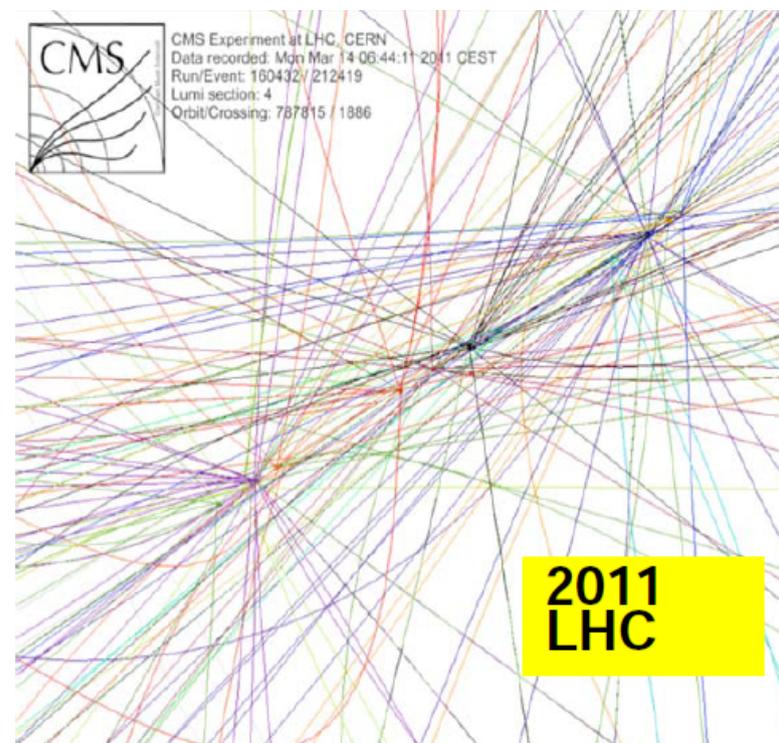
Event pile-up at high luminosity



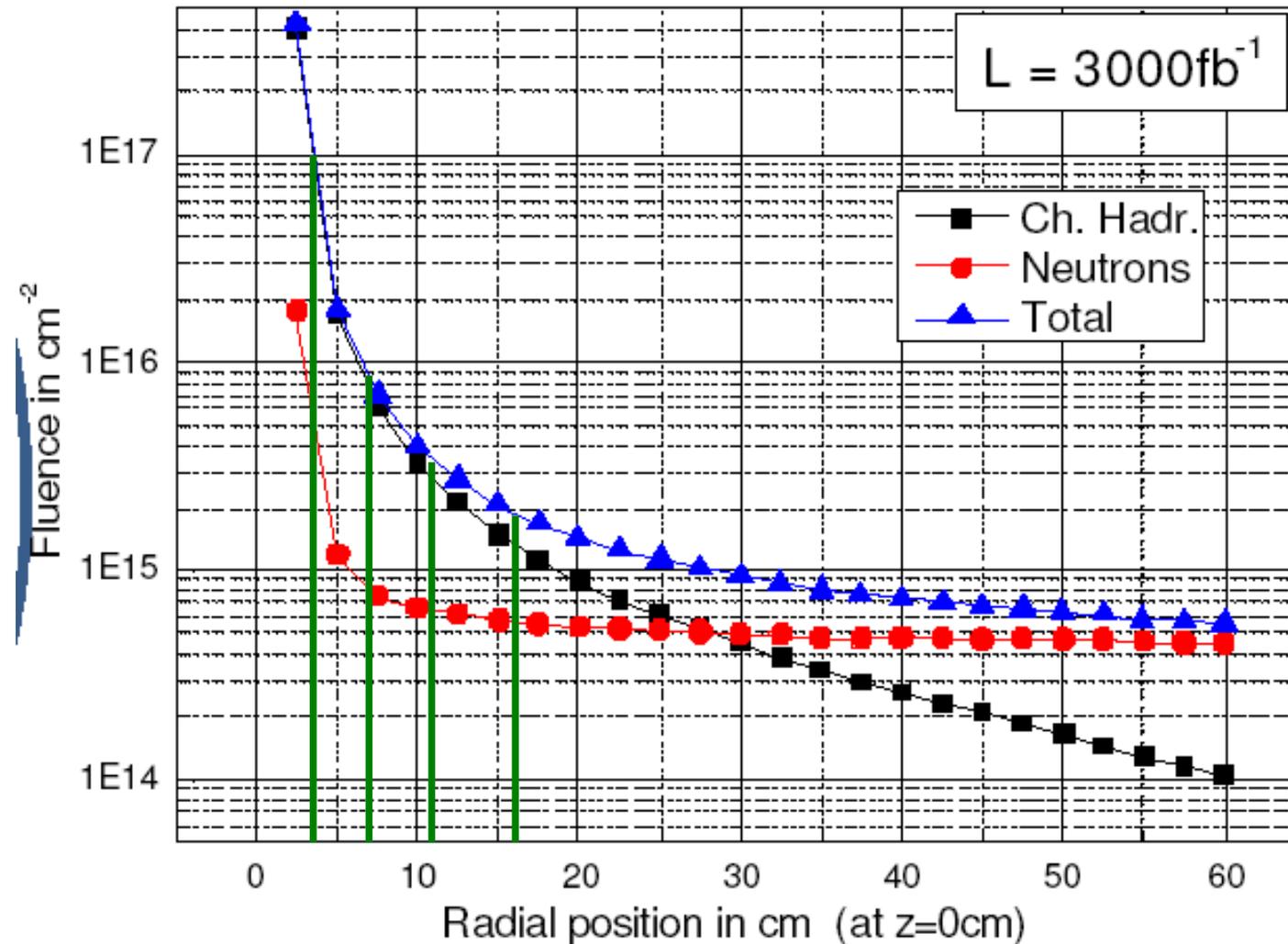
Simulation



**Data 2011:
7 pile-up events
at $2 \cdot 10^{33}$ and 50 ns
bunch spacing**



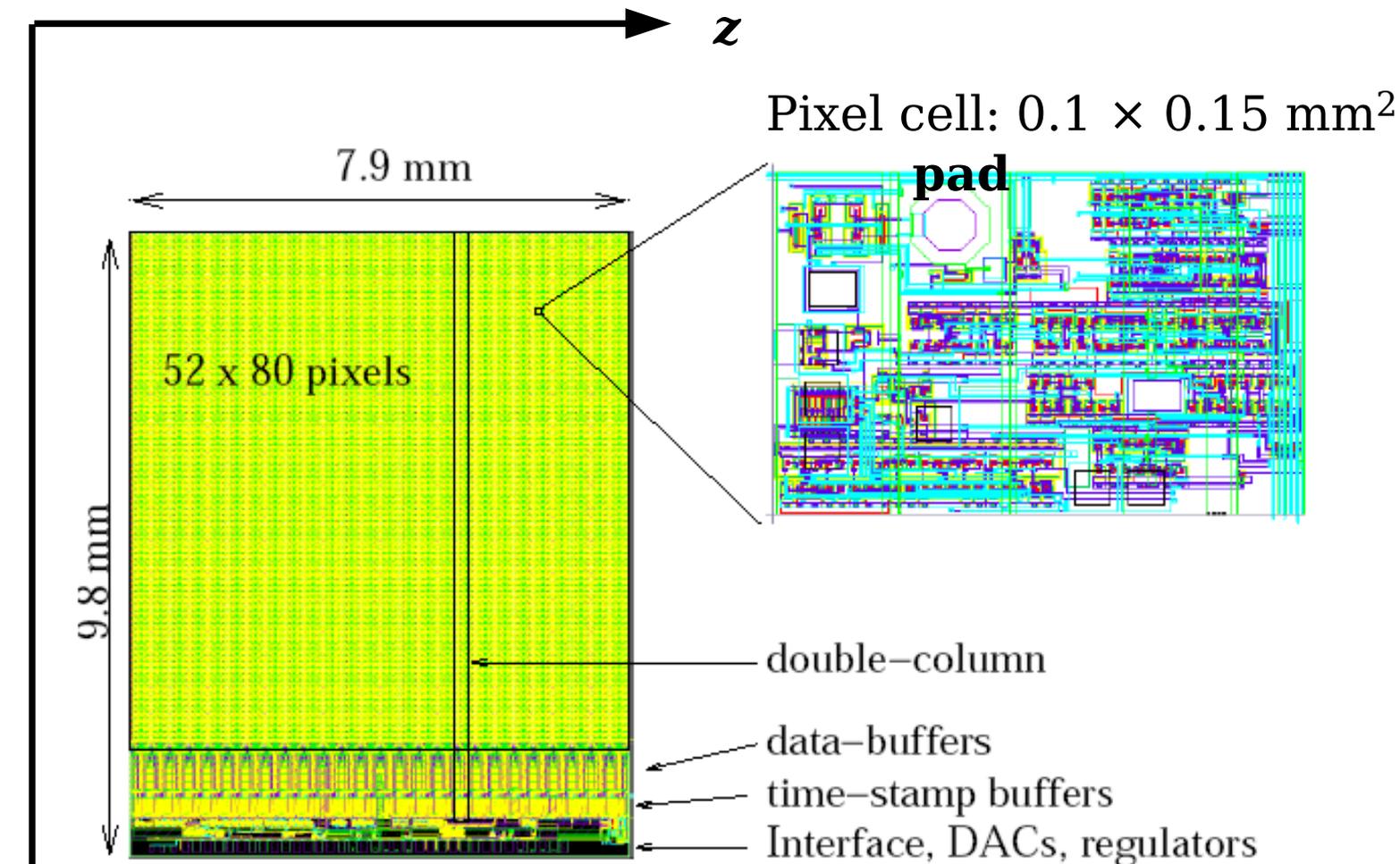
Particle fluence



- $3000 \text{fb}^{-1} = 20 \text{ years}$.
- This decade: 300fb^{-1} .
- Pixel region: dominated by pions.
- Layer at $R = 3 \text{ cm}$:
 - flux 500 MHz/cm^2 ,
 - may need replacement every year (200fb^{-1}).

F. Hartmann, sensor testing, CMS Tracker Week Sep 2009
<http://indico.cern.ch/conferenceDisplay.py?confId=47301>

CMS Pixel Chip



PSI46 V2.4

0.25 μm CMOS IBM process

radiation hard design operational after 130 kGy γ irradiation

1.3 M transistors

Double column readout

Sources of inefficiency:

now → **upgrade**

Pixel busy:

pixel insensitive until hit transferred to data buffer (column drain mechanism)

2BC → 1BC

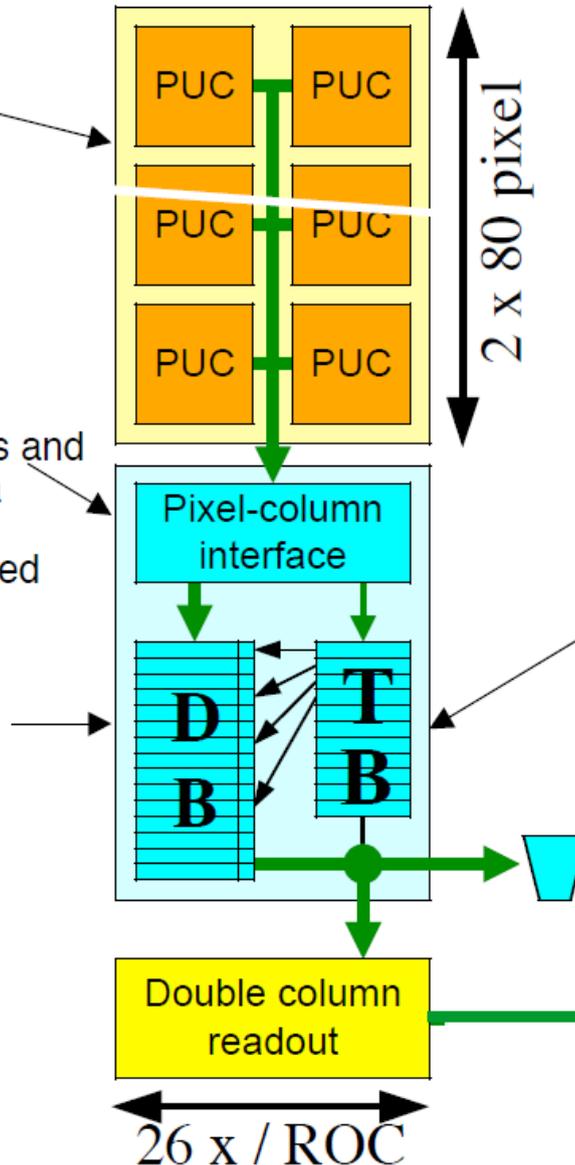
Double column busy:

Column drain finds hit pixels and transfers hits from pixel to data buffer. Maximum 3 pending column drains requests accepted

3 → 8 pending

Data Buffer full:

size: **80** (32)



Double column:

2×80 pixel, 0.024 cm²

L1 trigger:

after 3.2 us (130 BC).

at 500 MHz/cm²:

**0.3 tracks / DC / BC,
40 tracks in buffers.**

Timestamp Buffer full:

size: **24** (12)

Readout and double column reset:
Wait for token, reset after r/o

**40 MHz analog readout
→ 160 MHz digital**

Data loss mechanisms

Present PSI46 readout chip simulated **at LHC design luminosity**
Pythia physics generator + detector and chip simulation:

Pixel busy:

0.04% / 0.08% / 0.21%

pixel insensitiv until hit transferred to data buffer (column drain mechanism)

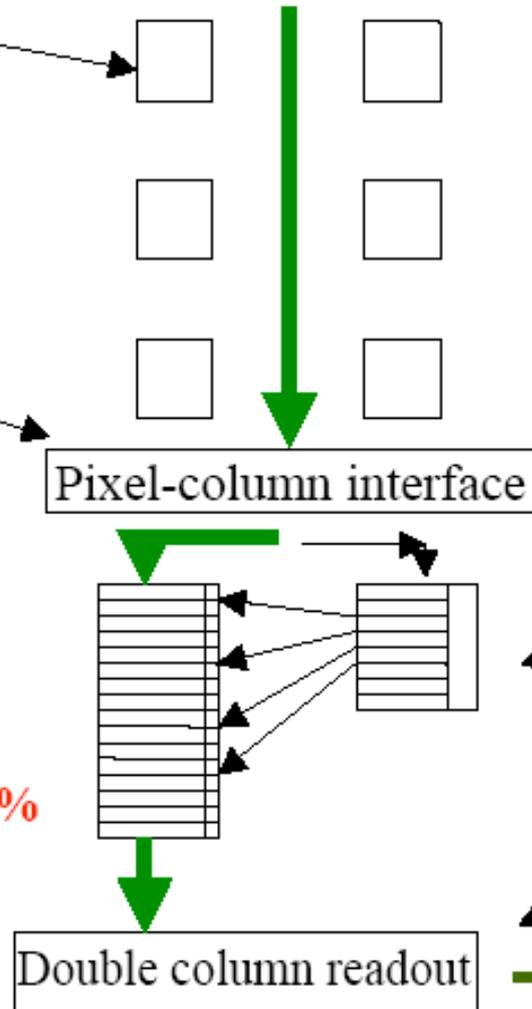
Double column busy:

0.004% / 0.02% / 0.25%

Column drain transfers hits from pixel to data buffer. Maximum 3 pending column drains requests accepted

Data Buffer full:

0.07% / 0.08% / 0.17%



- 1xLHC: $10^{34} \text{cm}^{-2} \text{s}^{-1}$
- 11 cm / 7 cm / 4 cm layer
- total data loss @ 100kHz L1A:
 - 0.8%
 - 1.2%
 - 3.8%

Timestamp Buffer full:

0 / 0.001% / 0.17%

Readout and double column reset:

0.7% / 1% / 3.0%

for 100kHz L1 trigger rate

Data loss mechanisms

Present PSI46 readout chip simulated at **2×** LHC design luminosity

Pixel busy:

0.09% / 0.18% / 0.48%

Double column busy:

0.003% / 0.18% / 1.3%

Data Buffer full:

0.09% / 0.17% / 0.83%

total data loss @ 100kHz L1A:

1.3% @ 11cm

2.7% @ 7cm

16% @ 4cm

Pixel-column interface

Timestamp Buffer full:

0 / 0.05% / 6.8%

Readout and double column reset:

1.1% / 2.1% / 6.7%

for 100kHz L1 trigger rate

Double column readout

Data loss with extended buffering

luminosity: $2 \times 10^{34} \text{ cm}^{-2}\text{sec}^{-1}$
layer 1 @ R = 38 mm

total data loss in layer 1
at run start: **5.63%**

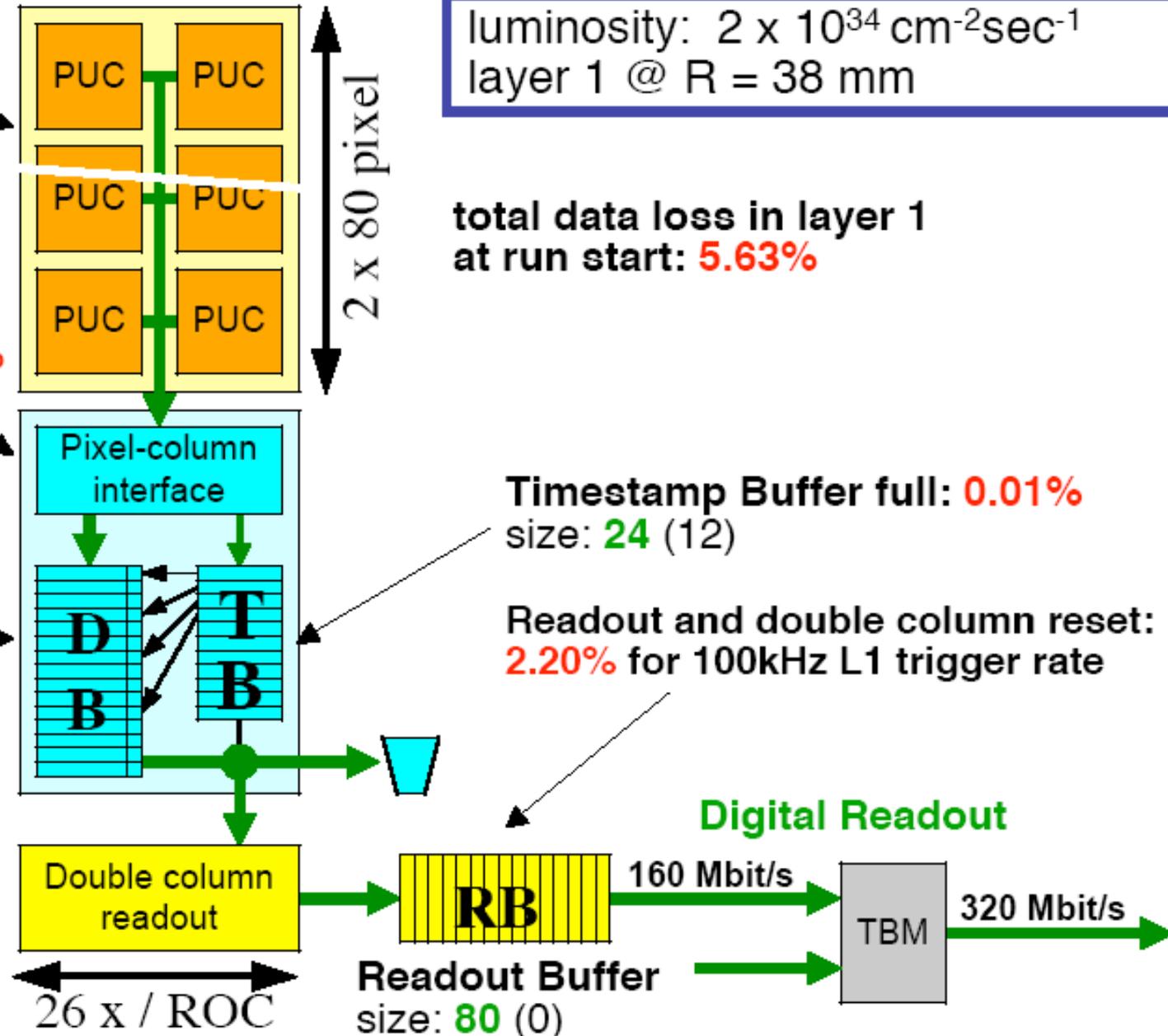
Pixel busy: 0.72%
pixel insensitive until hit transferred to data buffer (column drain mechanism)

Double column busy: 2.03%
Column drain finds hit pixels and transfers hits from pixel to data buffer. Maximum 3 pending column drains requests accepted

Data Buffer full: 0.68%
size: **80** (32)

Timestamp Buffer full: 0.01%
size: **24** (12)

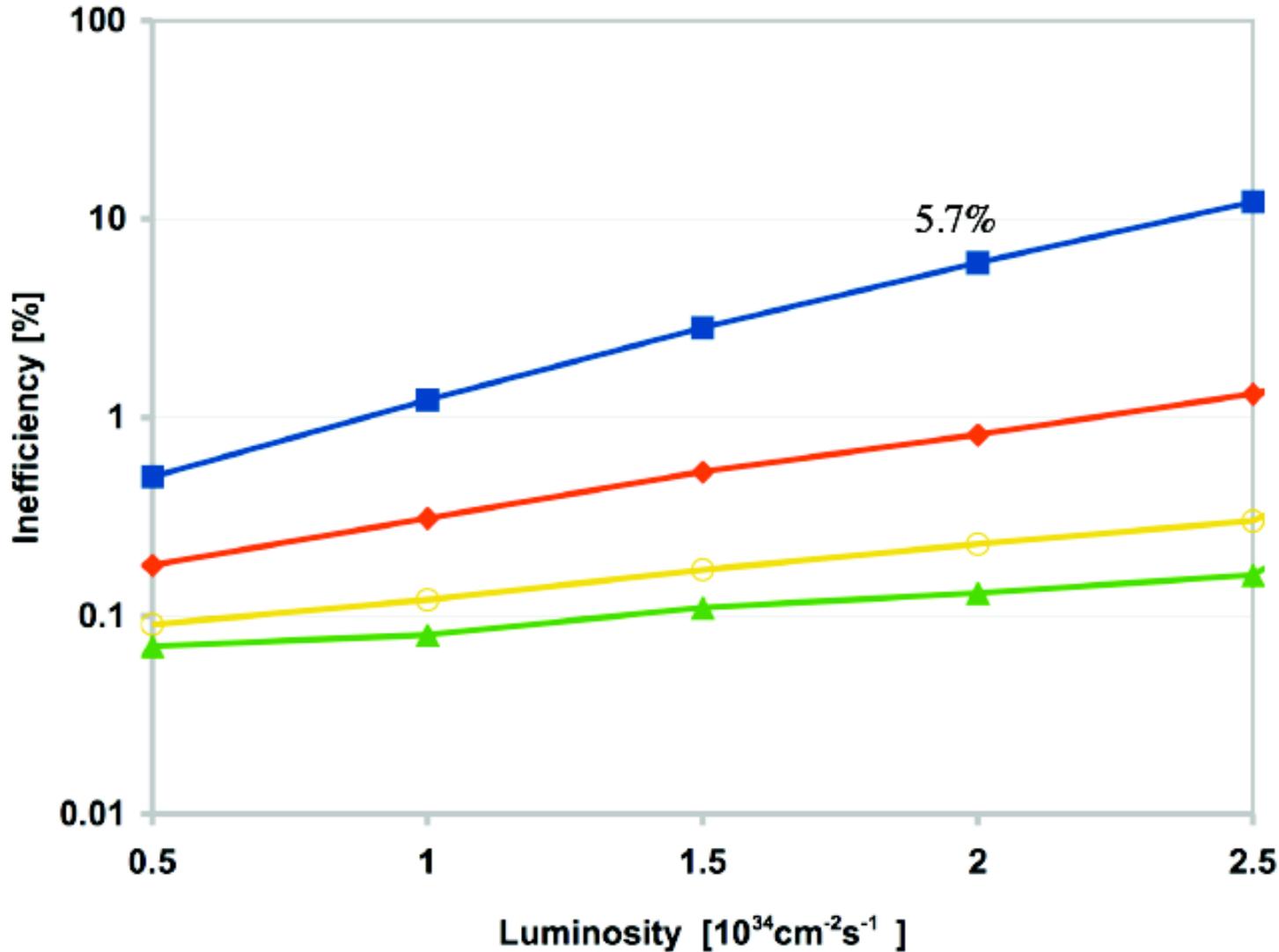
Readout and double column reset:
2.20% for 100kHz L1 trigger rate



H.C. Kaestli
Oct 2009

Data loss vs luminosity

Pixel readout chip simulation with increased buffering



Factor ~3 improvement compared to the present chip.

■ Layer 1 at 4 cm
◆ Layer 2
○ Layer 3
▲ Layer 4

Inefficiency averaged over a luminosity fill is factor 2 smaller.

Further design modifications under study: aim for 2.5% at $2 \cdot 10^{34}$

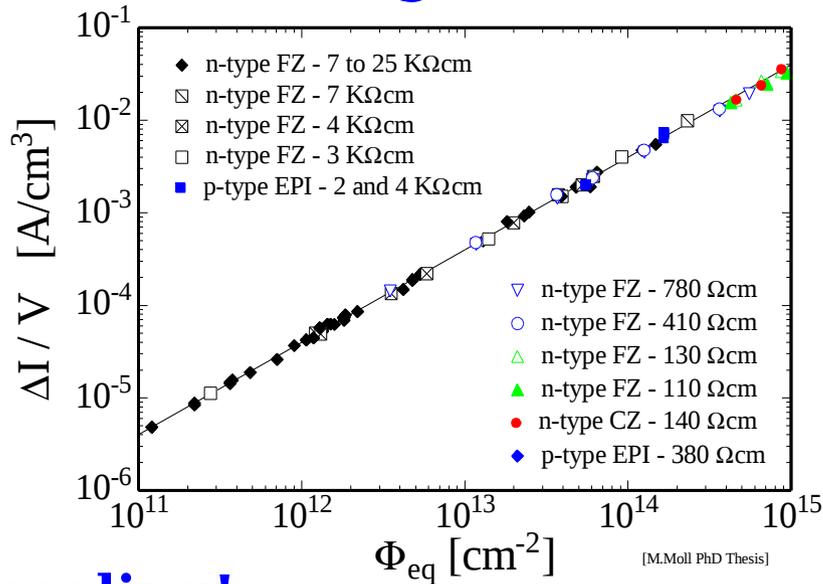
H.C. Kaestli
Oct 2009

Radiation damage in silicon

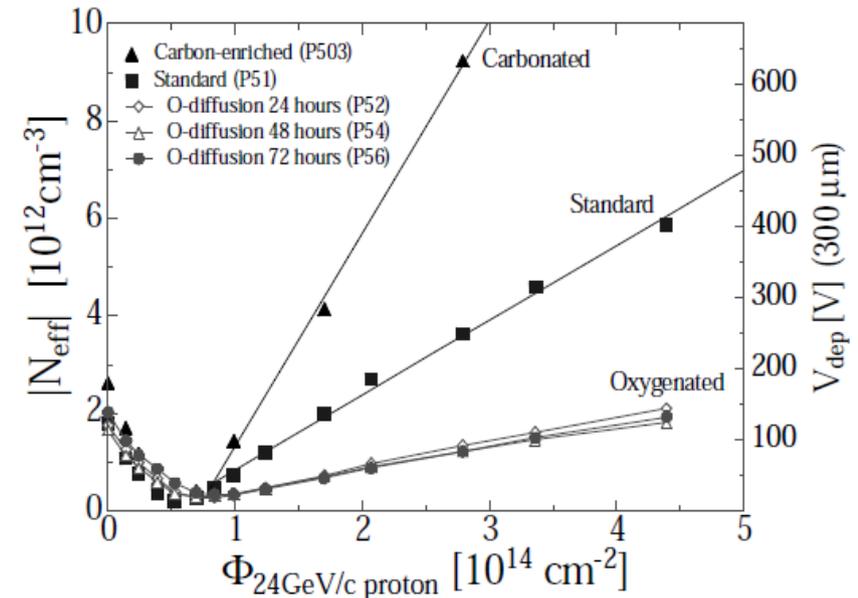
- Leakage current:
 - ▶ $I / \text{Vol} = \alpha \Phi$ (fluence Φ [particles/cm²])
 - ▶ all silicon materials (FZ, Cz, epi) have the same damage α .
 - ▶ only cooling helps to reduce leakage current (factor 2 / 8°C).
- Space charge creation ('type inversion'):
 - ▶ leads to high depletion voltage at high fluence.
 - ▶ oxygenated silicon is better (DOFZ, mCz).
 - ▶ cooling reduces activation of defects.
- Charge trapping:
 - ▶ reduces charge collection efficiency
 - ▶ collecting electrons (n-in-p or n-in-n) is better than holes (p-in-n).
 - ▶ no 'defect engineering' method known to help.
 - ▶ Charge amplification at high bias, earlier in thin sensors or 3D.

Radiation damage effects in silicon

leakage current

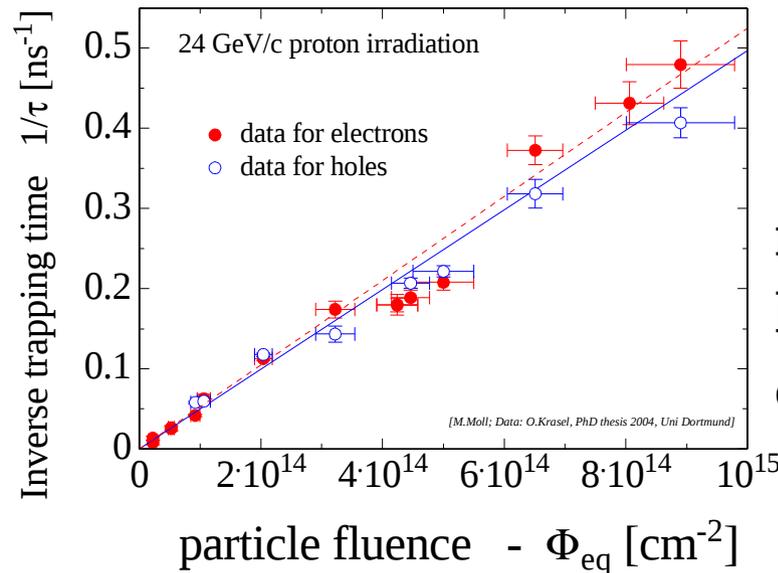


depletion voltage



cooling!
factor 1/2
every -8°C

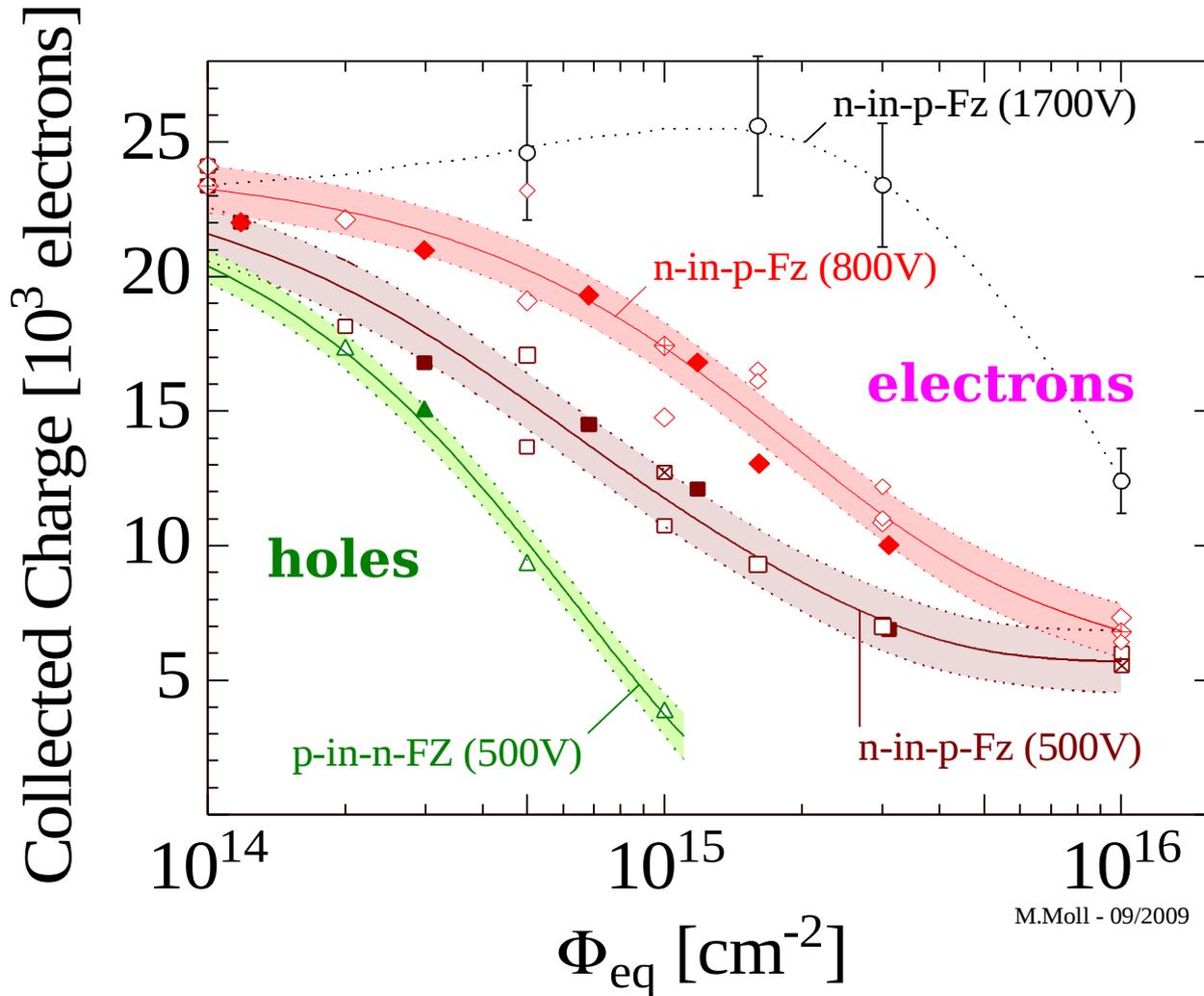
trapping



oxygenated
Si used!
Keep Si cool
to avoid
activation
of defects.

no
known
cure

Silicon charge collection vs fluence



FZ Silicon Strip Sensors

- n-in-p (FZ), 300μm, 500V, 23GeV p [1]
- n-in-p (FZ), 300μm, 500V, neutrons [1,2]
- ⊗ n-in-p (FZ), 300μm, 500V, 26MeV p [1]
- ◆ n-in-p (FZ), 300μm, 800V, 23GeV p [1]
- ◇ n-in-p (FZ), 300μm, 800V, neutrons [1,2]
- ◊ n-in-p (FZ), 300μm, 800V, 26MeV p [1]
- n-in-p (FZ), 300μm, 1700V, neutrons [2]
- ▲ p-in-n (FZ), 300μm, 500V, 23GeV p [1]
- △ p-in-n (FZ), 300μm, 500V, neutrons [1]

References:

[1] G.Casse, VERTEX 2008
(p/n-FZ, 300μm, (-30°C, 25ns)

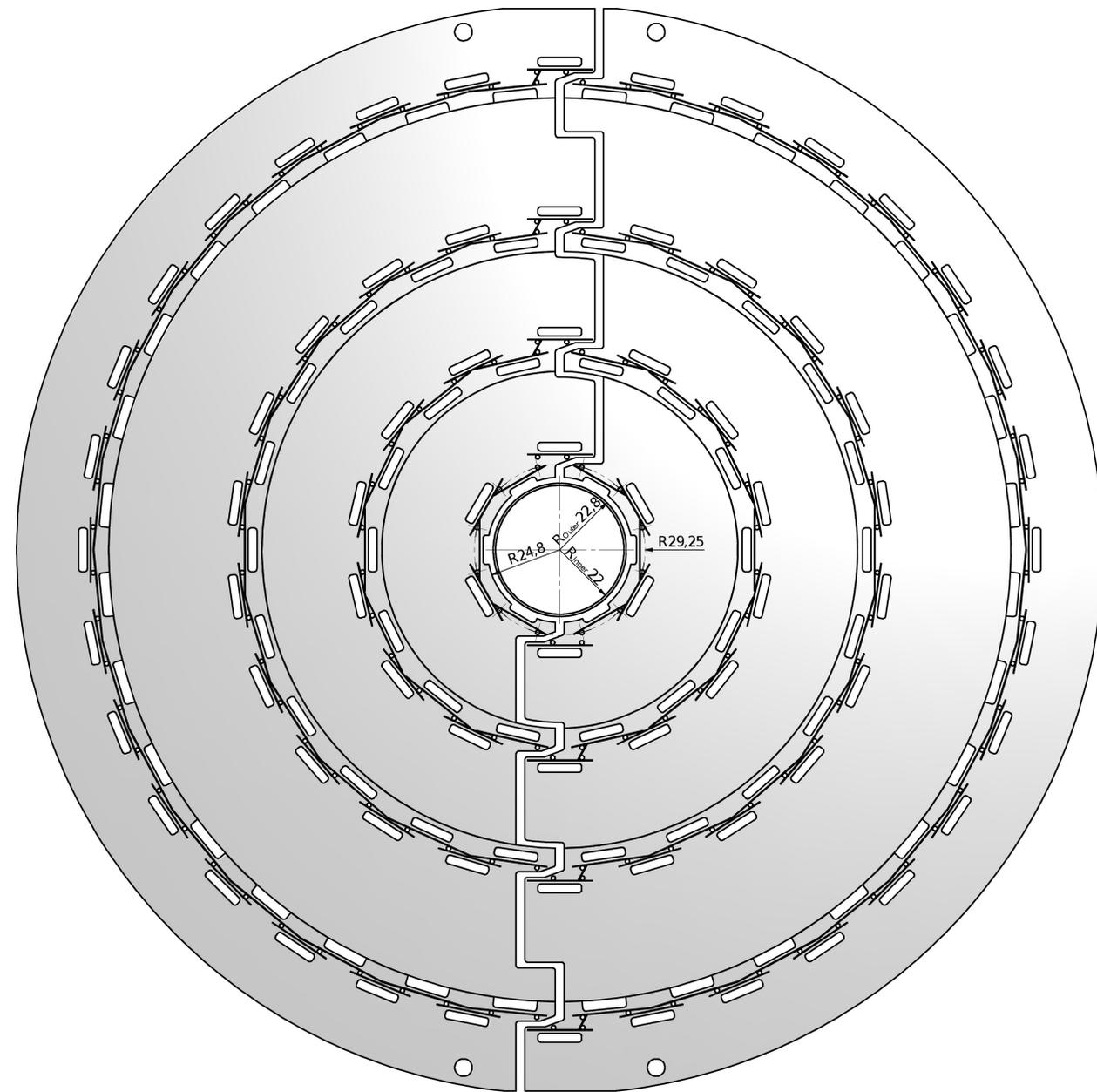
[2] I.Mandic et al., NIMA 603 (2009) 263
(p-FZ, 300μm, -20°C to -40°C, 25ns)

Detectors made from oxygenated Si and collecting electrons should operate up to a few 10^{15} n_{eq}/cm^2 with tolerable efficiency and resolution degradation: that's several 100 fb^{-1} at $R = 3 \text{ cm}$.

Further upgrade considerations

- Smaller beam pipe for improved impact parameter resolution:
 - ▶ B-tagging
- 4th layer for better track seeding efficiency and improved stand-alone tracking:
 - ▶ High Level Trigger
- Less material (mechanics, chips, cooling, cables):
 - ▶ less multiple scattering, photon conversions, nuclear interactions

CMS pixel upgrade: 4 layers



2 identical half-shells.
1184 modules (79M pixels)
(1.6 × present barrel)

$R_1 = 29$ mm, 96 modules

CH

(reduce beam pipe diameter
from 59 to 45 mm)

$R_2 = 68$ mm, 224 modules

CH

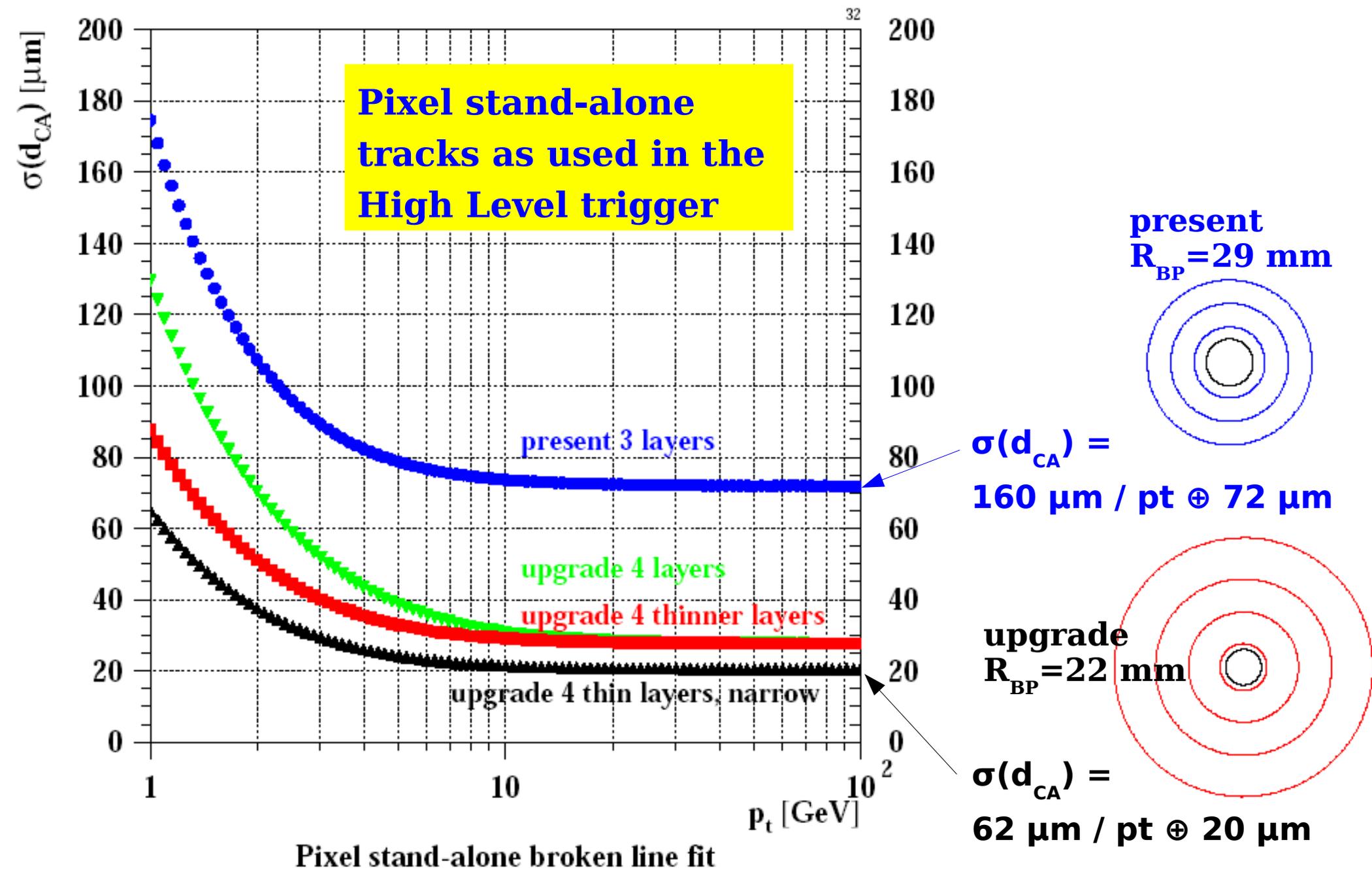
$R_3 = 109$ mm, 352 modules

Italy, CERN

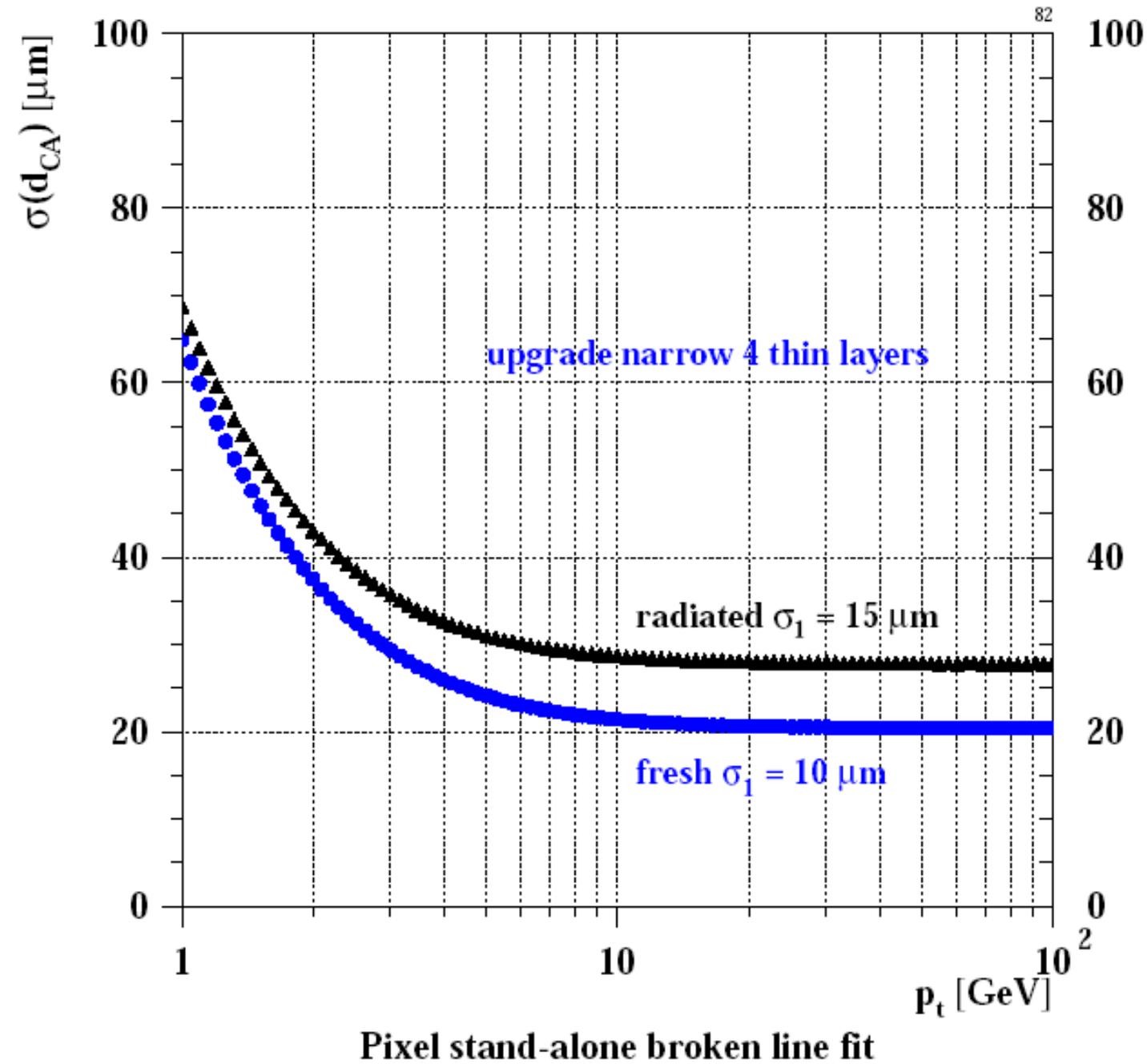
$R_4 = 160$ mm, 512 modules

Germany

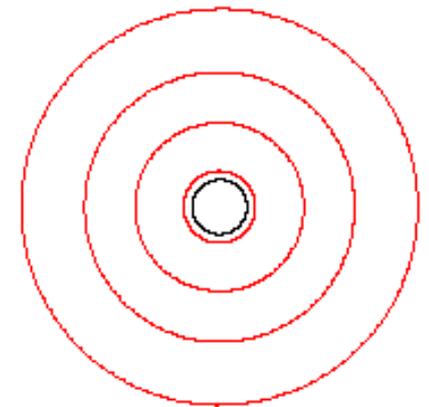
Pixel track impact parameter resolution



Radiation damage



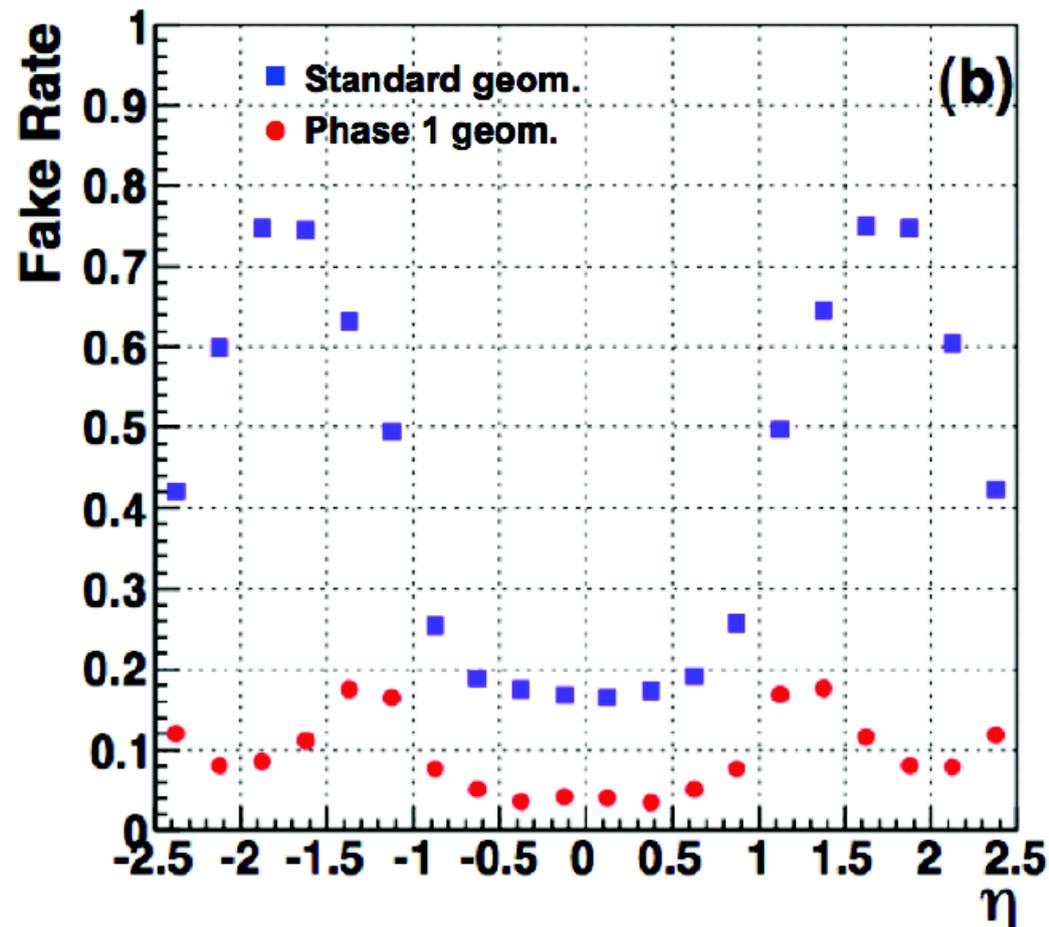
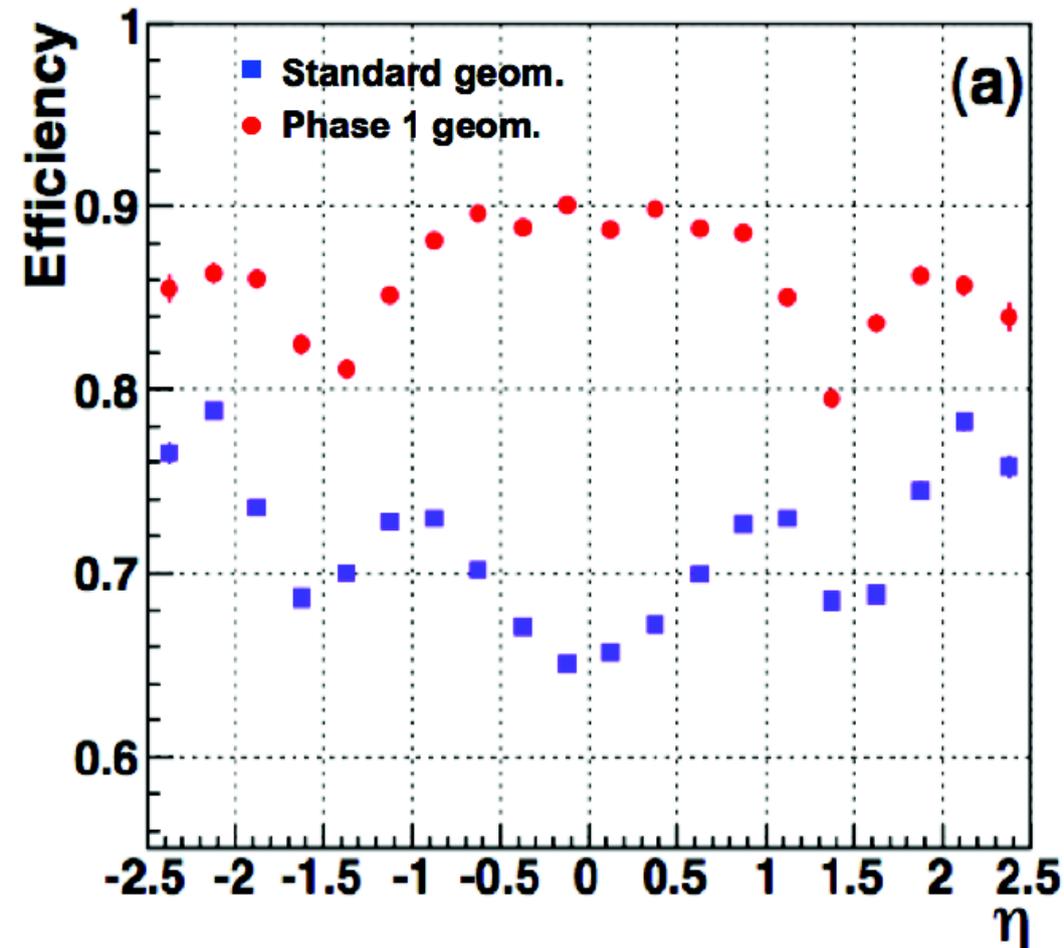
**4-layer
upgrade
 $R_{BP} = 22 \text{ mm}$**



Tracking performance with pile-up 50

- t-tbar simulation with pile-up of 50 minimum bias events ($2 \cdot 10^{34}$ with 25 ns spacing).

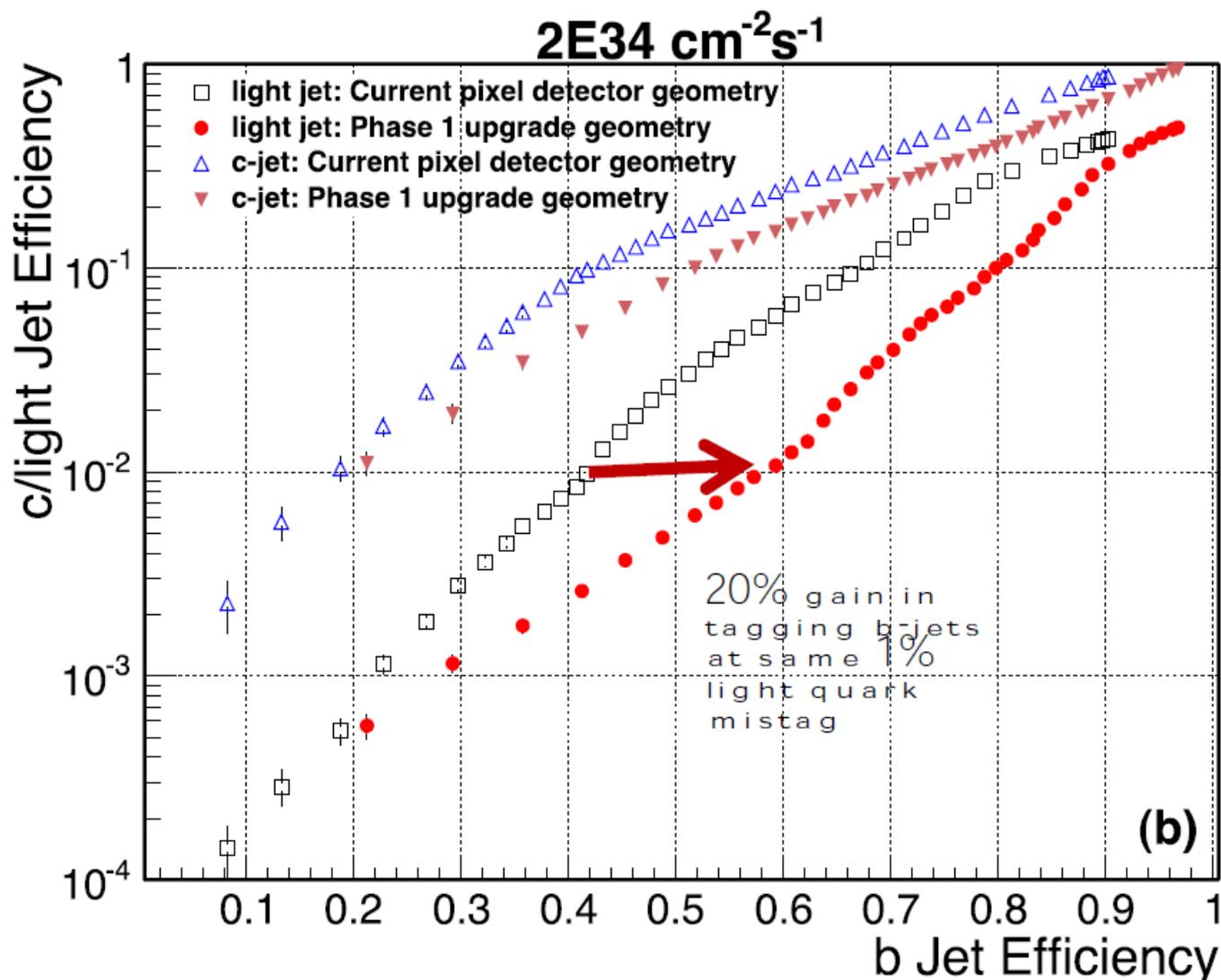
- Pixel-based track seeding.



- 4-layer upgrade improves seeding efficiency.** z-gaps remain

- 4-layer upgrade reduces fake rate.**

b-tagging performance with pile-up 50



- Detailed simulation of the physics performance on going:
 - ▶ at high level trigger,
 - ▶ at full analysis level.
- 4-layer upgrade is needed to maintain present performance at high luminosity
 - ▶ Expect improved pixel b-tagging in the HLT.

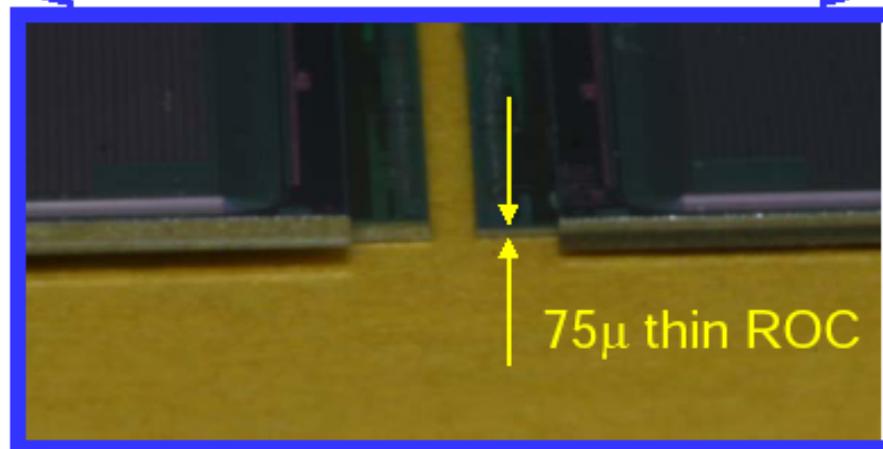
Pixel upgrade motivations

- Prepare for $2\times$ higher luminosity than design: $2 \cdot 10^{34}/\text{cm}^2/\text{s}$:
 - ▶ maintain pixel efficiency
- Less material (mechanics, chips, cooling, cables):
 - ▶ less multiple scattering, photon conversions, nuclear interactions
- 4th layer for better track seeding efficiency and improved stand-alone tracking:
 - ▶ High Level Trigger
- Smaller beam pipe for improved impact parameter resolution:
 - ▶ B-tagging
- Add redundancy in the tracking system:
 - ▶ independent of the luminosity evolution

Pixel upgrade implications

- Prepare for $2\times$ higher luminosity than design: $2 \cdot 10^{34}/\text{cm}^2/\text{s}$:
 - ▶ Requires a new readout chip with more buffering.
- Less material:
 - ▶ Low mass supports, CO_2 cooling, optical converters outside the tracking volume.
- 4th layer for better track seeding efficiency and improved stand-alone tracking:
 - ▶ Digital readout and DC-DC power converters (have to use the same outer power cables and optical fibers)
- Smaller beam pipe for improved impact parameter resolution:
 - ▶ Accepted by LHC machine group.
- Add redundancy in the tracking system:
 - ▶ Be ready early, almost independent of the luminosity evolution.

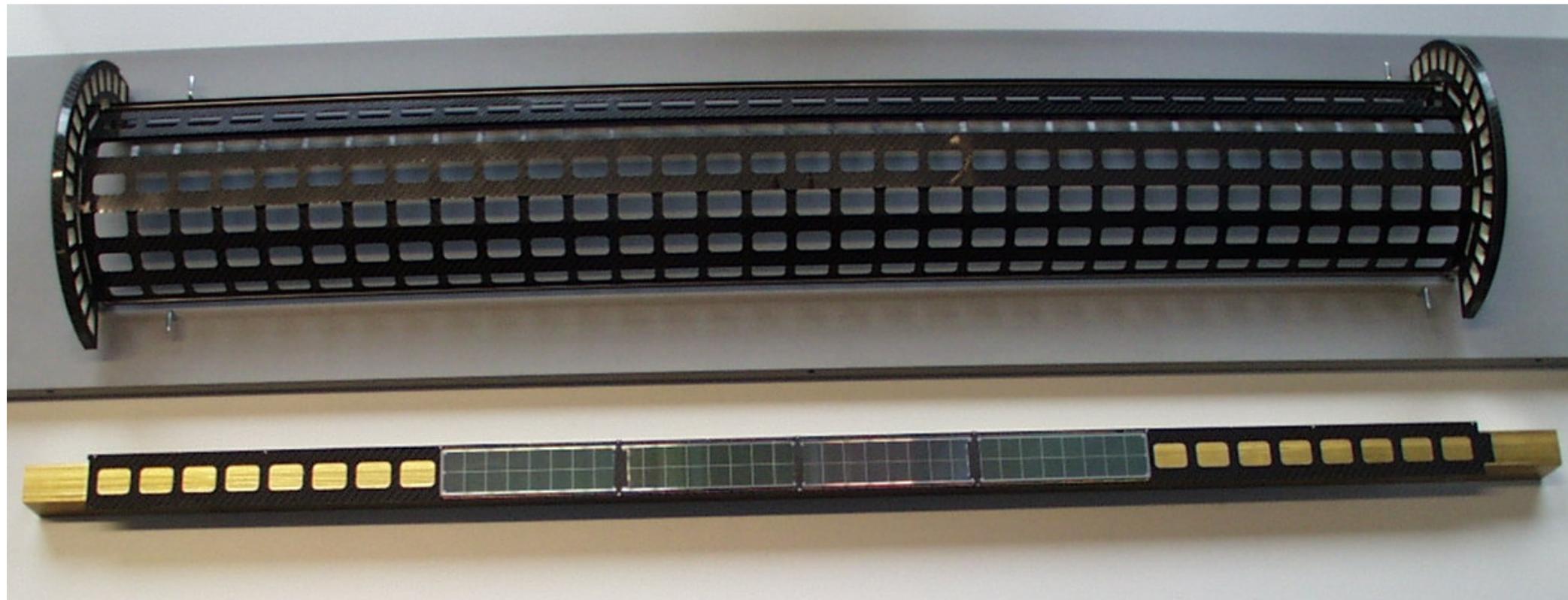
CMS pixel upgrade



Sensor 225 μ thick
Future bare module
weight = 0.89 gr
→ 65% of present

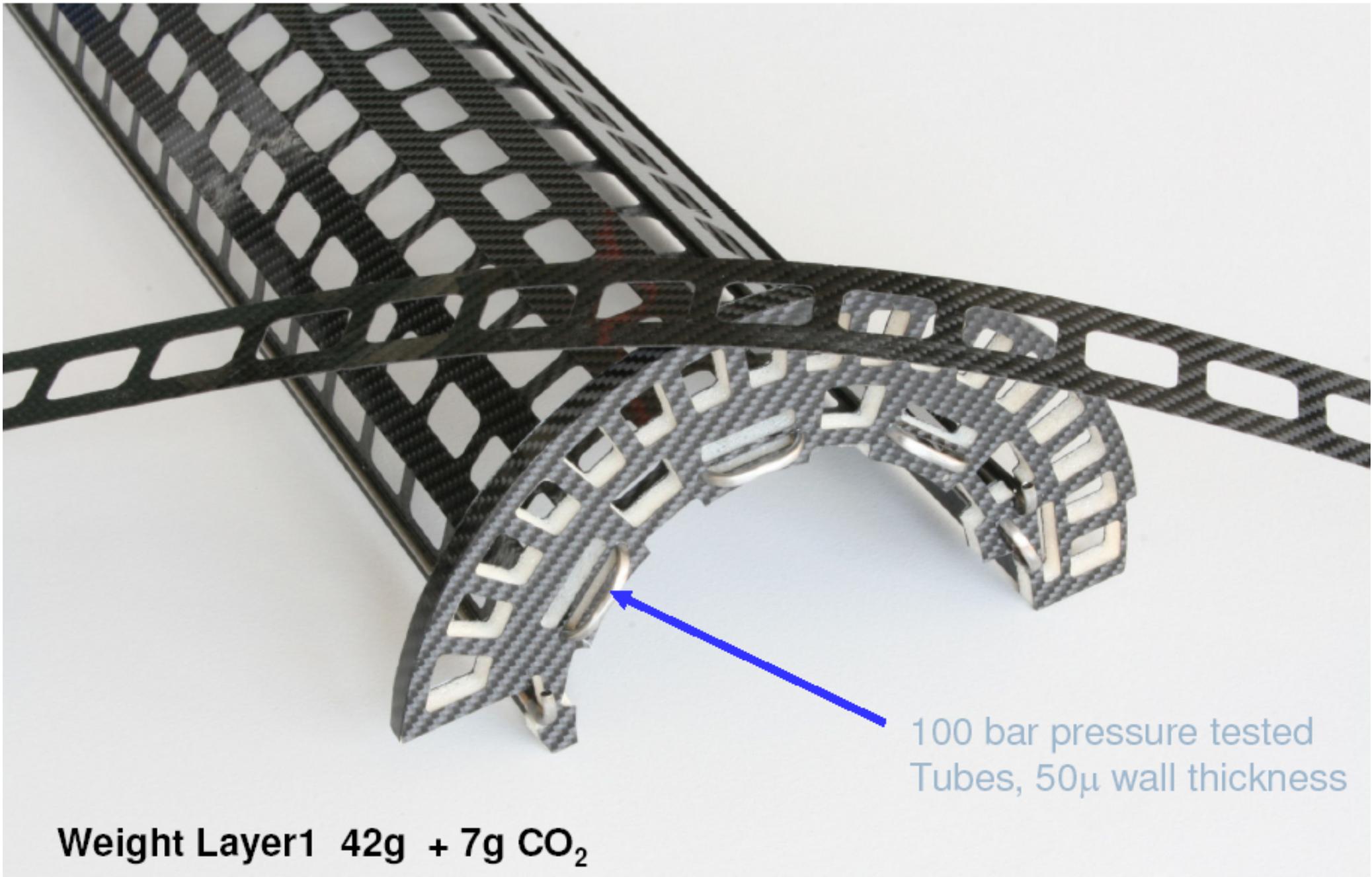
R. Horisberger
June 2009

Upgrade carbon fiber frame

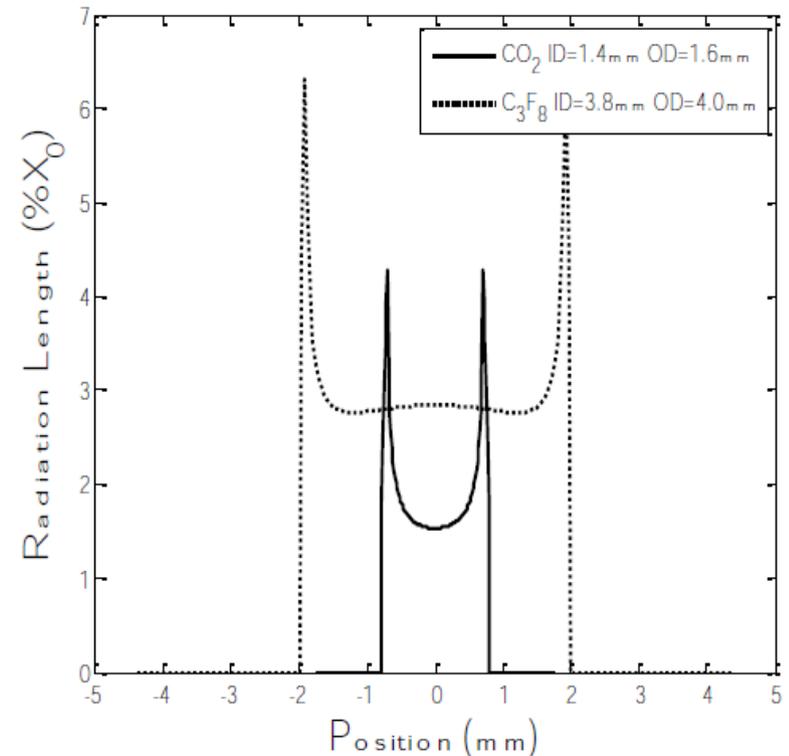
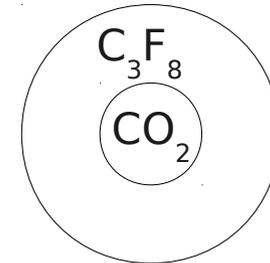
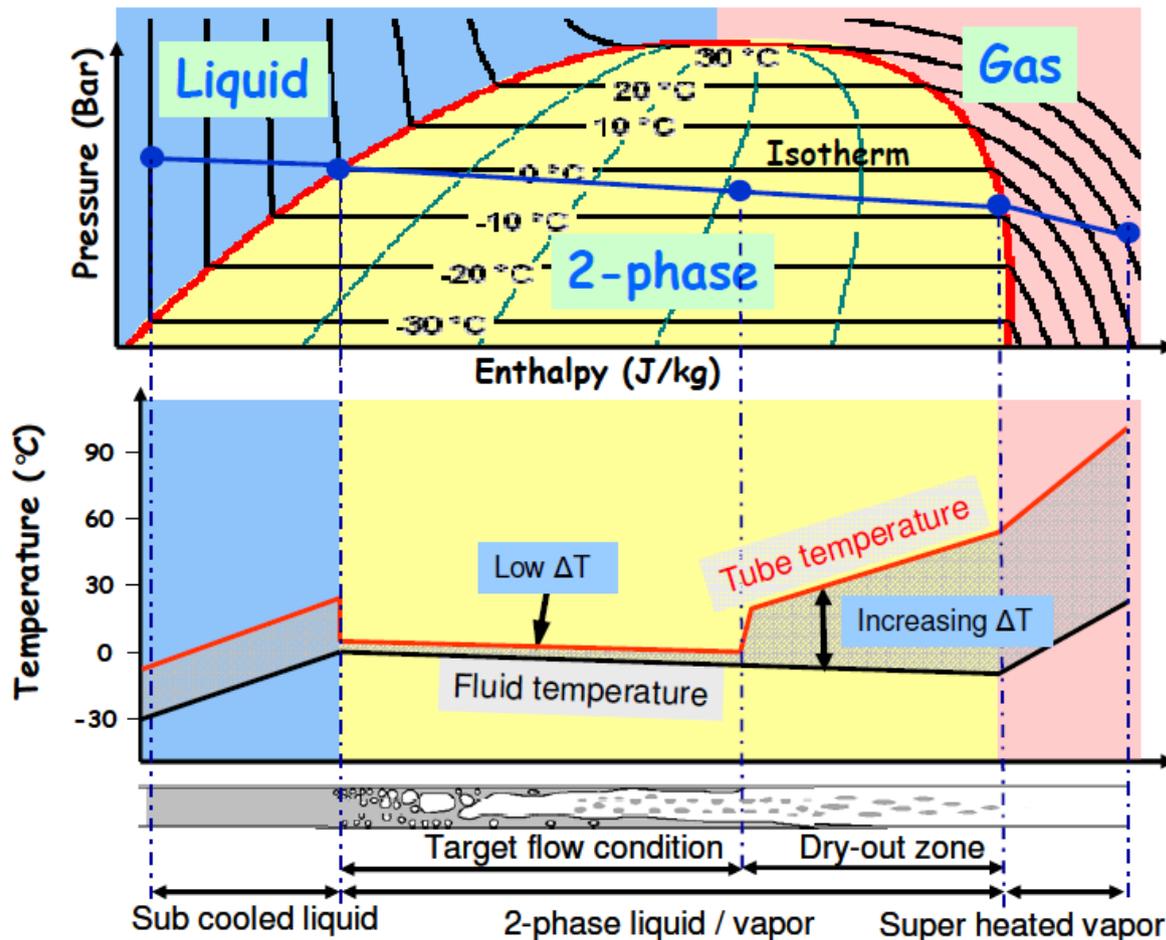


Ultra-leight weight carbon fibre frame and airex end flange with pipes for CO2 cooling.

CMS pixel upgrade



Upgrade: CO₂ cooling



- 2-phase CO₂ cooling: large latent heat
- operating at -35°C, good viscosity
- reduces Si leakage current
- reduces defect activation in Si

- Thin tubes, 50 bar
- material reduction

Barrel Pixel services

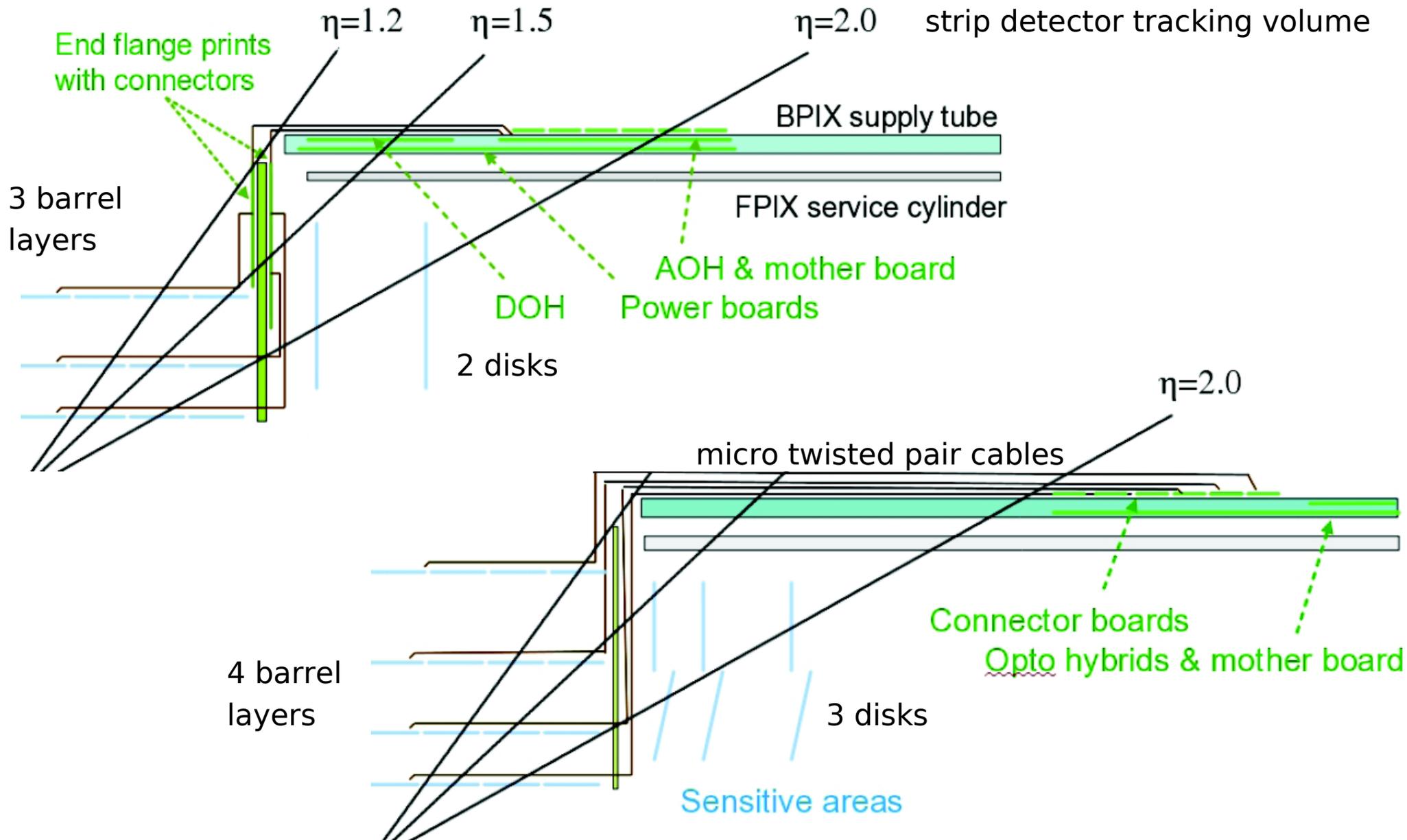


Analog-Optical
Digital-Optical

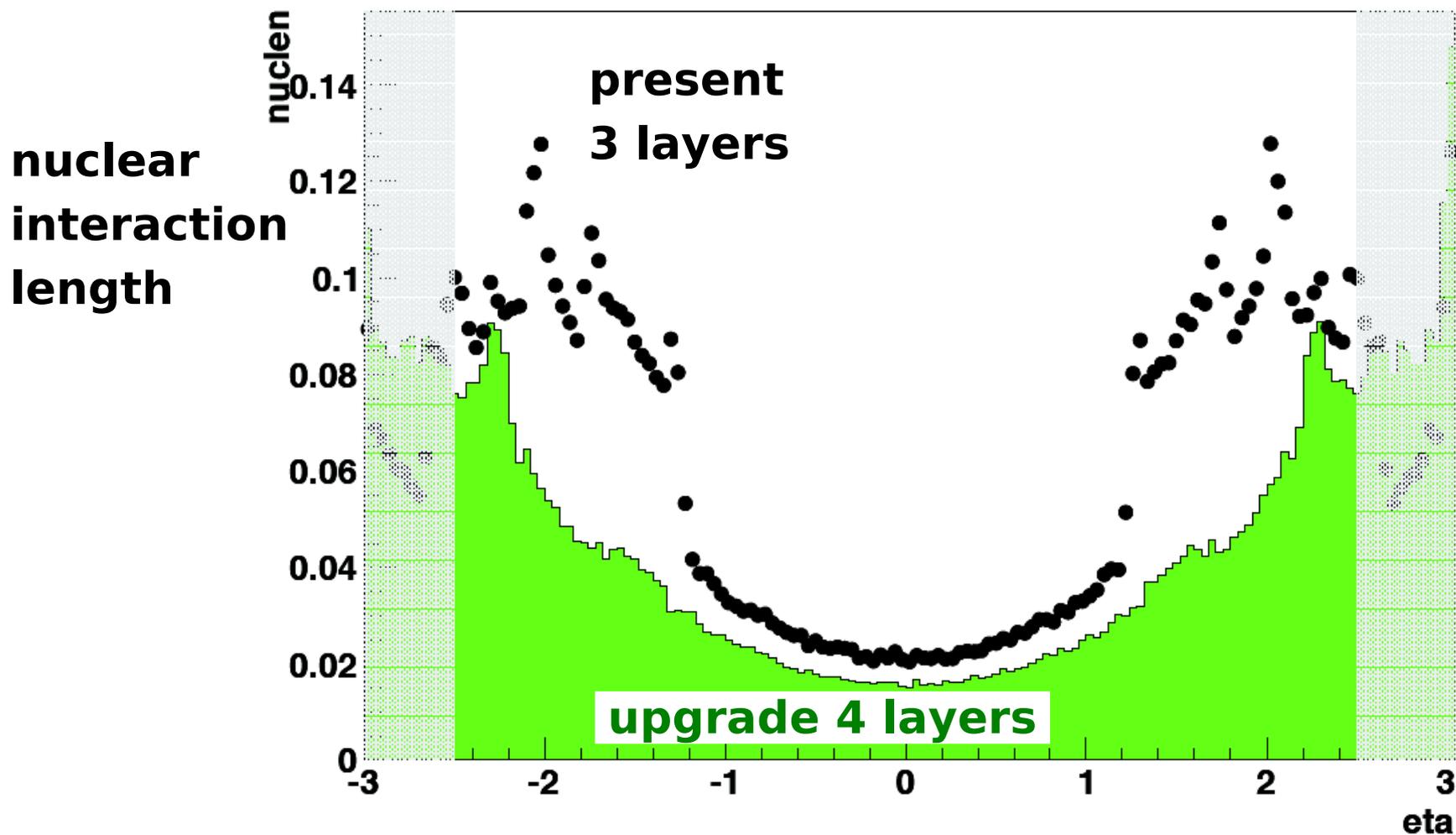


Optical
Fibers

Moving readout material out of the tracking region



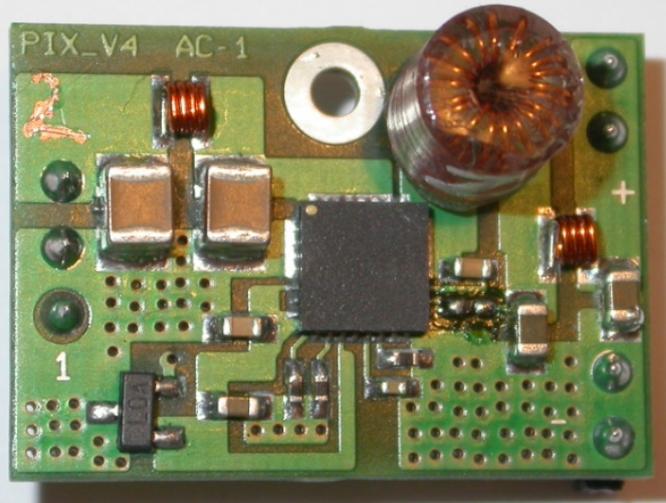
Barrel pixel material budget



Up to 12% of all hadrons are lost due to nuclear interactions in the present pixel barrel.

Upgrade will give up to factor 2 reduction.

Services

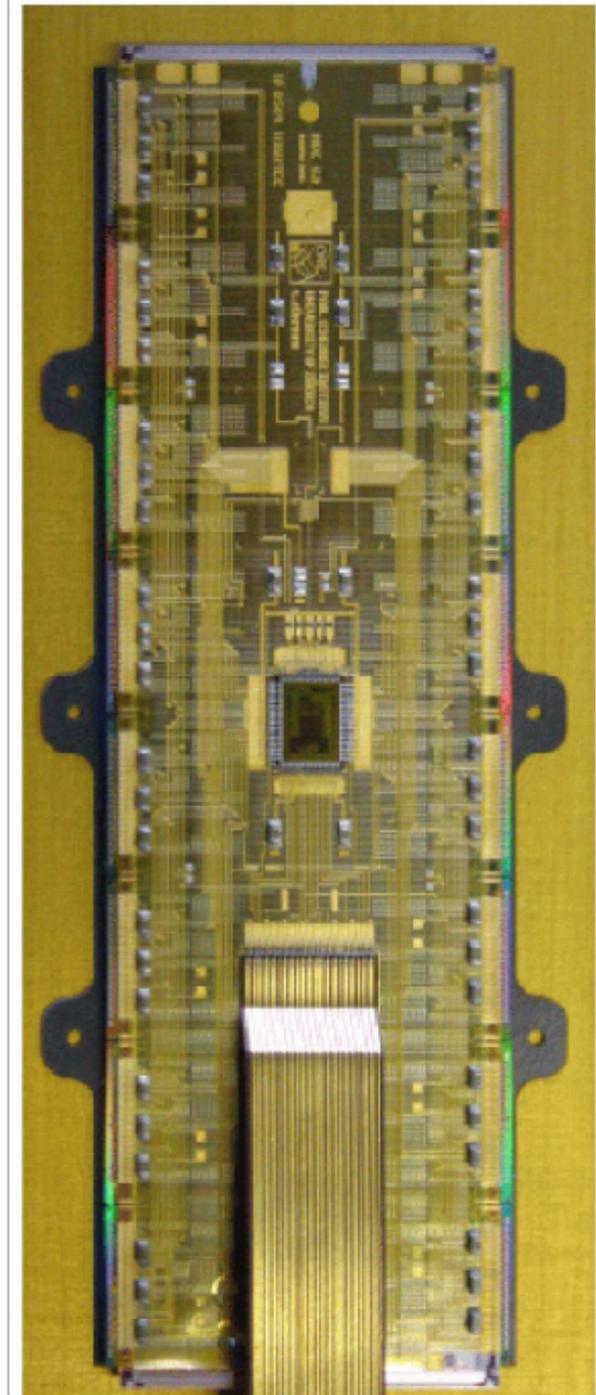
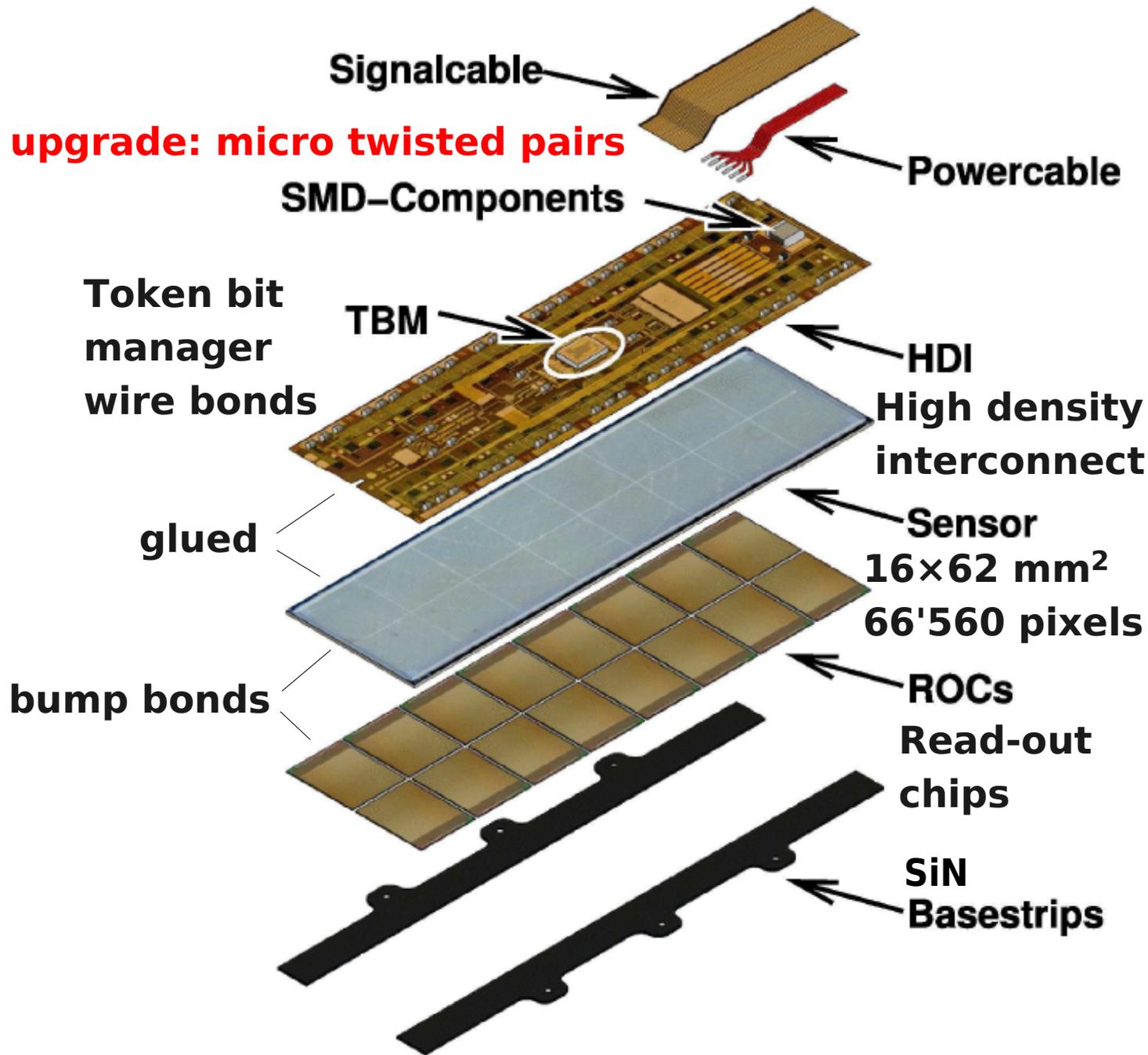


- DC-DC converter developed in Aachen:

- ▶ air-core coil, $10\text{V} \rightarrow 3.3\text{ V}$, 3 A , $\eta=75\%$
- ▶ radiation resistant AMIS 2 chip (CERN), switching at 1.2 MHz ,
- ▶ optimized design for low noise.

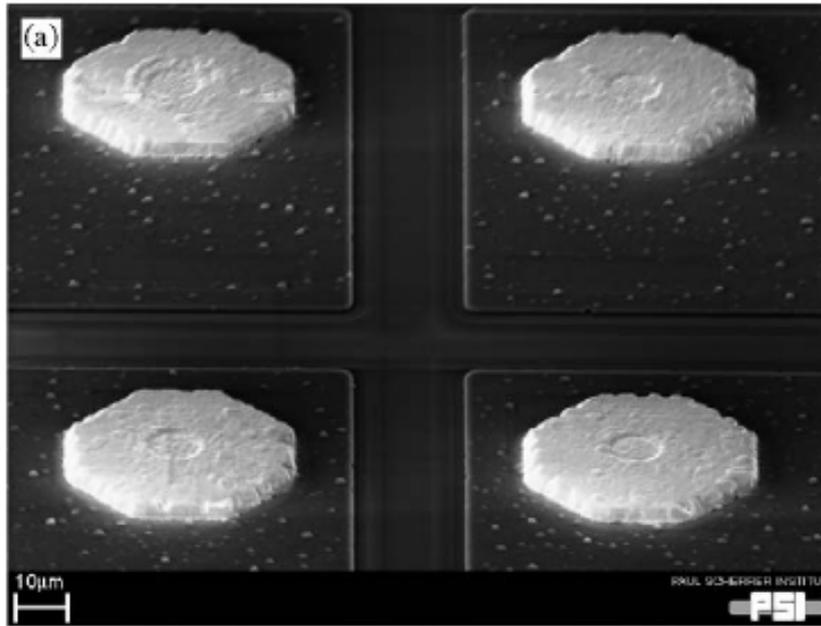
- CMS tracker cable channels are full:
 - ▶ have to use the existing services.
- Optical fibers:
 - ▶ go from 40 MHz analog to 320 MHz digital readout.
- Power:
 - ▶ Use DC-DC converters at the detector.
- Sensor bias:
 - ▶ $600\text{ V} \rightarrow 1000\text{ V}$.
- CO₂ cooling:
 - ▶ pipe-in-pipe for 100 bar .

CMS barrel pixel module



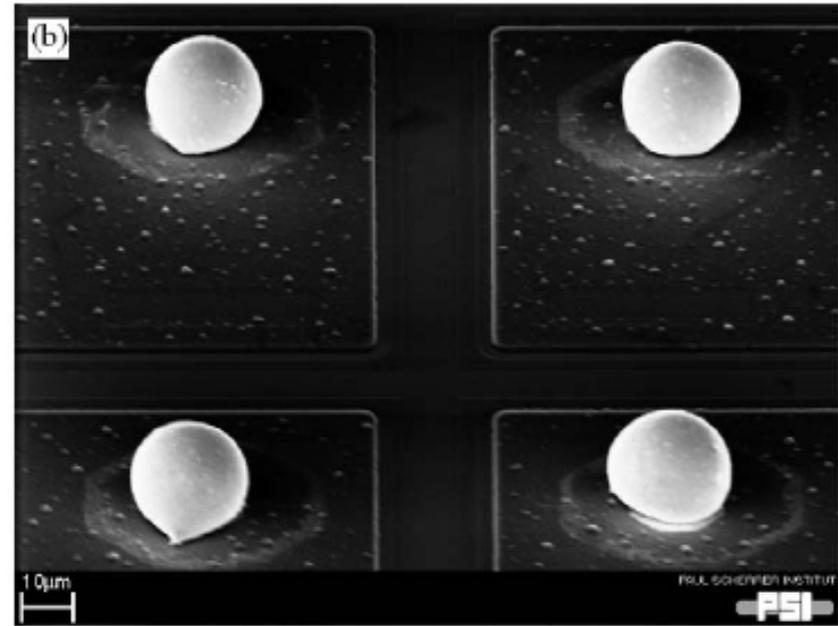
full-module $\hat{=}$ 16 ROCs

Bump bonding at PSI



**Indium pads deposited
on the Si sensor.**

**Involves many steps:
sputtering,
photo lithography,
etching...**



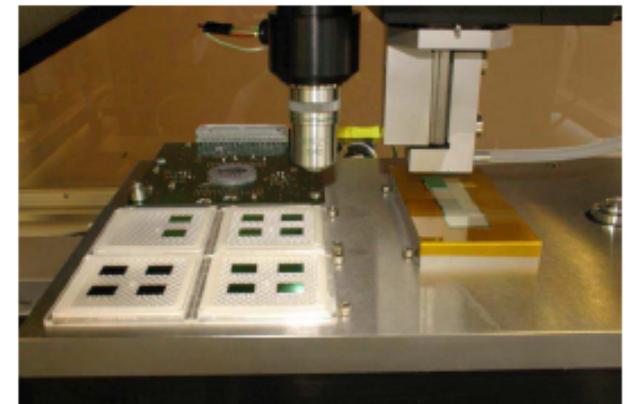
**After re-flow at 150°C in
N₂ and CH₂O₂ atmosphere.
15 μm diameter.**

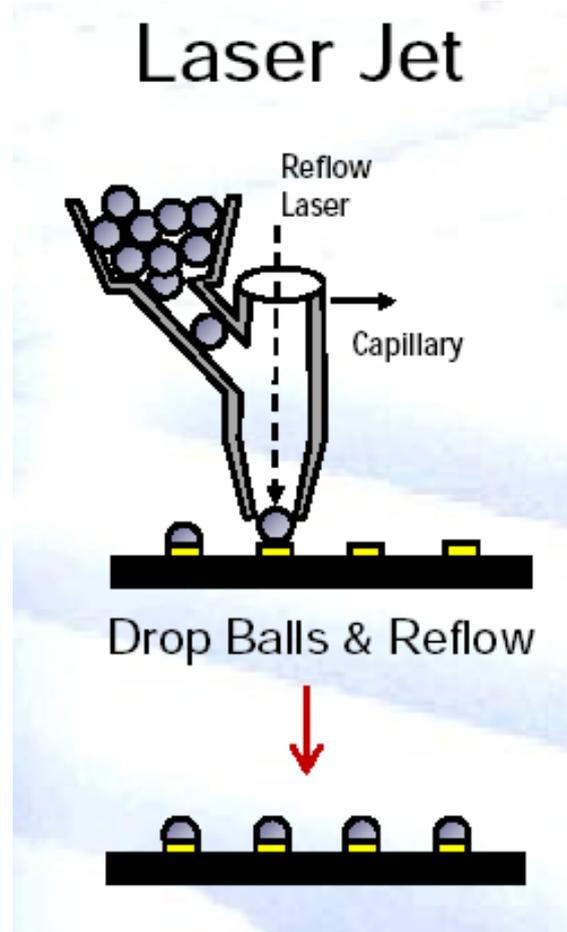
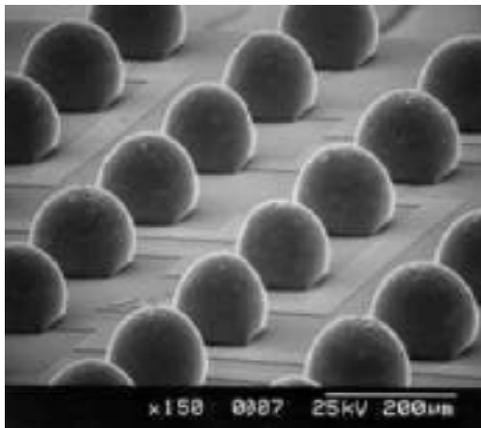
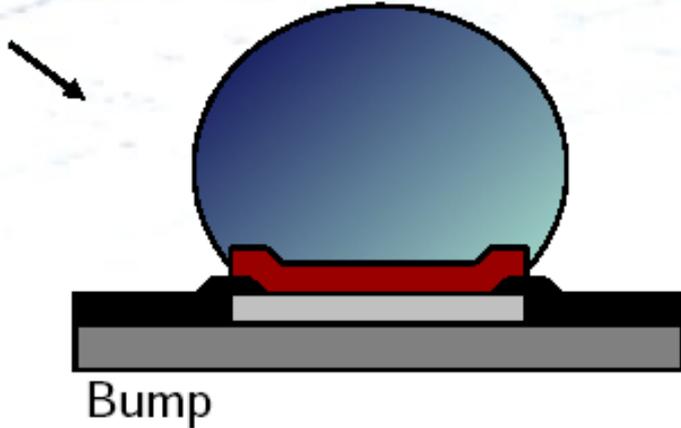
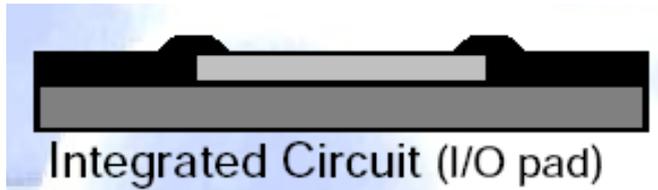
Ch. Broennimann et al.: Development
of an Indium bump bond process for
silicon pixel detectors at PSI
[NIM A565\(2006\)303-8](#)

Flip chip assembly at PSI

- ▶ Precision: $1 \div 2 \mu\text{m}$
- ▶ Production rate:
 - ▶ 6 modules / day + tests
 - ▶ automated: 1 hr/module
- ▶ Bare module test:
 - ▶ IV-curve
 - ▶ ROC functionality
 - ▶ bump yield
 - ▶ rework: 80% success

Precision x-y-z stage
Computer controlled
Commercially available.

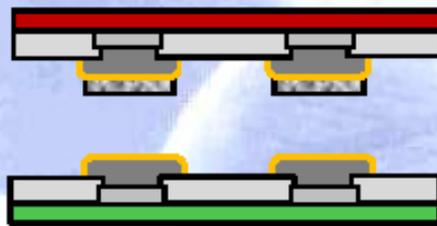




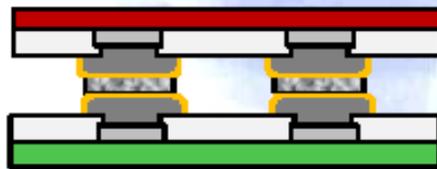
- Start with high-precision balls.
- Drop through capillary towards pad.
- Melt by laser pulse during fall.
- Solidify on pad.
- Step-motor controlled.
- 5 ball / second.
- 40 μm balls at 80 μm pitch possible now.
- 30 μm balls under development.

Laser reflow bonding

1) Pickup Die & Align
($\pm 5 \mu\text{m}$)

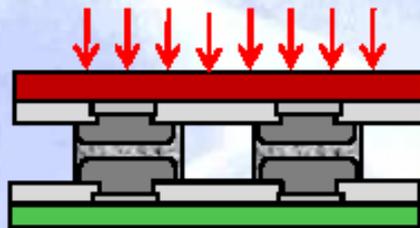


2) Contact
(10kgf)

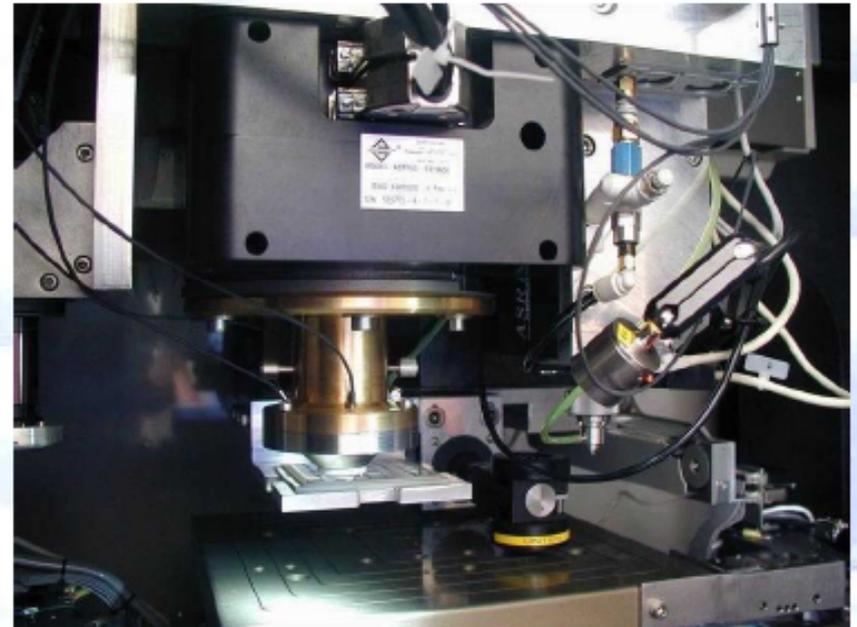


Neodym-dotierter Yttrium-Aluminium-Granat-Laser 1064

3) Laser Reflow
(20msec, Nd^{3+}YAG)



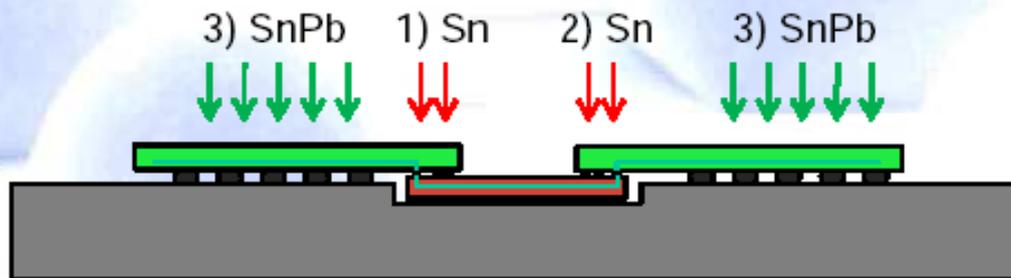
LaPlace Assembly System™ PacTech



Placement accuracy: $\pm 15 \mu\text{m}$: 3000 - 5000 UPH
 Placement accuracy: $\pm 10 \mu\text{m}$: ~2000 UPH
 Placement accuracy: $\pm 5 \mu\text{m}$: ~1000 UPH
 Placement accuracy: $\pm 2.5 \mu\text{m}$: ~500 UPH

units
per
hour

Laser based assembly allows localized heating:



- Selective to individual die
- Energy localized to bumped areas
- Ability to differentiate between solder alloys
- Low stress
- Minimizes IMC (time/temp)

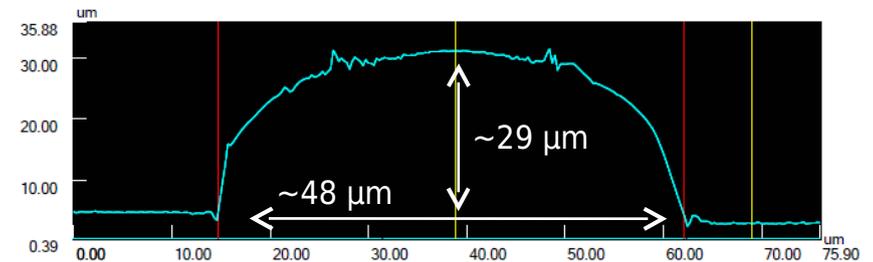
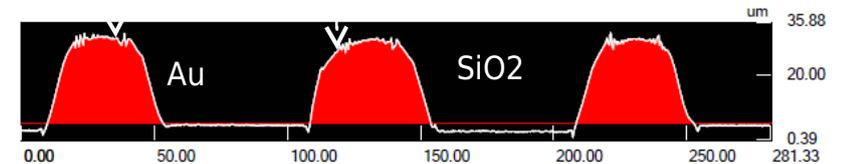
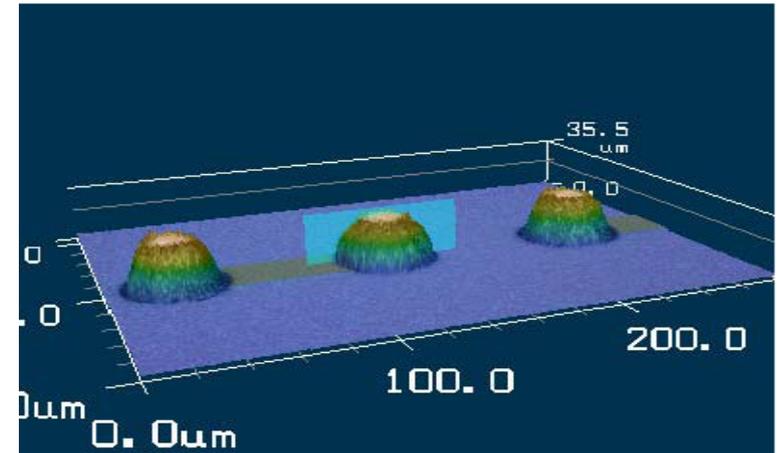
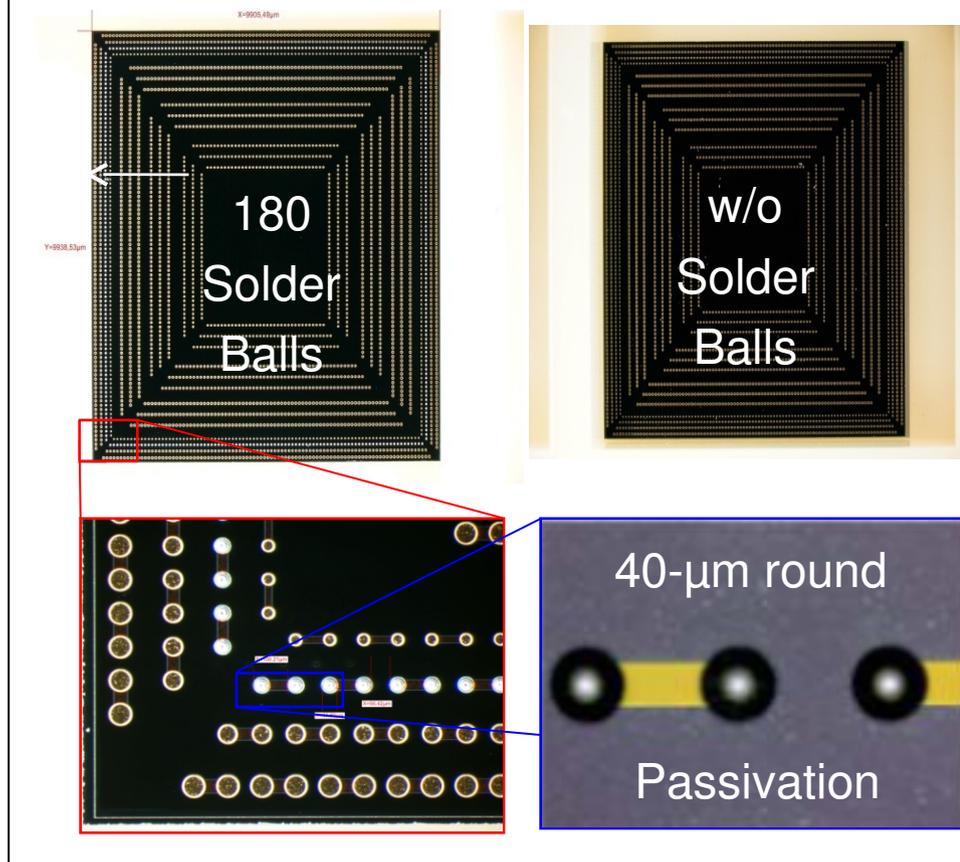
$M_p \text{ SnPb} = 183^\circ\text{C}$

$M_p \text{ Sn} = 232^\circ\text{C}$

PacTech test structures

Pac 2.7 Wafer from Pac Tech GmbH

- Two 200-mm Wafers with 275 Chips each
- 5- μm electroless Ni/Au UBM on both
- 40- μm SAC305 Solder Jetting with SB2 on one
- Wafer Sawing & Chip Singulation



Available since Dec 2010.
Used with 4 machines/vendors.

Pac Tech: SB2 Jet



Solder Ball Placer:

pre-formed balls are placed sequentially at 6-7 Hz
fused by laser heating

30 μm balls being certified, 40 μm ordered for test.

SET: FC 150 Flip-chip bonder



Industry standard, expensive, slow.

For placing and re-flow heating. Used at IZM.

SET: Kadett K1



Unitemp: RS-350-110



PSI design: cheapest, slow.

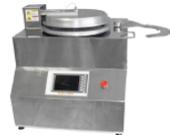
no > 50 mm heating chuck available.

Tacking Tests completed on small samples:
> 0.6 g/ball @ 155°C for chip & substrate.
Re-flow tests completed: OK.

Pac Tech: Laplace



RFA 300M



Reflow Oven RFA 300M

Novel Industry Standard: medium price
laser-assisted, fast.

Tacking Tests completed:
low force with chip at 195°C for 1s.
Reflow Tests completed: OK.

Finetech: FINEPLACER femto

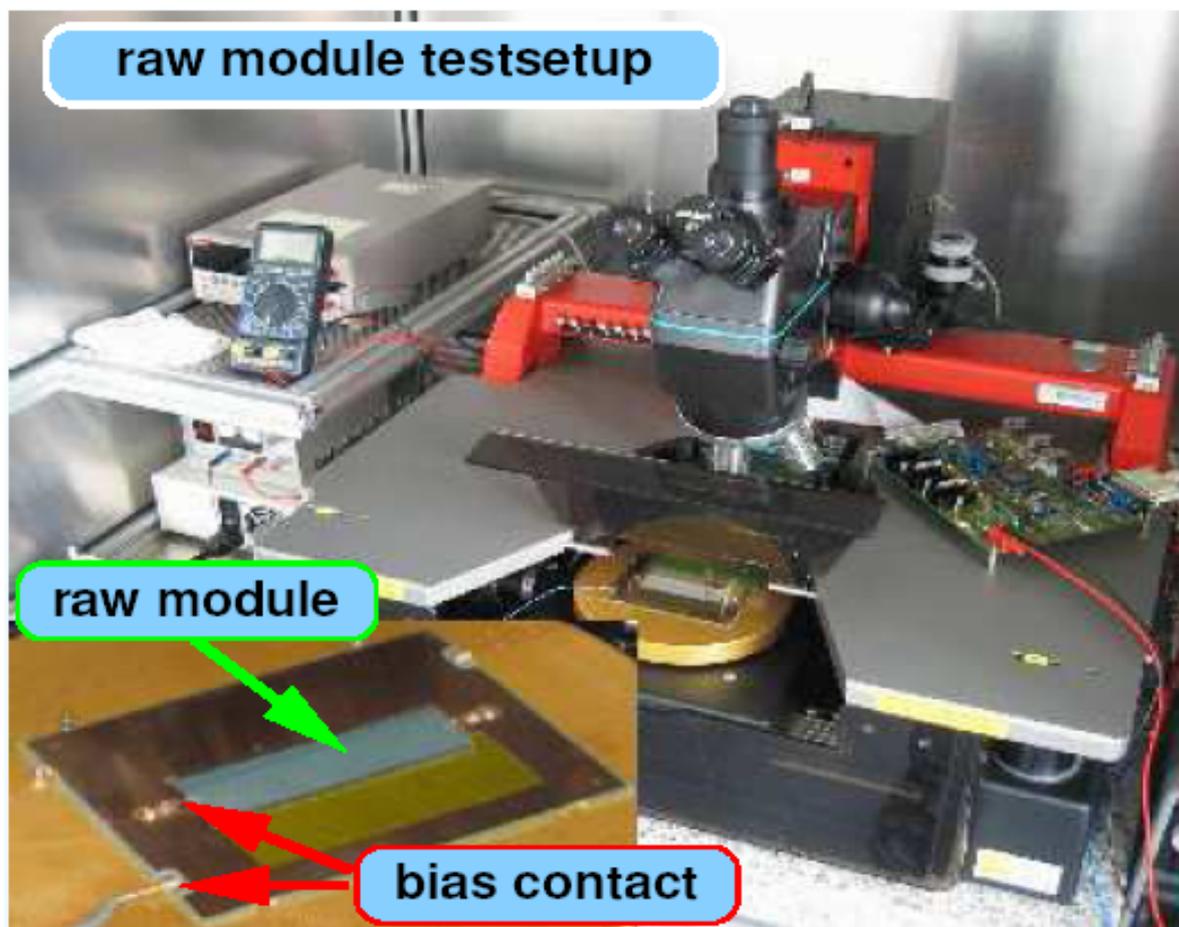


Novel FC 150 competitor: medium price.

Placing and re-flow heating, low-force, fast.

Tacking / re-flow tests under way.

Bare module test at PSI



Semi-automatic probe station at PSI:
load manually,
step and measure automatically.

- Test bare module after flip-chip bump bonding:
- Sensor I-V curve.
- Test 16 readout chips.
- Determine bump yield.
- Rework bad modules:
 - replace individual chips.

Probe station at DESY FEC

Süss Microtech PA 300 Probe Station

auctioned
from
Qimonda
in Dec 2009



Probe-Card Holder



will order 42 needle
probe card for testing
ROCs after bump
bonding.

up to 300 mm wafers

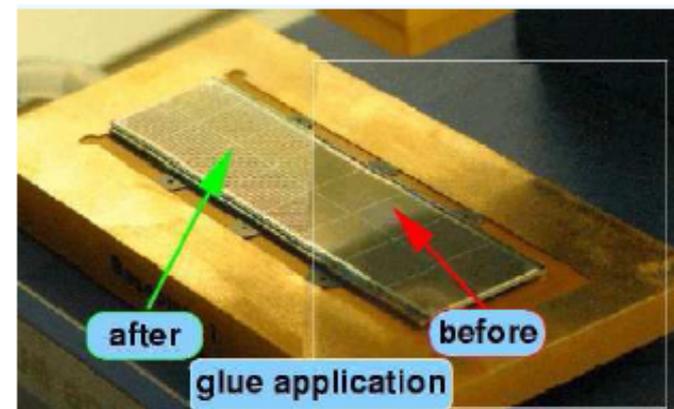
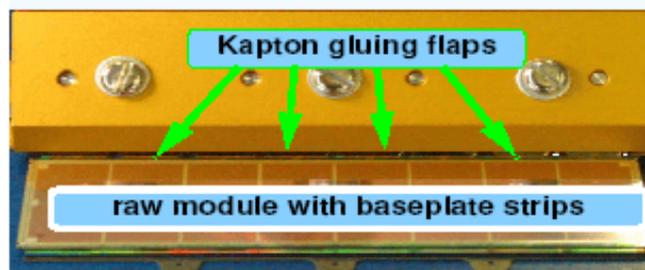
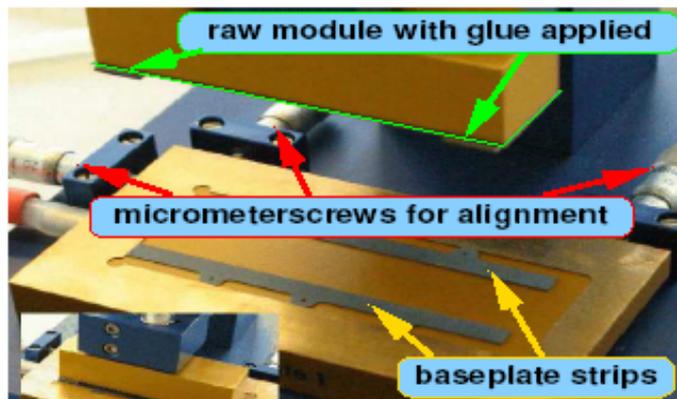
Semi-Automatic

Shielded

Thermo chuck -40 .. +125°C

Barrel pixel module assembly line at PSI

- ▶ Production rate:
 - ▶ 4 full + 2 half modules / day
 - ▶ or 6 full modules / day
- ▶ Three glueing steps:
 - ▶ glue basestrips to raw module
 - ▶ underfill sensor with glue
 - ▶ glue HDI to complete assembly
- ▶ Important: custom-made tools



Tools and assembly line being prepared at Uni Hamburg.

Pixel module cold calibration

► Challenges

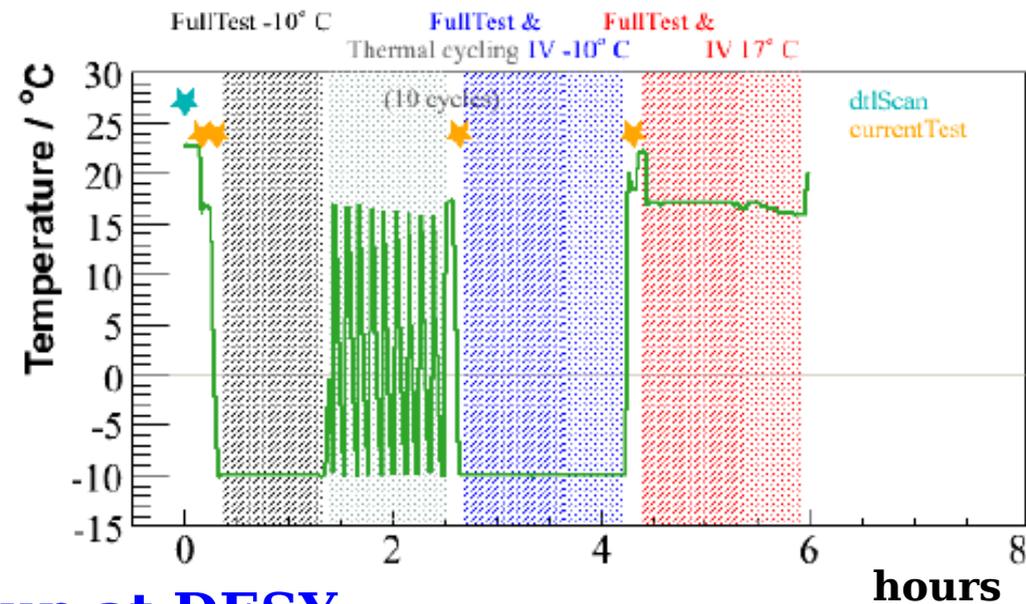
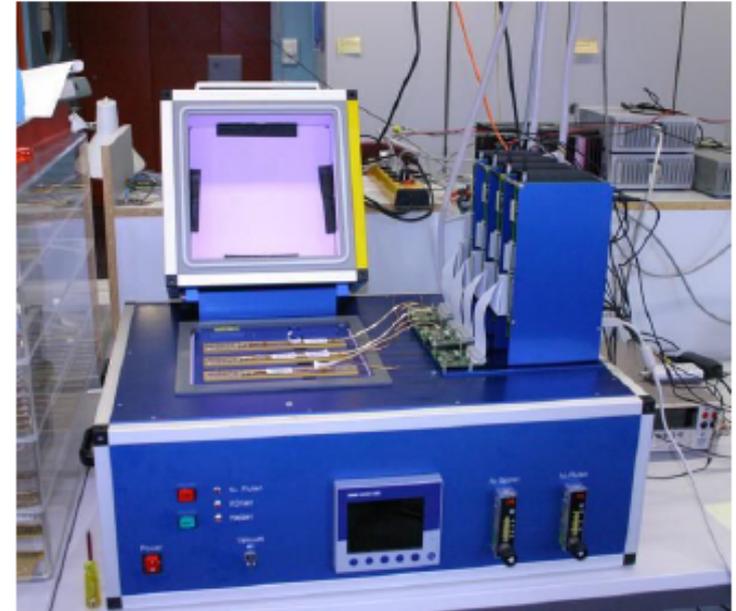
- Huge number of channels: $5 \div 6 \times 10^7$
- Multy-dimensional parameter space: 29 DACs/ROC
- Temperature dependence: tests done at -10°C and $+17^\circ\text{C}$ **upgrade: -20°C**

► Test set up

- Programmable cooling box
- 4 modules at a time
- Custom built test-boards with FPGA

► Procedure

- Start-up adjustments
- Full Test at -10°C
- 10 thermal cycles
- Full Tests and IV at -10°C and $+17^\circ\text{C}$



Cold calibration set up will be set up at DESY.

Pixel gain calibration

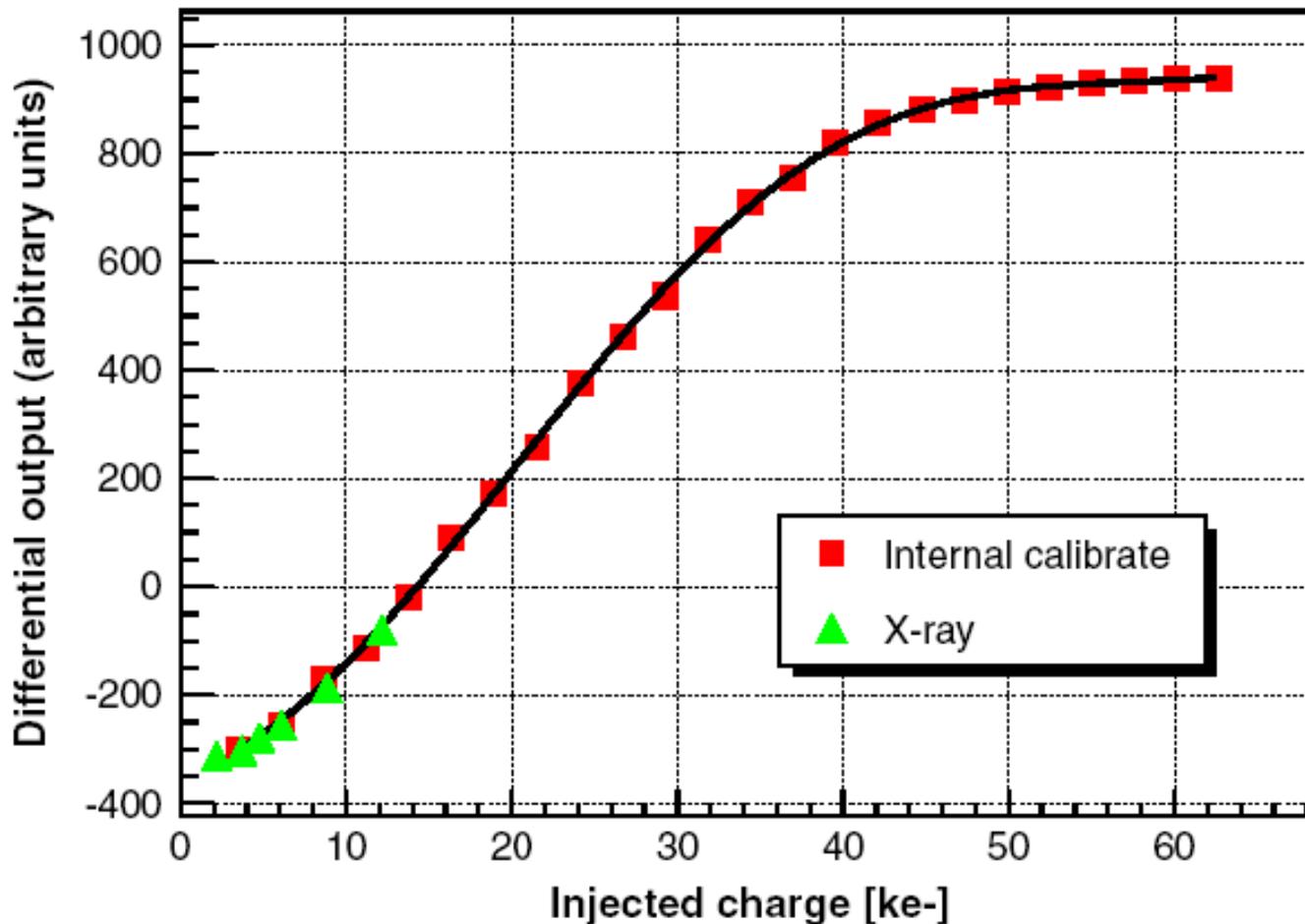


Fig. 8. Analog signal transmission.

- Ultimate position resolution comes from pulse height interpolation.
- Need pixel-to-pixel gain calibration.
- Large amplitudes:
 - ▶ internal test pulse.
- Close to threshold:
 - ▶ X-ray lines (Mo, Ag, Ba).
- X-ray stand being prepared at Uni HH.

Universal pixel test board

Design and firmware
by Beat Meier, PSI

bias voltage

psi46
chip

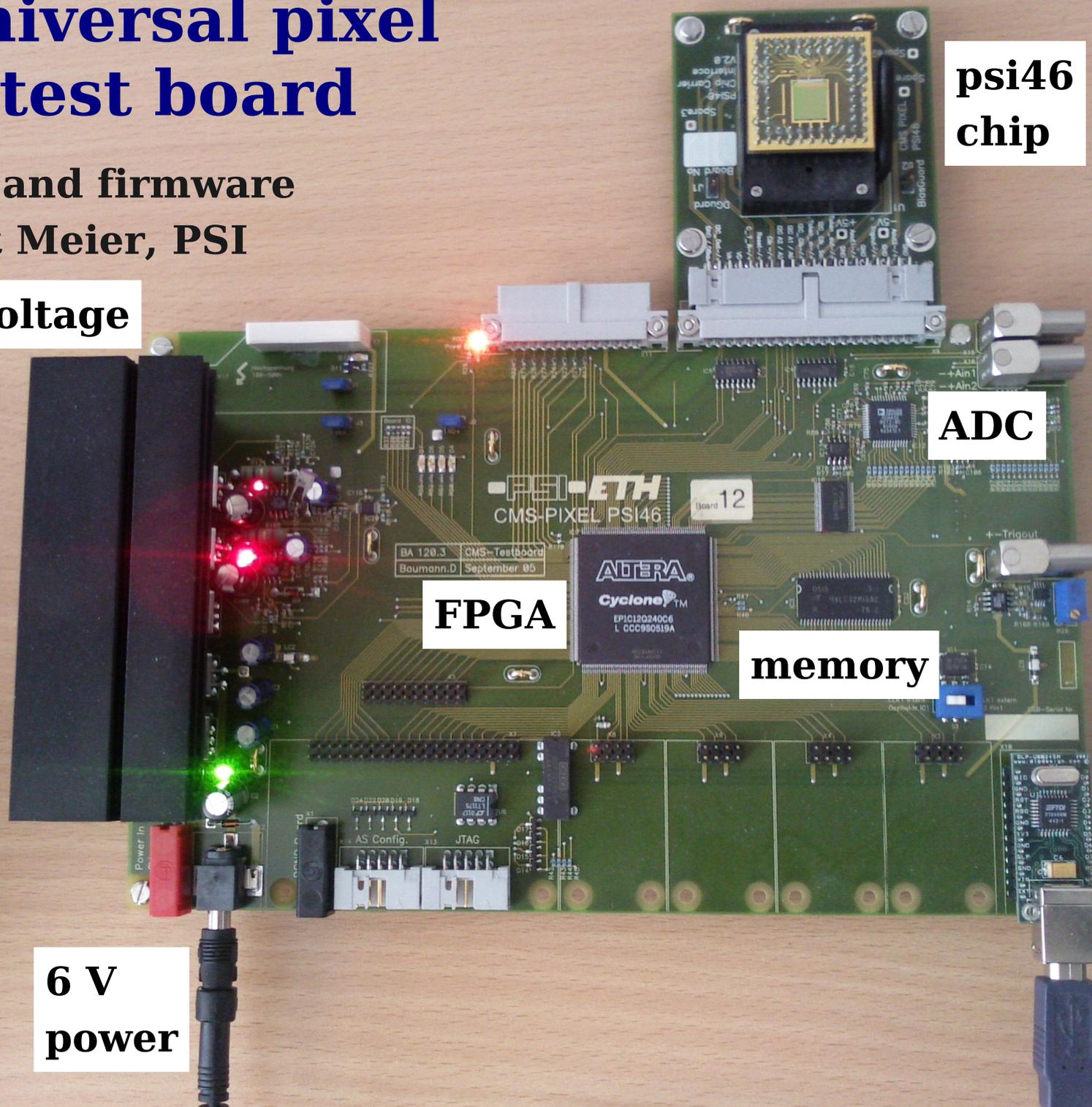
ADC

FPGA

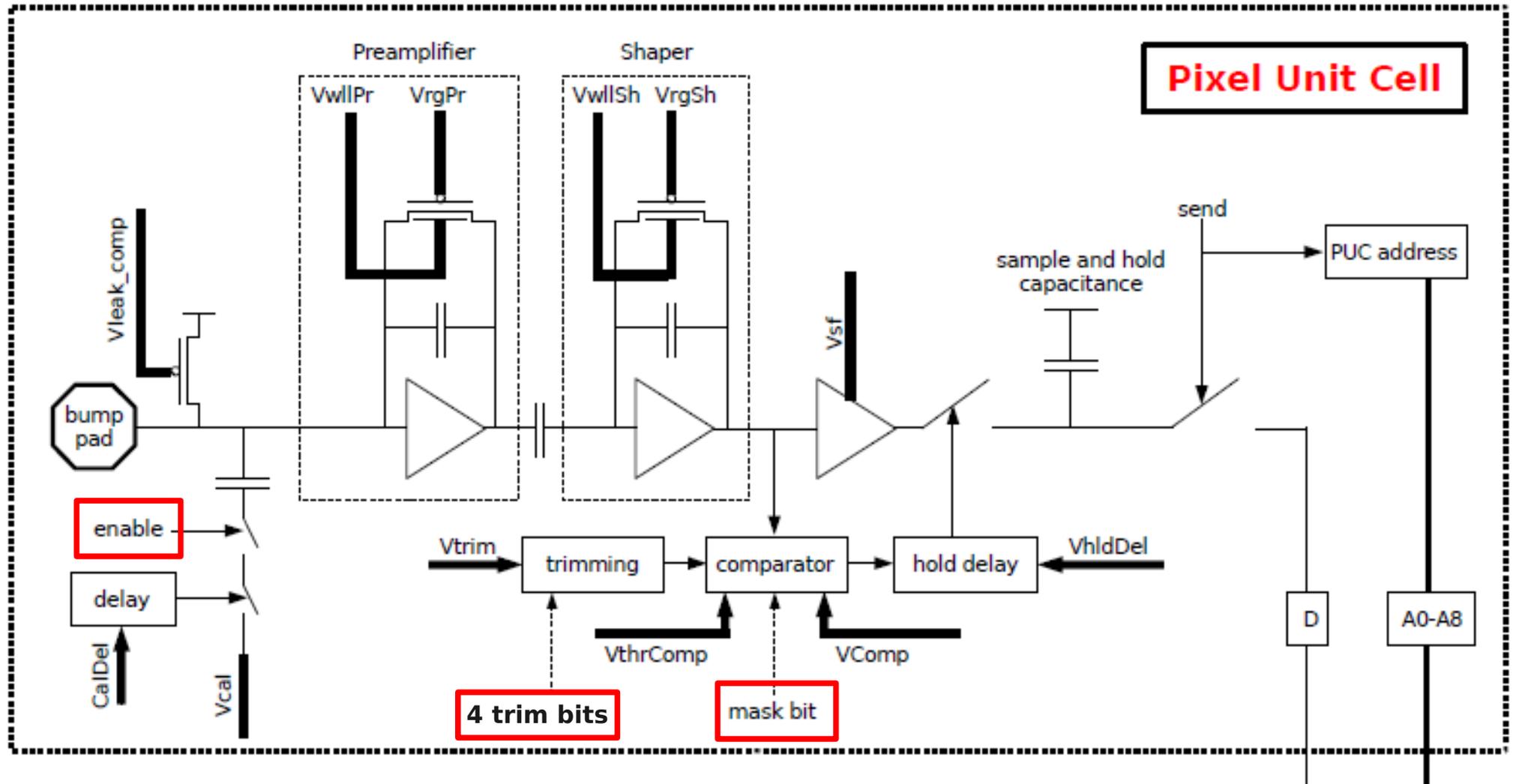
memory

6 V
power

USB to
laptop



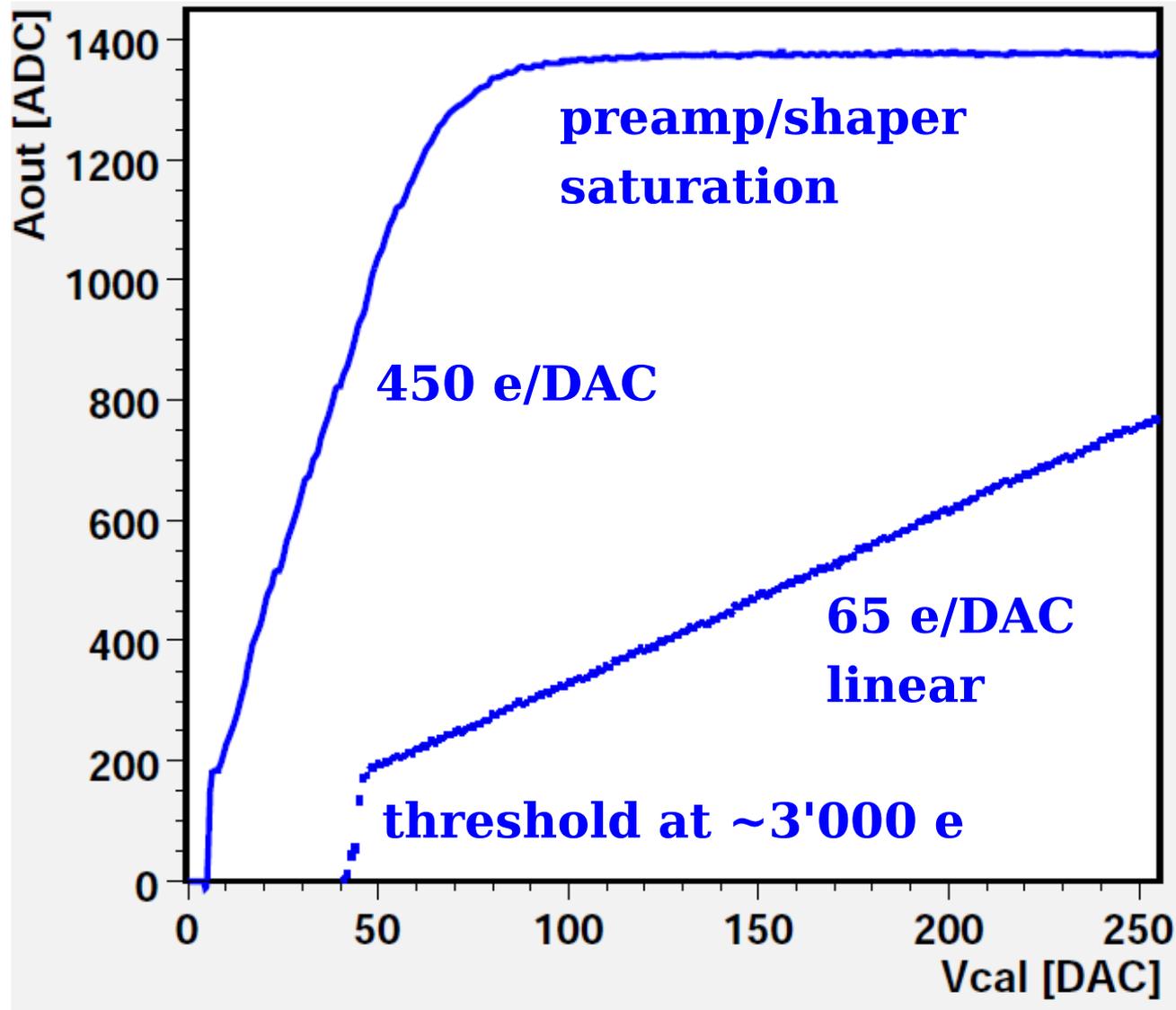
psi46 pixel readout chip



— adjustable by programmable DAC, 26 per ROC

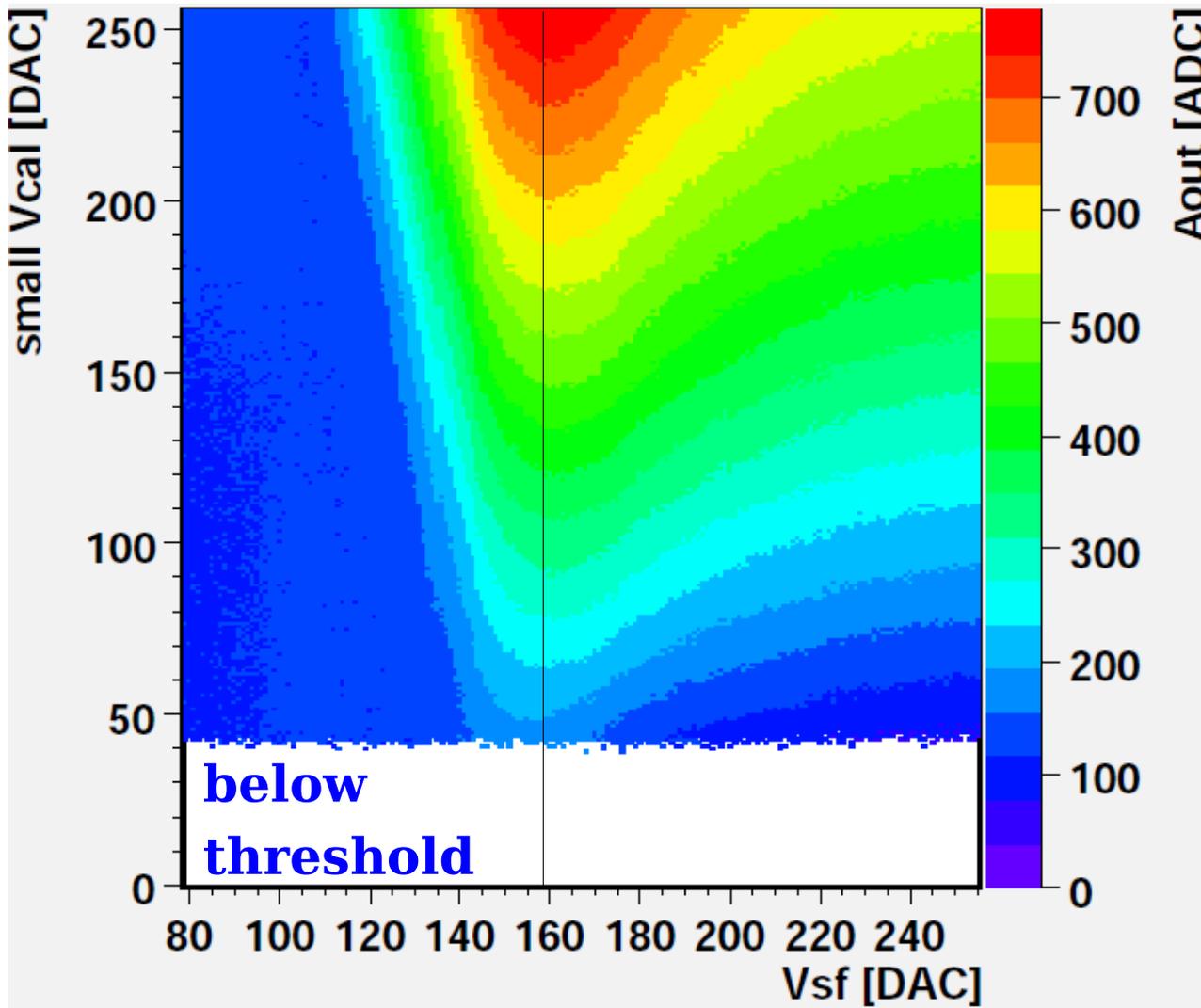
□ programmable register, 3 per pixel

gain and linear range

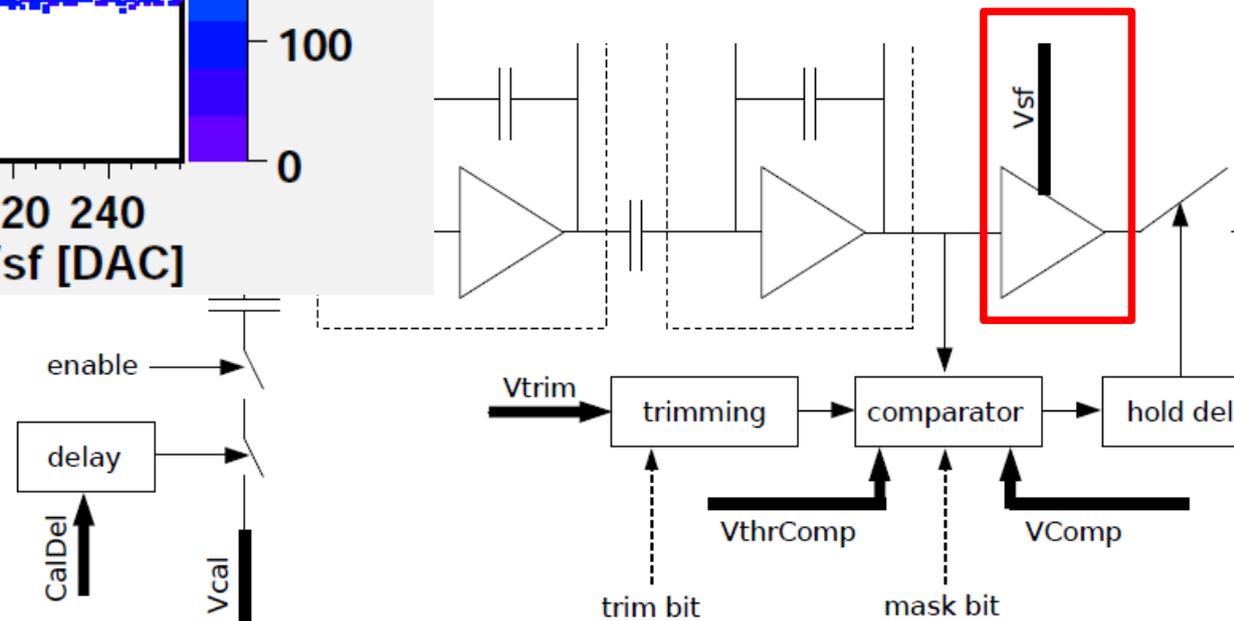


- One pixel.
- 2 Vcal ranges (PSI X-ray calibration):
 - CtrlReg 0 or 4,
 - 65 ± 5 e/DAC,
 - 450 e/DAC.
- Linearity for small pulses important for spatial resolution using charge sharing.
- Saturation around 36'000 e (~ 1.6 MIP).

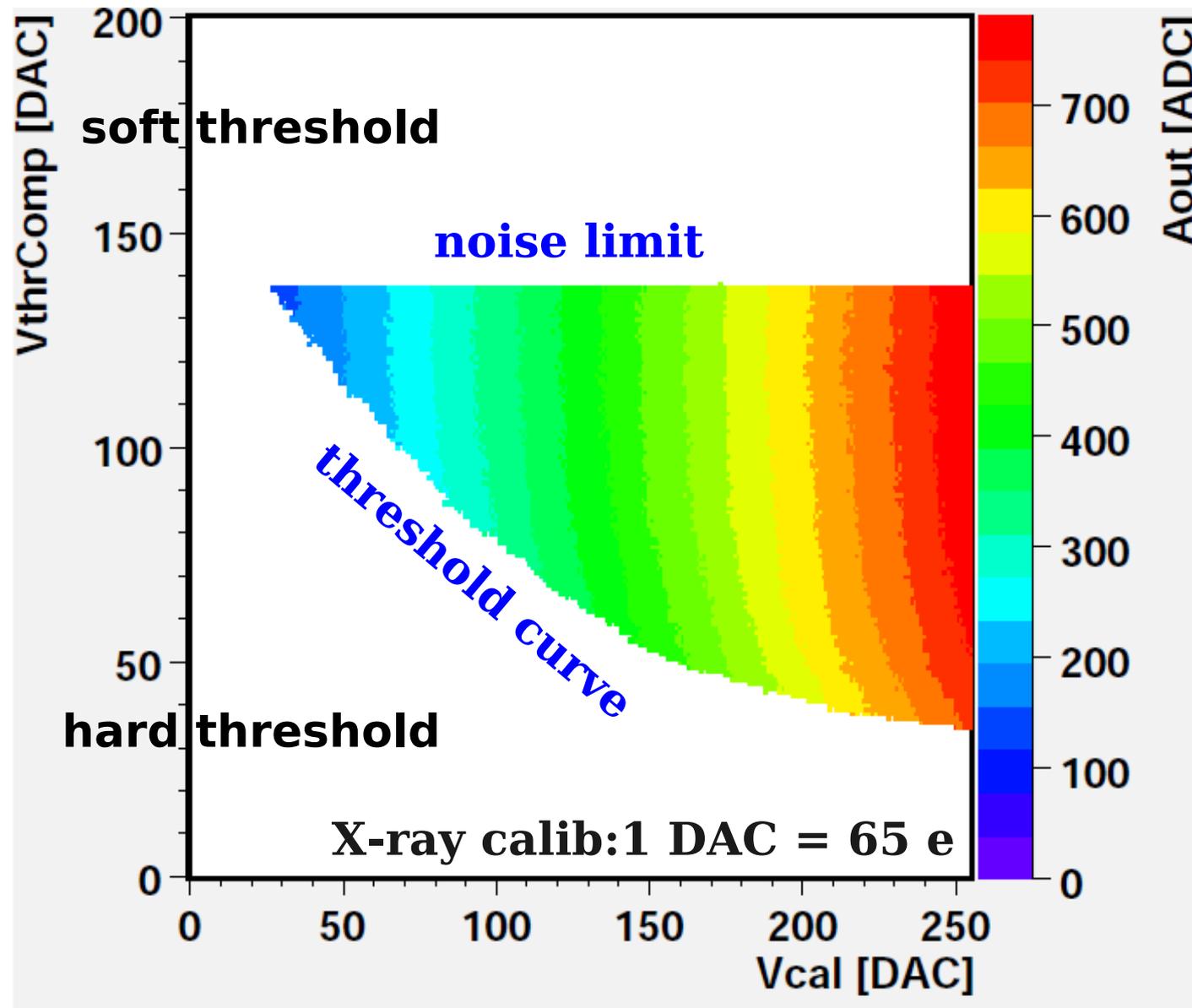
Linear range vs Vsf



- One pixel
- Analog pulse height vs calibrate amplitude and source follower voltage.
- Best linearity in valley.



Comparator threshold

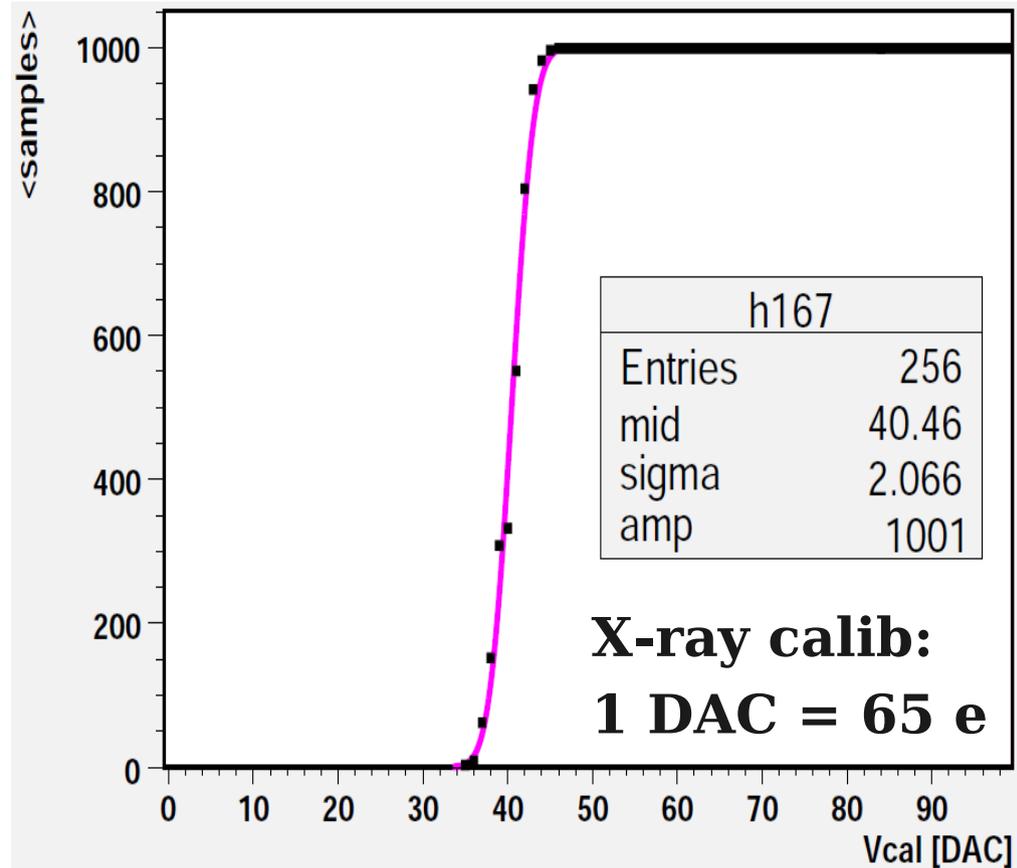


- One pixel
- Analog pulse height vs threshold and calibrate amplitude.
- White region:
 - no signal.
- Colored bands are not vertical:
 - time walk.

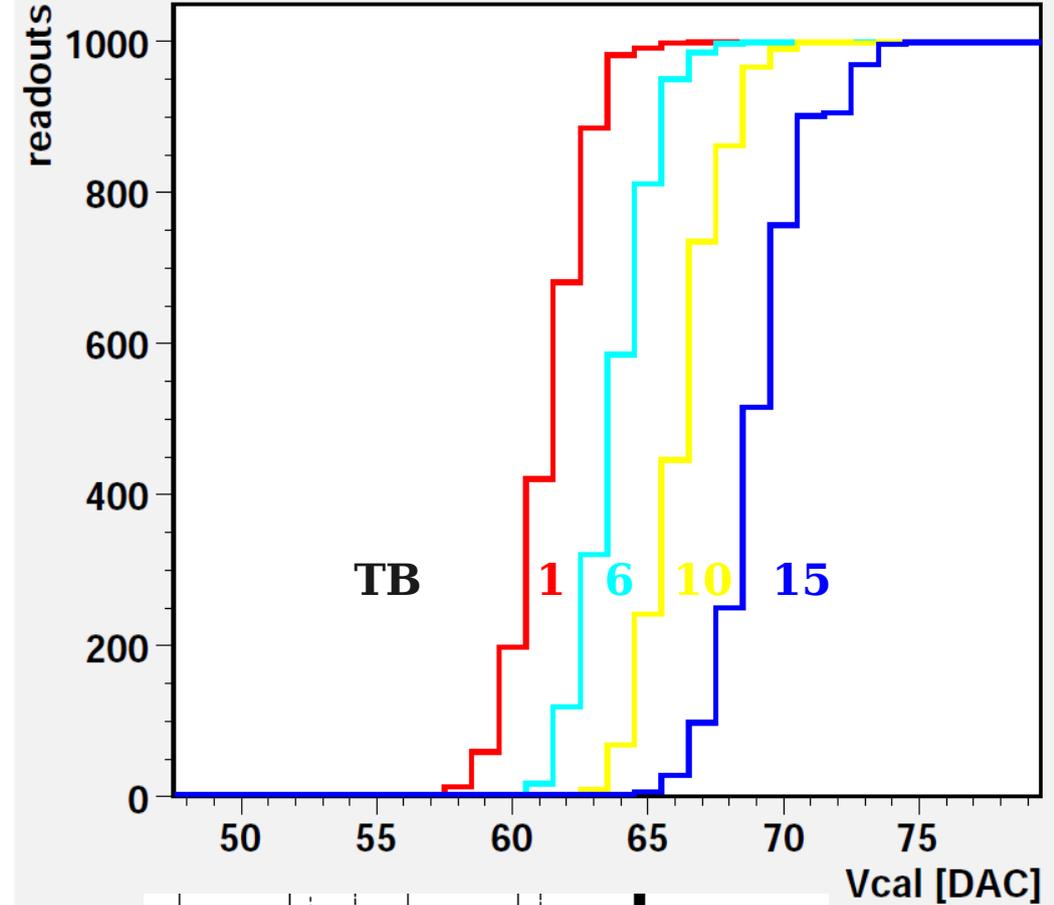
Threshold curve

one pixel

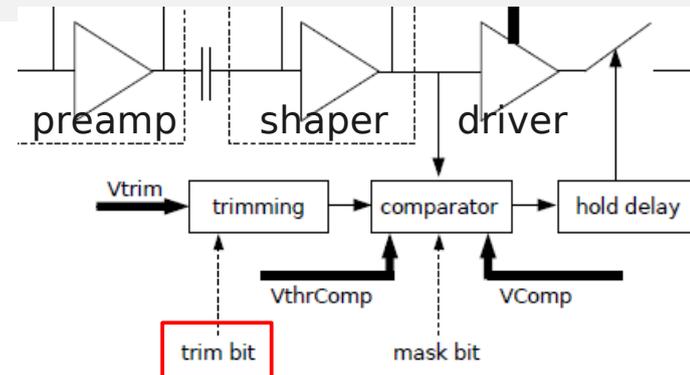
vary test pulse amplitude



vary trim bits

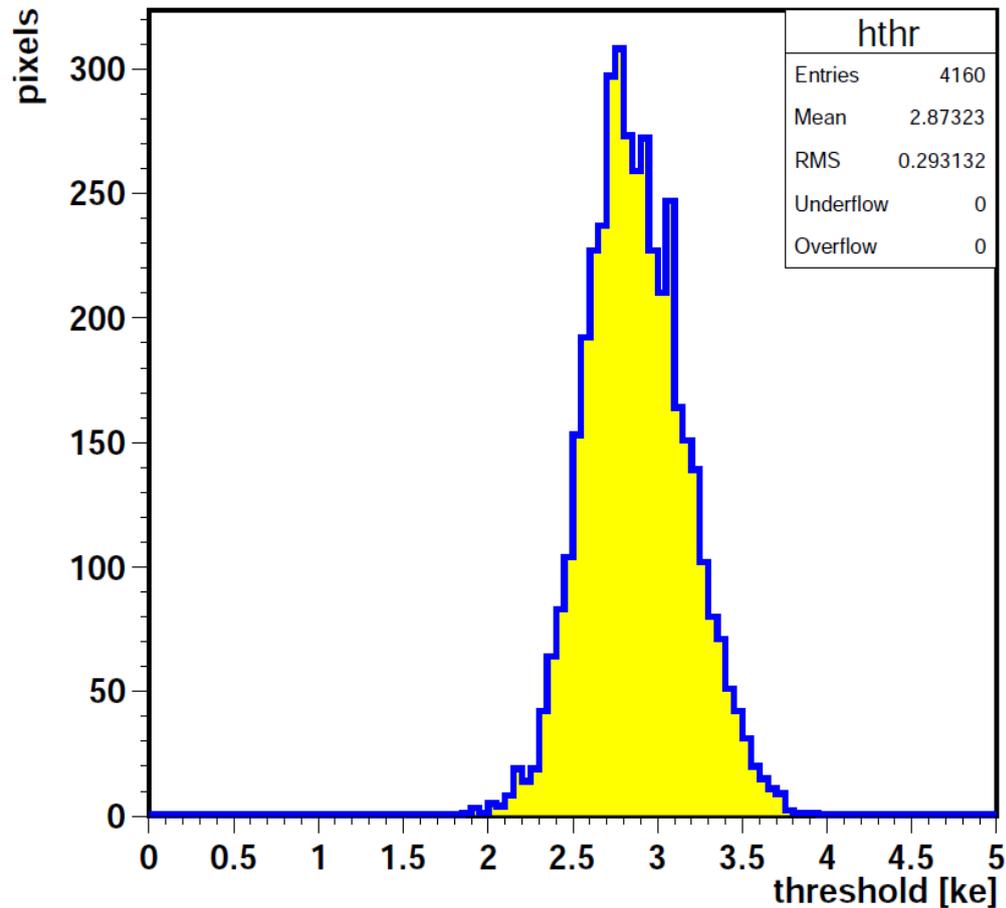


threshold broadened by noise
fit by error function
noise: 130 e



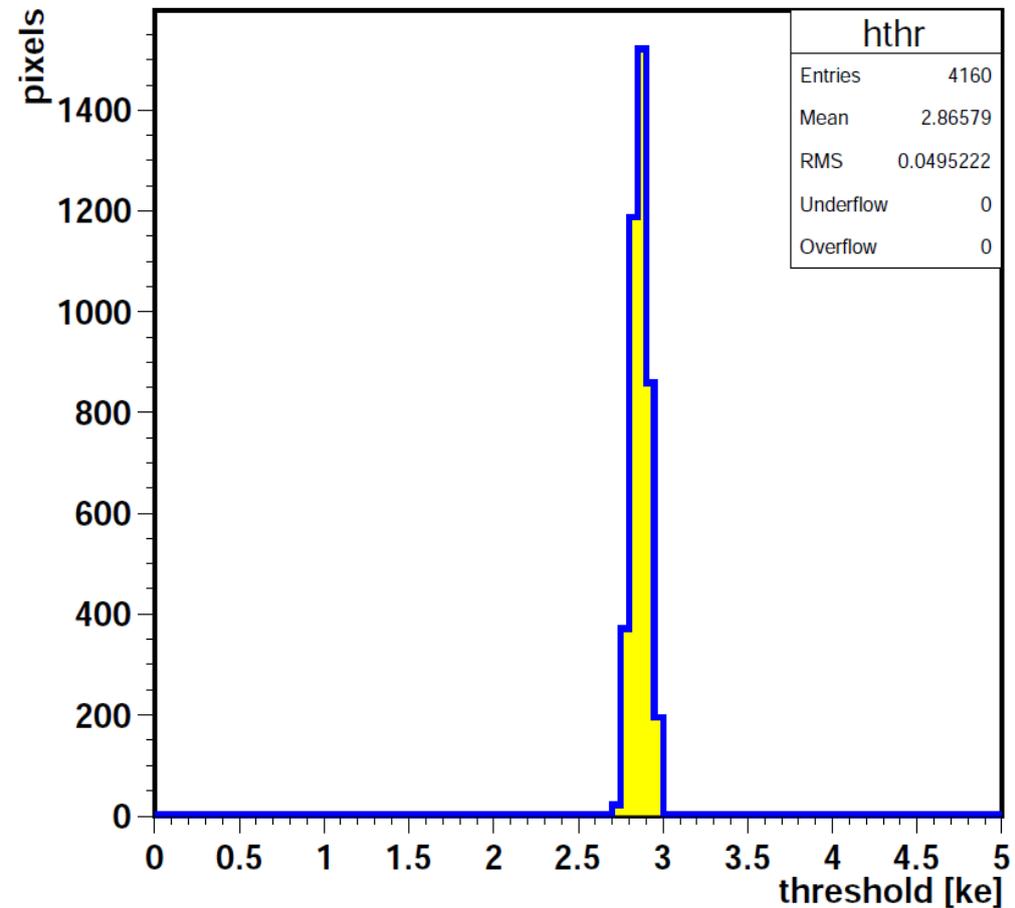
Threshold variation

4160 pixels / cip



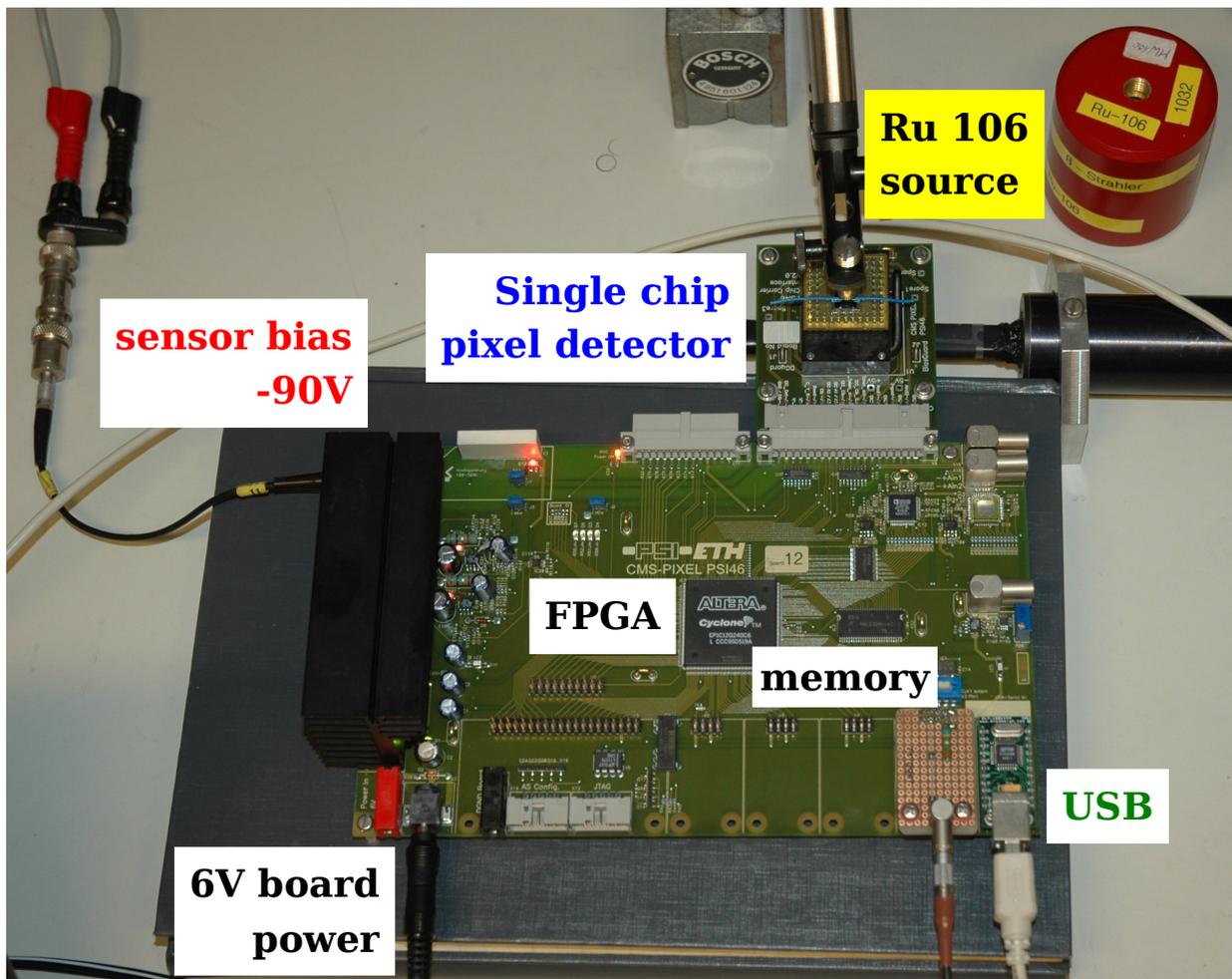
**CMS transistor variations:
threshold spread 290 e**

the same chip, trimmed:



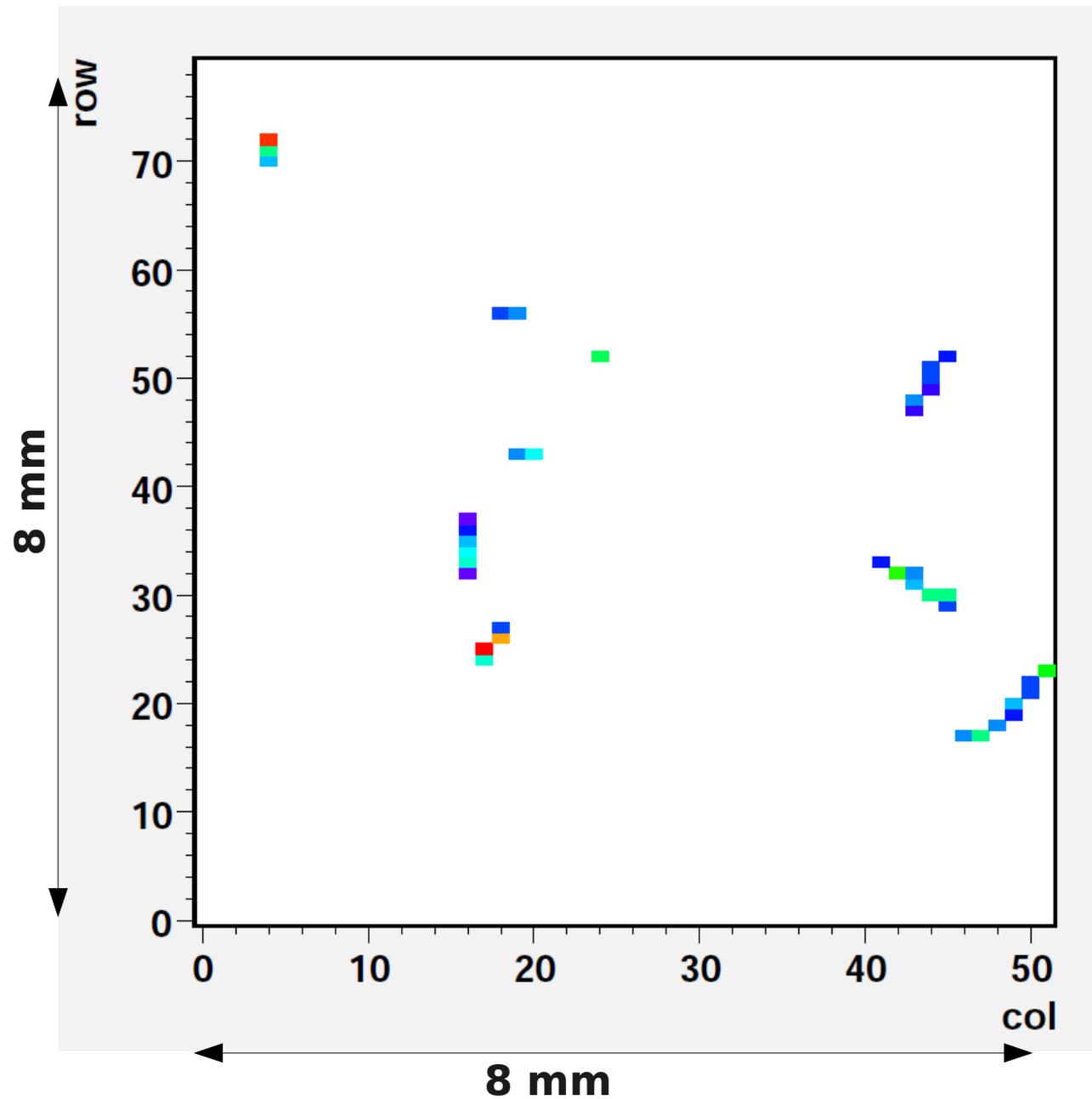
**4-bit DAC trimming:
threshold spread 50 e**

Source test setup



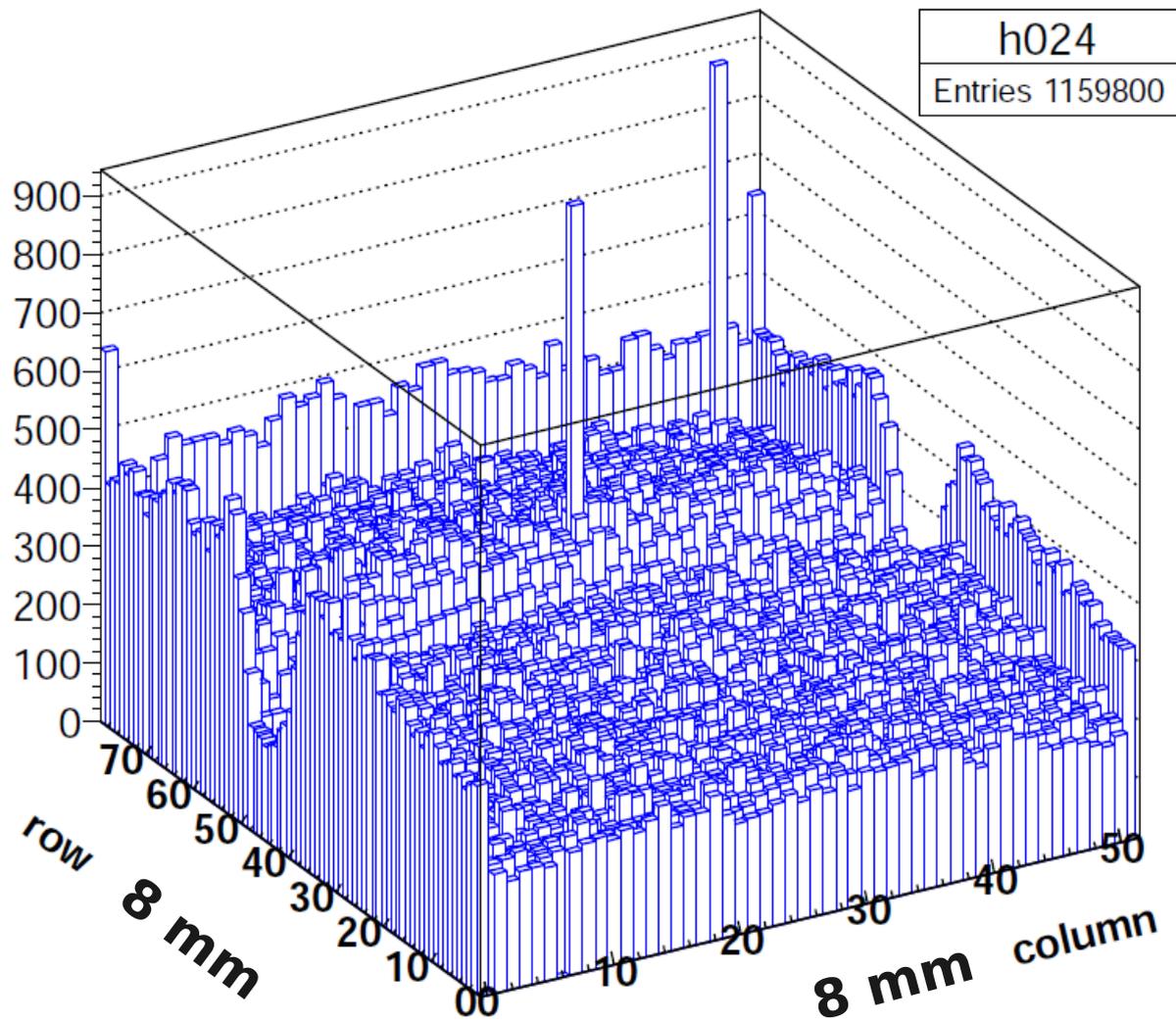
- ^{106}Ru source mounted above the chip:
 - ▶ Activity ~ 14 kHz,
 - ▶ electrons up to 3.5 MeV.
- FPGA:
 - data clock cycle stretched up to 1 ms,
 - trigger,
 - readout,
 - store in memory.
- Final readout by USB.

Source test event display



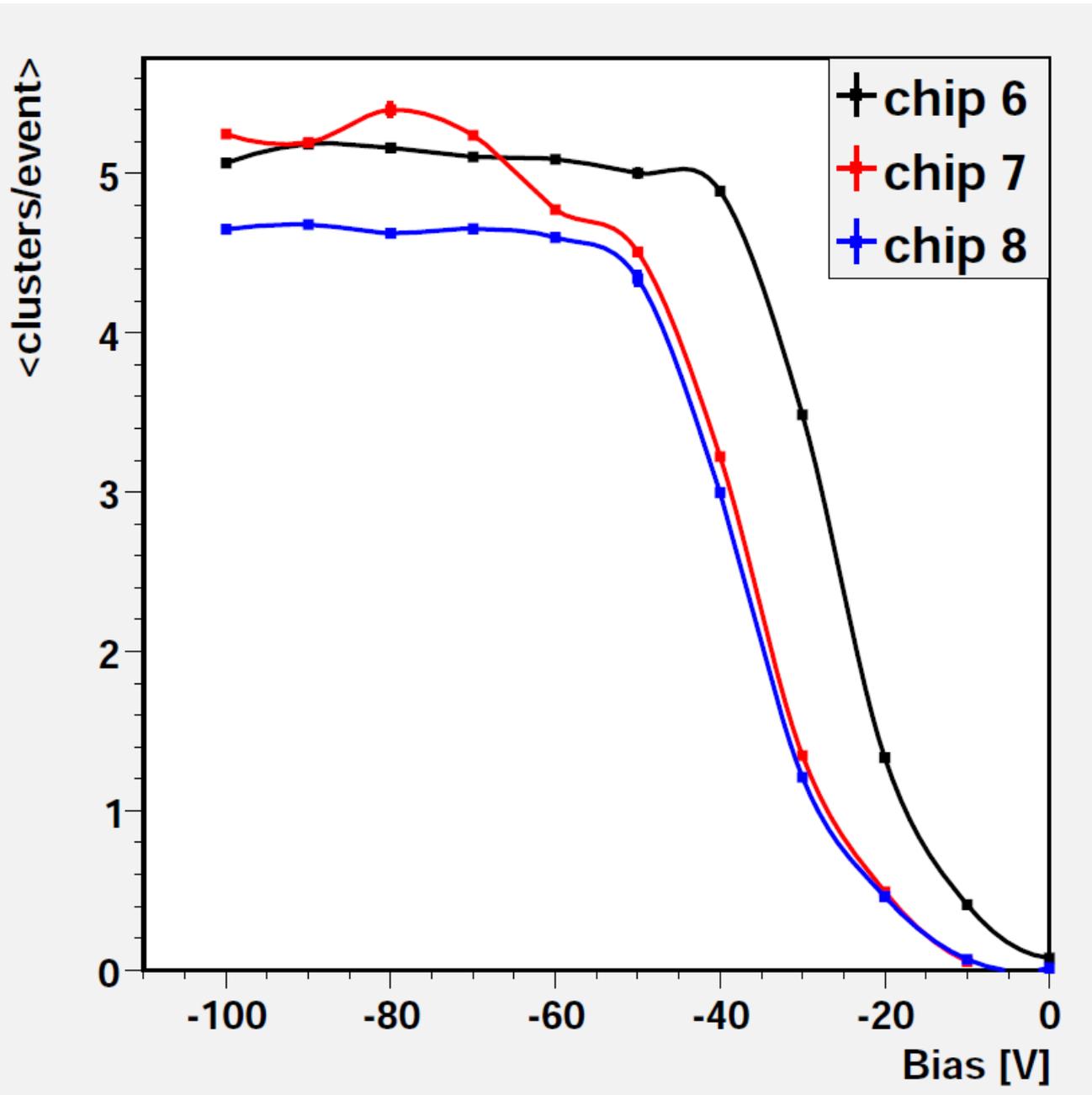
- A single event integrating over 1 ms:
 - ~15 hits per trigger
- Low energy electrons:
 - Scattering in the source holder,
 - wide angles of incidence,
 - large clusters.
 - tracks visible.
- Clusters of pixels identified by software.

hit map



- Ru source, 100s.
- Wire placed across the chip.
- Pixel map (φ - z):
 - shadow of the wire
 - 2 noisy pixels.
 - long and/or wide pixels at 3 edges.

Cluster multiplicity vs. bias voltage



- Ru106 source.
- All scans with:
 - Internal trigger
 - Clock stretch 1 ms
 - 10s run for one V_{bias} value
- Cluster efficiency saturates below -50 V.
- Plateau variation:
 - Source position,
 - Thresholds.

DESY II

<http://adweb.desy.de/~testbeam/>



**DESY II
(positrons)**

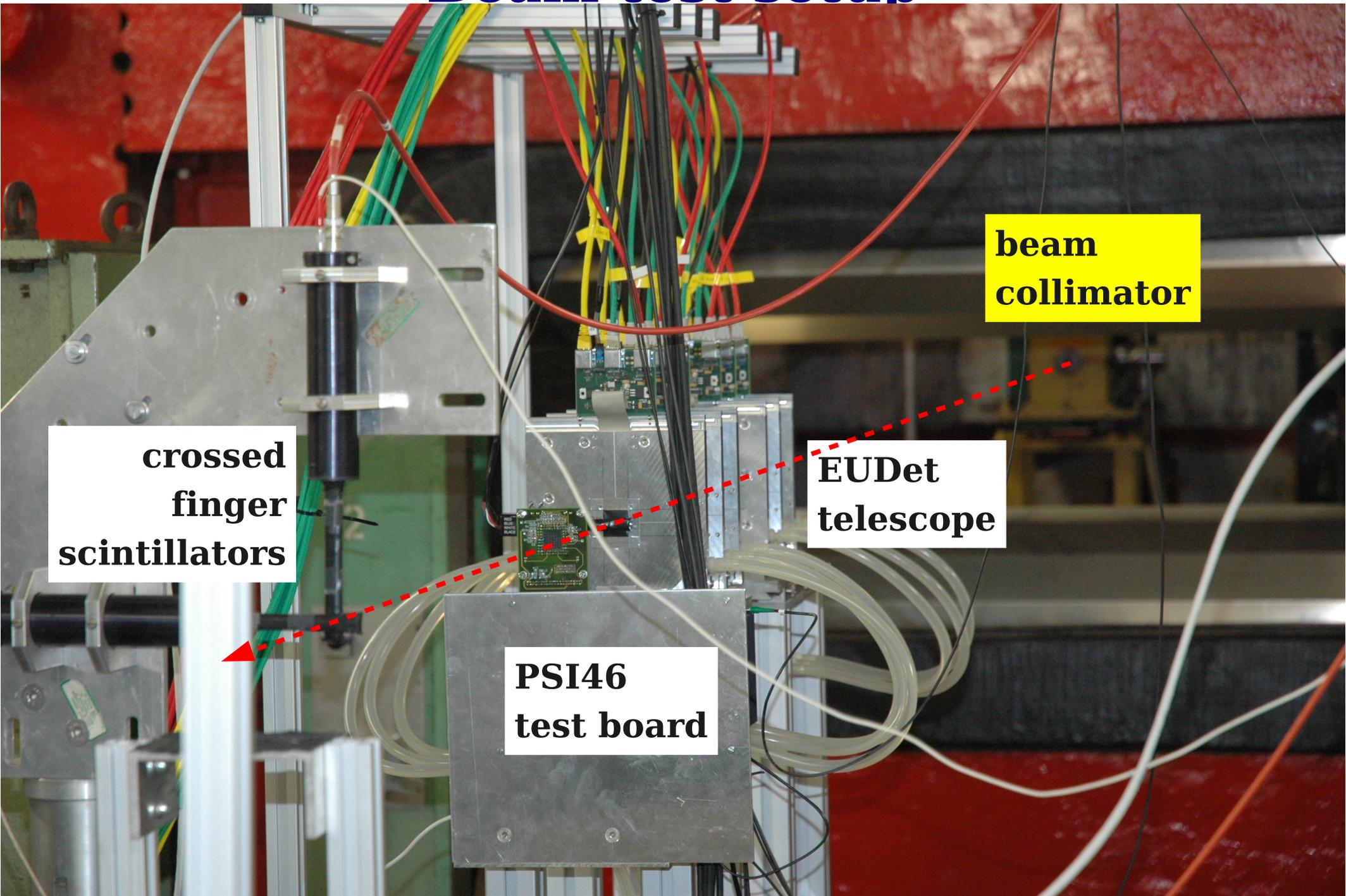
24

22

**DESY III
(protons)**

21

Beam test setup



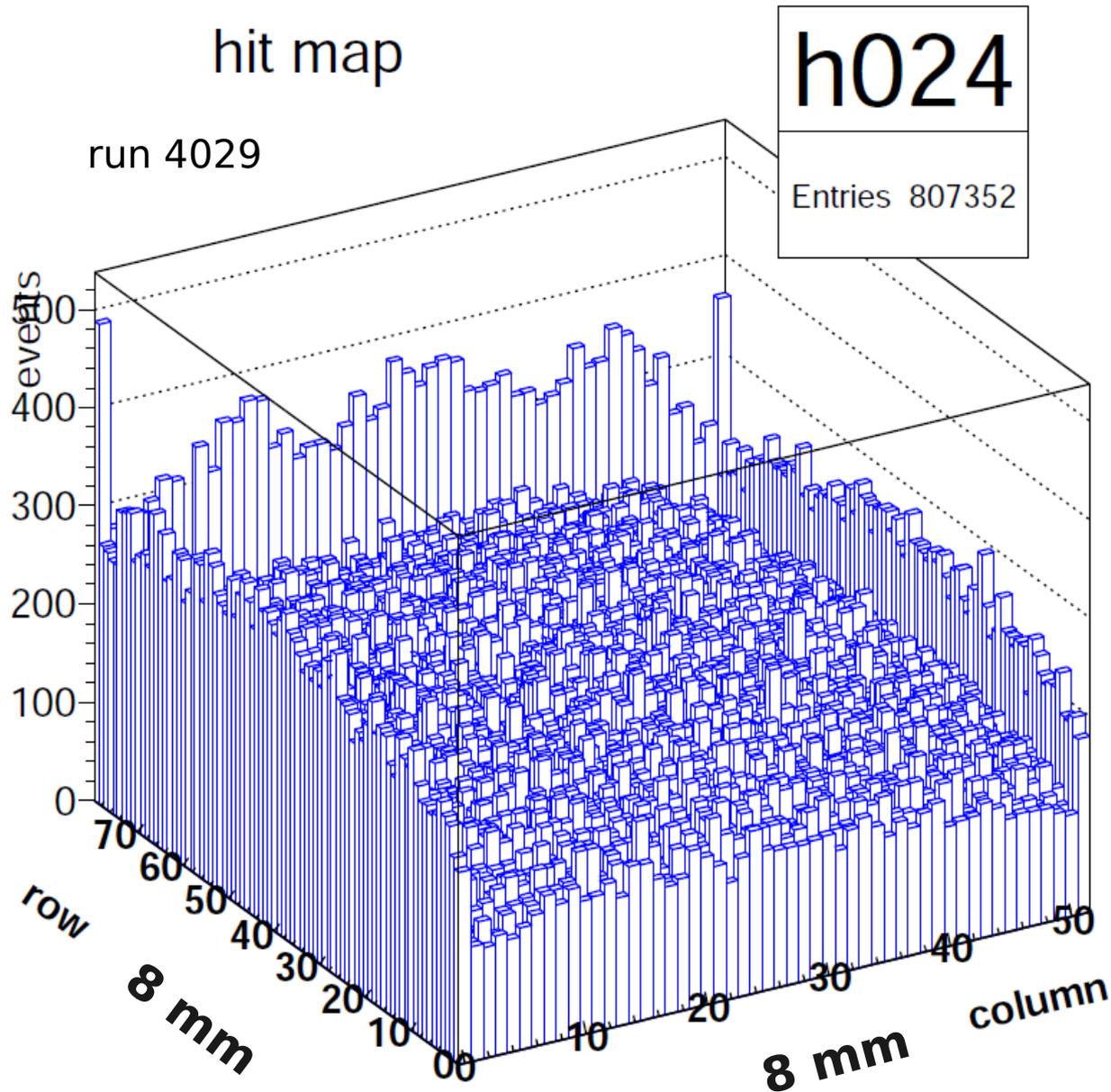
**beam
collimator**

**crossed
finger
scintillators**

**EUDet
telescope**

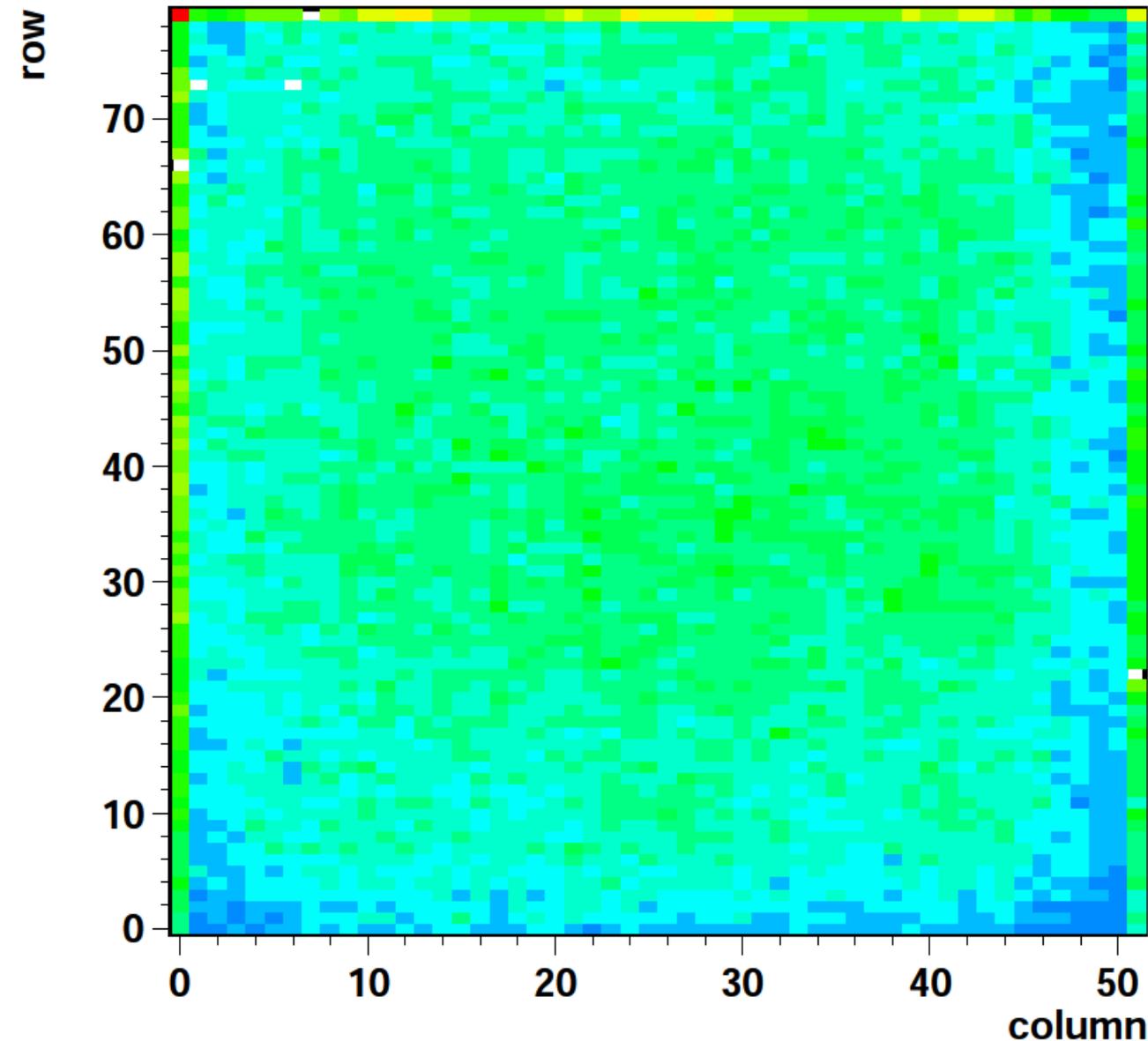
**PSI46
test board**

Pixel hit map



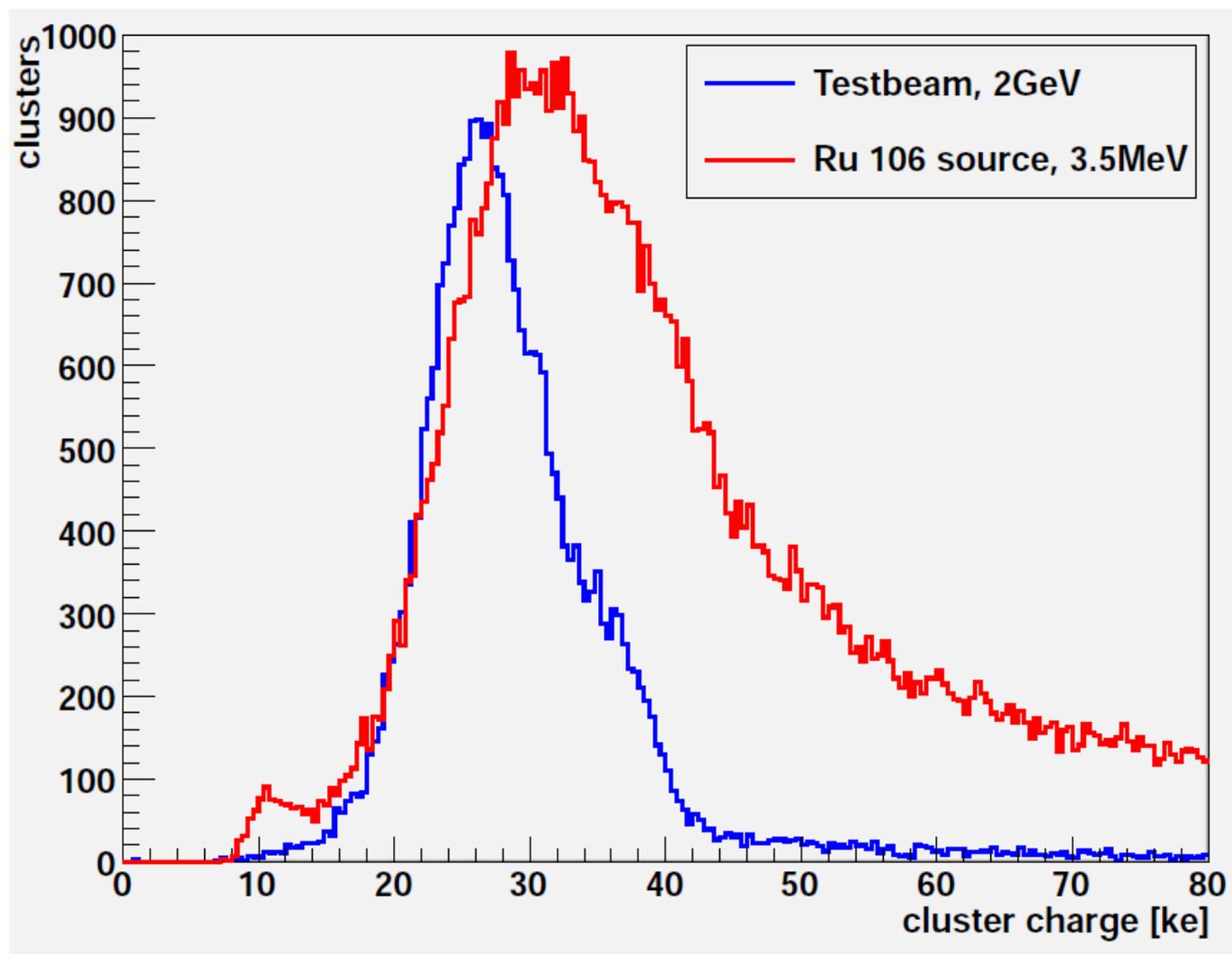
- 2 GeV e^+ beam.
- After space and time alignment:
 - ▶ 4 kHz coincidence rate
 - ▶ Fill test board memory: 60MB in 3.5 min.
 - ▶ USB transfer takes another ~ 2 min.
- One chip fully illuminated.
- Border pixels have double size and rate
- Corner pixels have quadruple size and rate

Pixel hit map



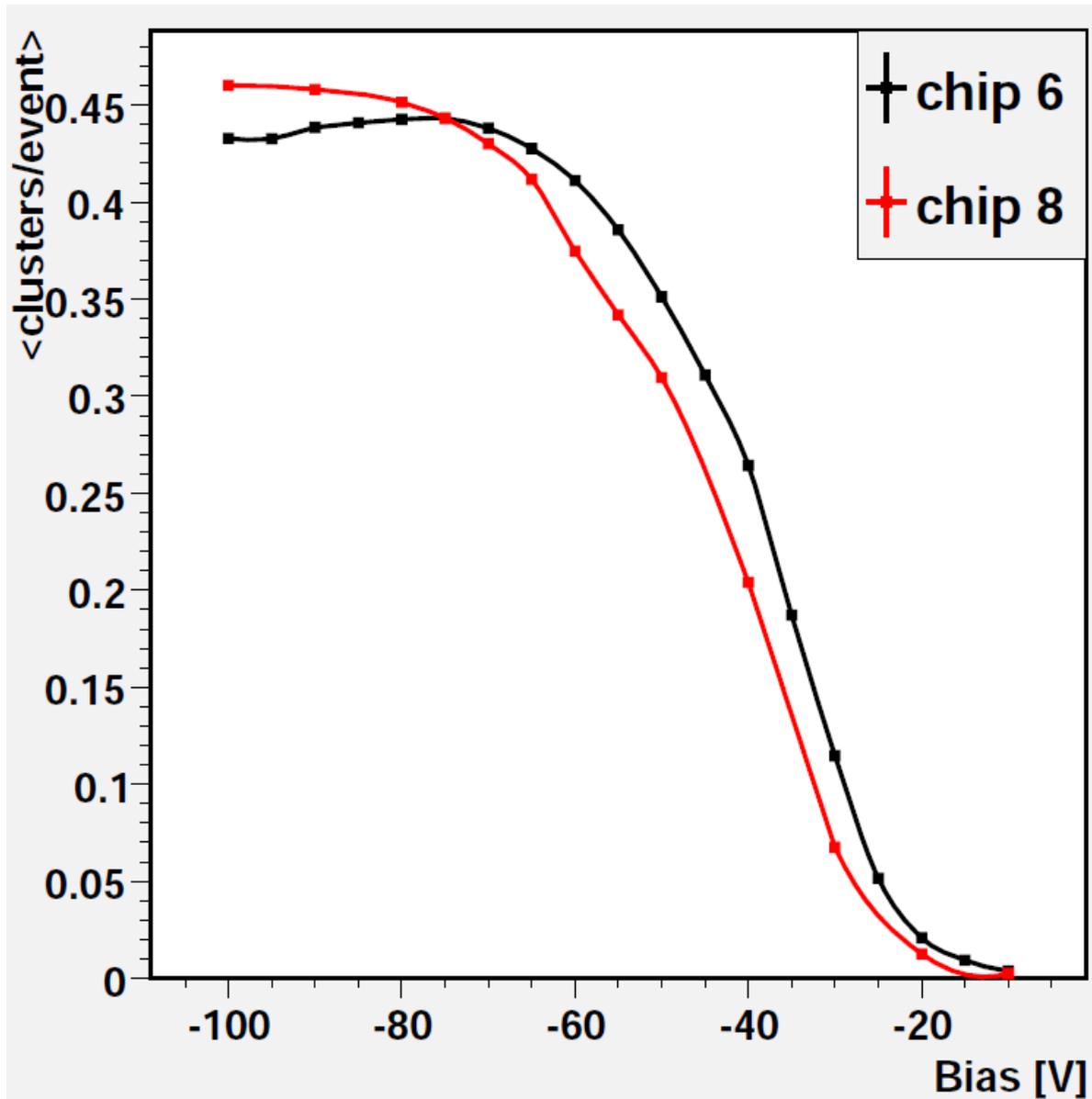
- the same run
- a few dead pixels
- non-uniformity:
 - ▶ beam profile,
 - ▶ misalignment between sensor and scintillator,
 - ▶ limited trigger region ($\sim 1 \text{ cm}^2$) just enough to cover $0.8 \times 0.8 \text{ cm}^2$ chip.

Cluster charge: Ru source vs beam



- Chip 8, -90V bias, Vthr 100
- 2 GeV e+ test beam:
 - ▶ Minimum ionizing particles
- Ru 106 source:
 - ▶ long tail of stronger ionizing electrons (not fully relativistic).

Cluster multiplicity vs. bias voltage



- 2 GeV e^+ beam.
- Cluster efficiency saturates below -80 V:
 - ▶ Need more bias voltage to reach full efficiency for minimum ionizing particles.

Project time line

- Produce assembly tools since 2010
- Develop assembly procedures 2011
- Develop testing and calibration procedures 2011
- Bump bonding tests 2010-2011
- Decide on bump bonding technique end 2011
- Assembly and test procedures established 2012
- Receive all components for series production 2013
- Module assembly and calibration 2013-2015
- 4th layer assembly and test mid 2015
- Full system test at CERN 2015-2016
- Ready for installation in CMS mid 2016

Work packages in D-CMS

4th layer: 512 modules + 100 spares + 88 rejects = 700

task	quantity	DESY	HH	Ka	Ac
sensors I-V	700		350	350	
bare module test	700	350		350	
bond TBM to HDI	700	350		350	
glue HDI to sensor	700		350	350	
bond ROCs to HDI	400k	200k		200k	
module testing	700	350		350	
cold calibration	700	350			350
X-ray calibration	700		350		350
layer assembly	1	1			
layer system test	1	1			
DC-DC converters	~2000				all

People at DESY and Uni Hamburg 2011



- DESY:
 - ▶ Günter Eckerlin, deputy CMS group leader, DPix coordinator
 - ▶ Daniel Pitzl, pixel upgrade project leader
 - ▶ Carsten Niebuhr, Doris Eckstein, staff
 - ▶ Maria Aldaya, Jan Olzem, Alexey Petrukhin, Hanno Perrey, postdocs
 - ▶ Karsten Hansen, Jan Hampe, staff FEC
 - ▶ Carsten Muhl, Holger Maser, engineering
- Uni Hamburg:
 - ▶ Peter Schleper, professor
 - ▶ Georg Steinbrück, staff
 - ▶ Thomas Hermanns, postdoc
 - ▶ Lutz Berger, technical support



Summary

- The present CMS pixel detector is working very well and is an essential tool for track reconstruction and vertexing.
- The LHC luminosity is expected to exceed 10^{34} /cm²s in this decade:
 - ▶ the present pixel readout chip will become inefficient.
 - ▶ at least the inner pixel layer has to be exchanged after 250 fb⁻¹.
- A 4-layer replacement with a new readout chip has further benefits:
 - ▶ Better resolution, efficiency, and purity for pixel-based tracking,
 - ▶ Reduced material in the tracker volume with CO₂ cooling, low mass design, services moved out of the tracking region.
- The German CMS institutes have been asked to contribute:
 - ▶ Design optimization and physics evaluation,
 - ▶ module assembly and testing,
 - ▶ DC-DC converter development and production.
- Preparations are underway.

Acknowledgments summer 2011

- **Aleksander Gajos**
 - 2011 summer student from Cracow
- **Fedor Glazov**
 - 2011 summer intern
- **Beat Meier (PSI), Thomas Weiler (KIT), Tilman Rohe (PSI):**
 - for code and advice.
- **Ulrich Koetz (DESY):**
 - for lab space, NIM crate and modules, oscilloscope
- **Wladimir Hain (DESY):**
 - for the source
- **Carsten Muhl (DESY):**
 - for the source holder
- **Torsten Külper (DESY):**
 - for the TTL trigger adapter
- **Ingrid Gregor (DESY, test beam coordinator):**
 - for instructions and test beam hospitality
- **Norbert Meyners (DESY, test beam coordinator):**
 - for help with collimator and wire target
- **Samuel Ghazaryan (DESY, test beam support):**
 - for help with moving system and rate monitor
- **Holger Maser (DESY):**
 - for the test board support frame
- **Erika Garutti (DESY and Uni HH):**
 - for the finger scintillator and PM
- **DESY Machine Group:**
 - for the steady test beam

Backup slides

The CMS Tracker upgrade

– DESY contributions –

April 15, 2010

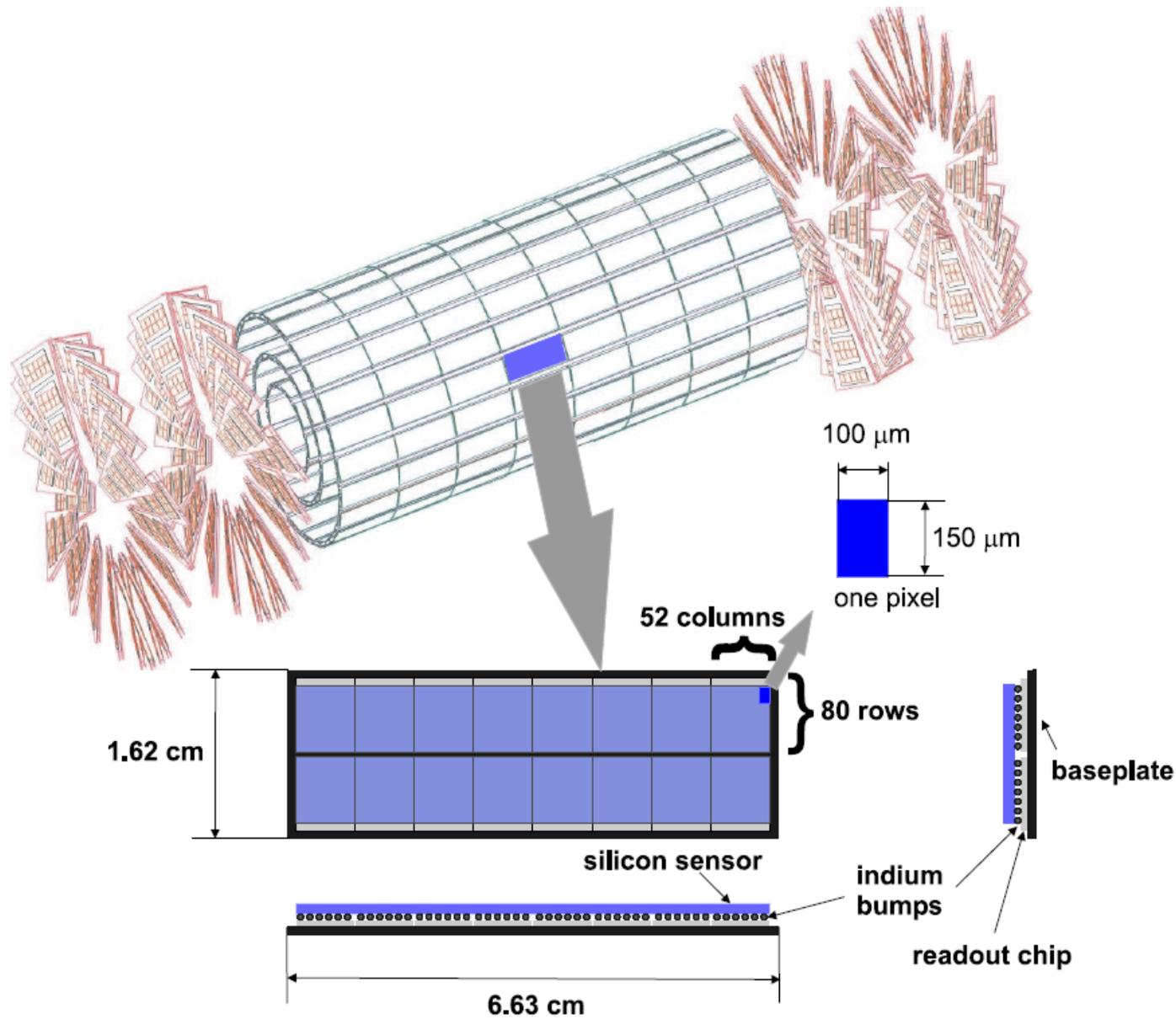
The DESY CMS Group

Abstract

A 4-layer low mass replacement of the CMS Barrel Pixel detector is planned for the middle of the decade. DESY is interested to contribute to the module production, in collaboration with the universities in Hamburg, Karlsruhe and Aachen. At a later stage, the entire silicon tracker needs replacement to cope at higher luminosity with increased track density and larger radiation dose while the material budget should be reduced. DESY R&D activities within the Central European Consortium involving the above mentioned universities and those in Barcelona, Louvain and Vilnius are described.

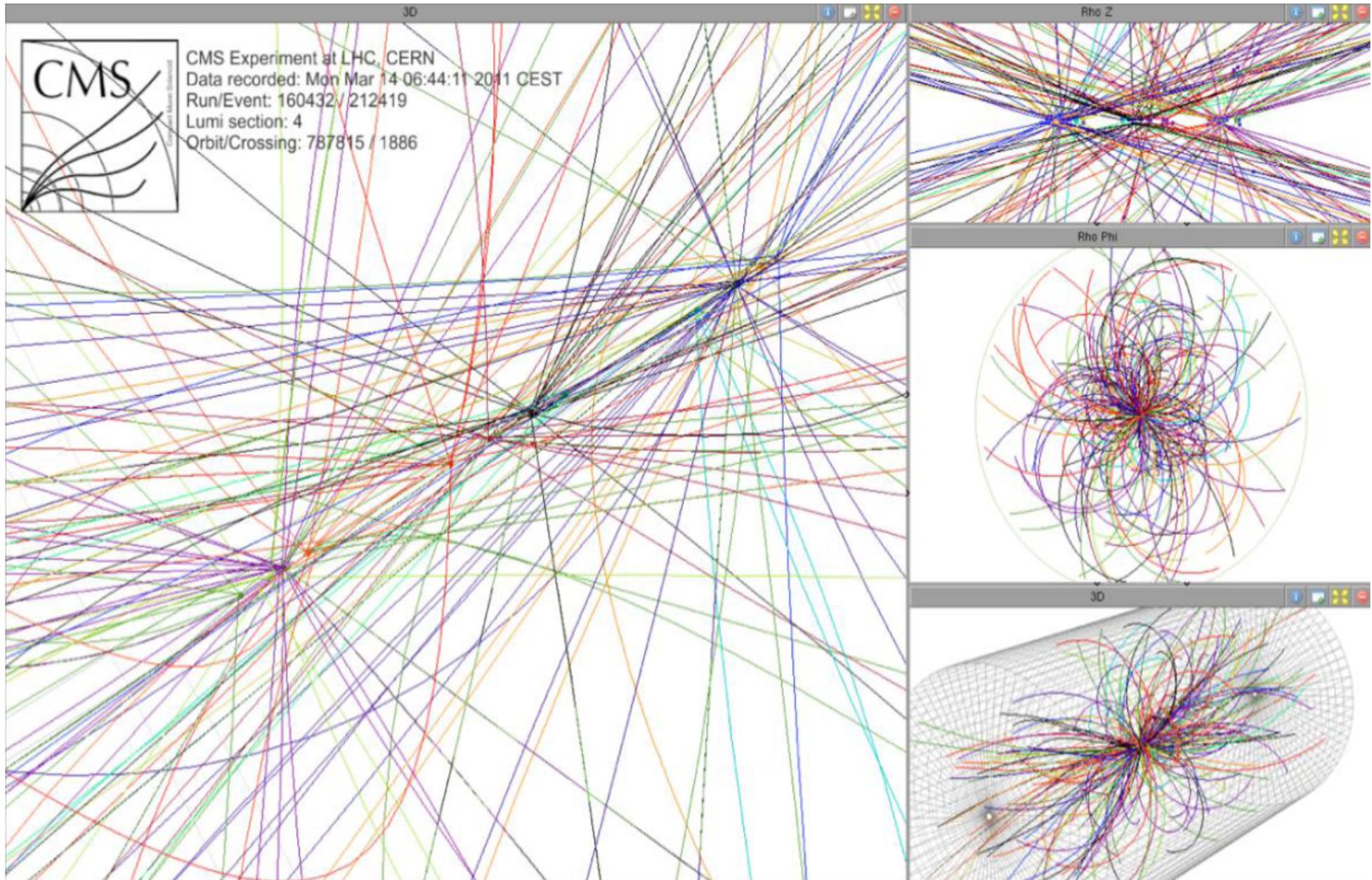
- DESY PRC document for the CMS Tracker upgrade.
- Pixel and Strips
- Hamburg and Zeuthen
- Submitted April 2010.
- Positive recommendation.

CMS Pixel



A. Dorokhov
Uni Zurich
2005

2011 data



Pixel operation in 2010



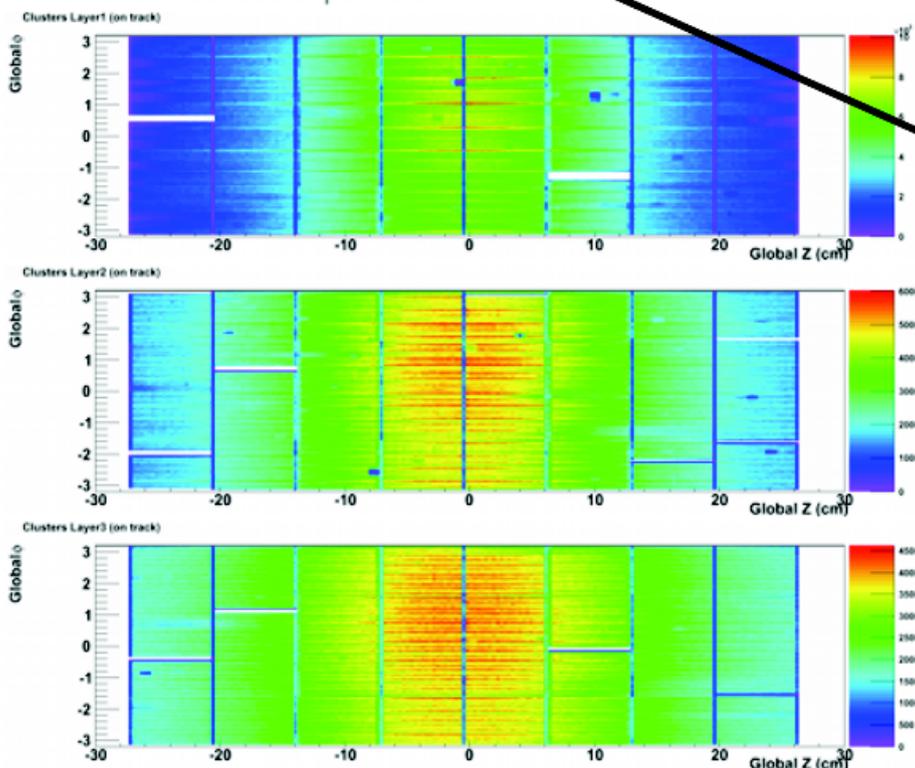
One ROC no-signal:
1/192 (0.5%)
Recoverable.

Too Low signal
amplitude (TBM):
1/192 (0.5%)

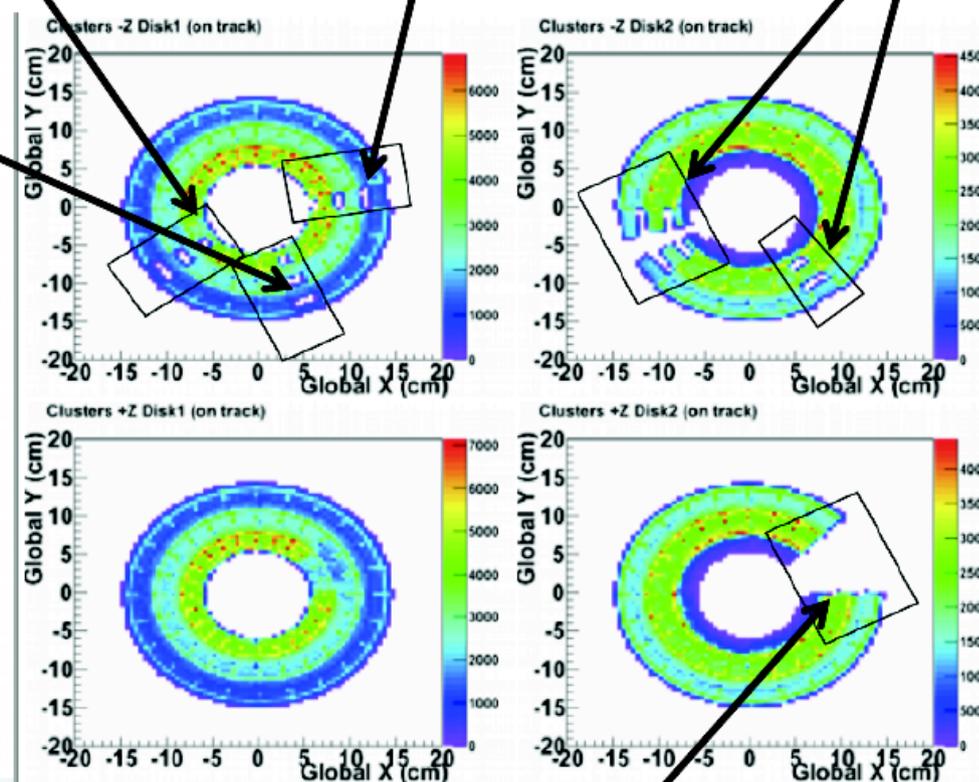
No signal output:
1/192 (0.5%)

Slow panels:
5/192

05 - Barrel OnTrack cluster positions



06 - Endcap OnTrack cluster positions

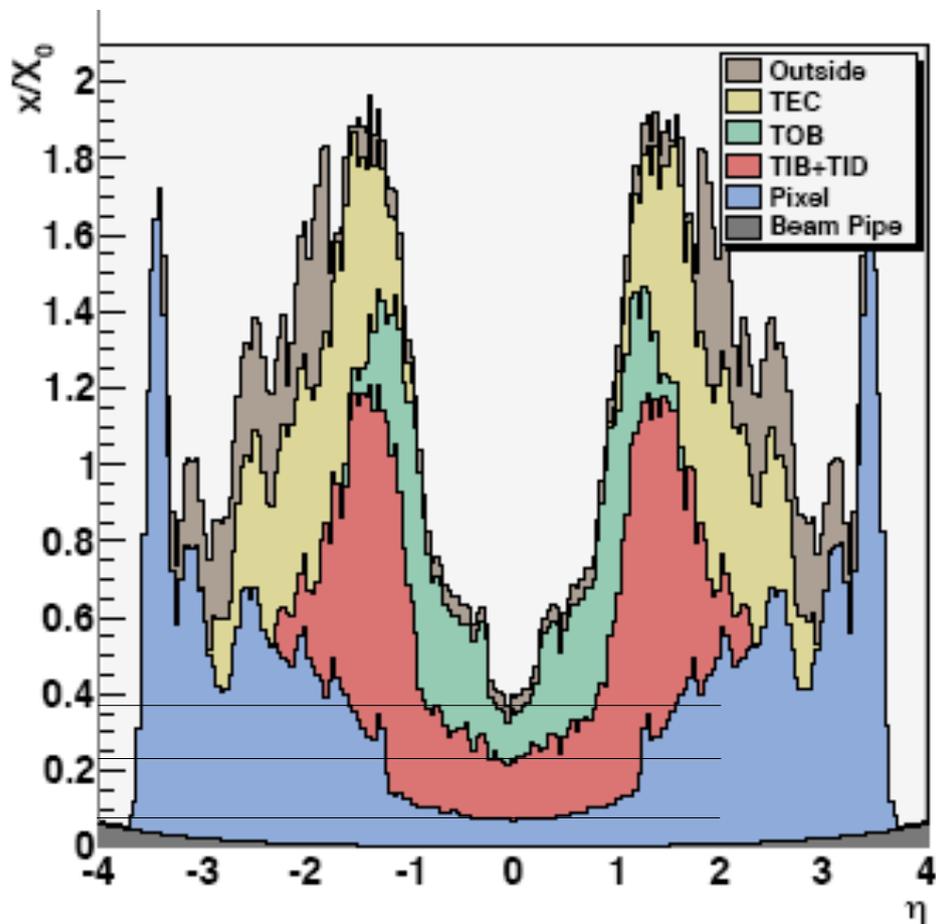


No I2C communication with
AOH: 6/192 (3.1%)

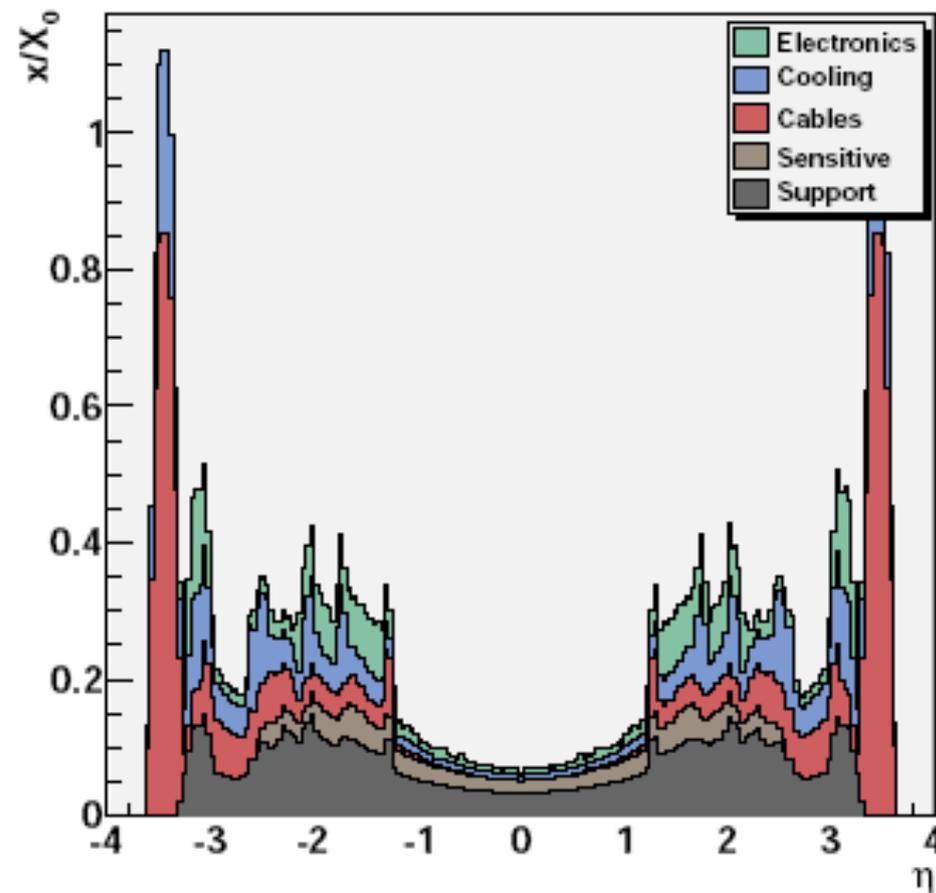


CMS tracker material

All trackers

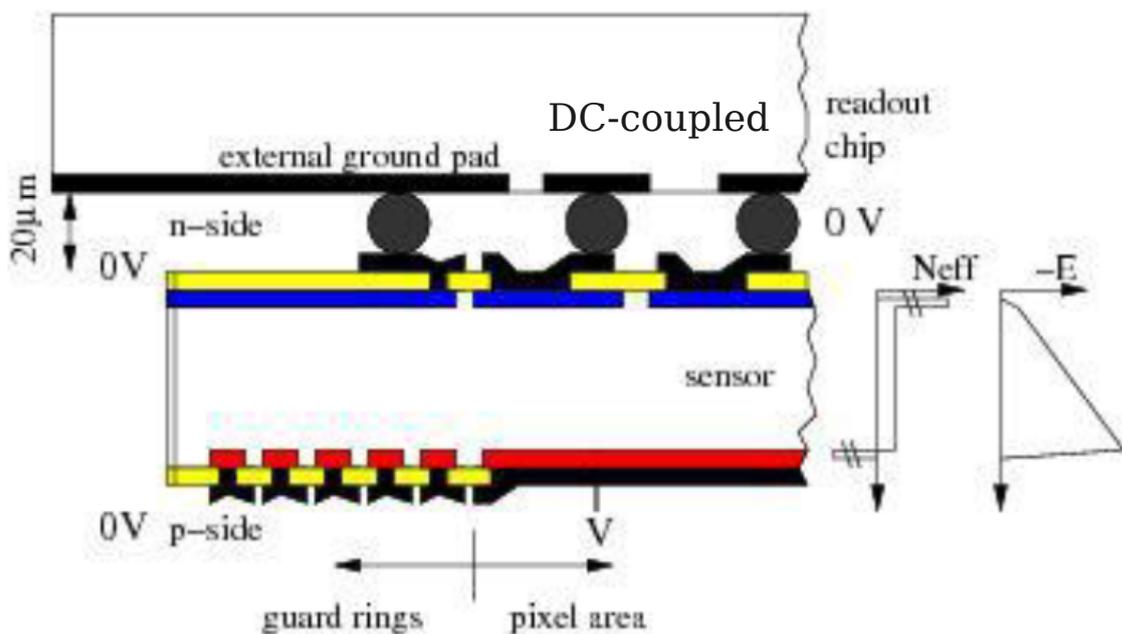


Barrel pixel

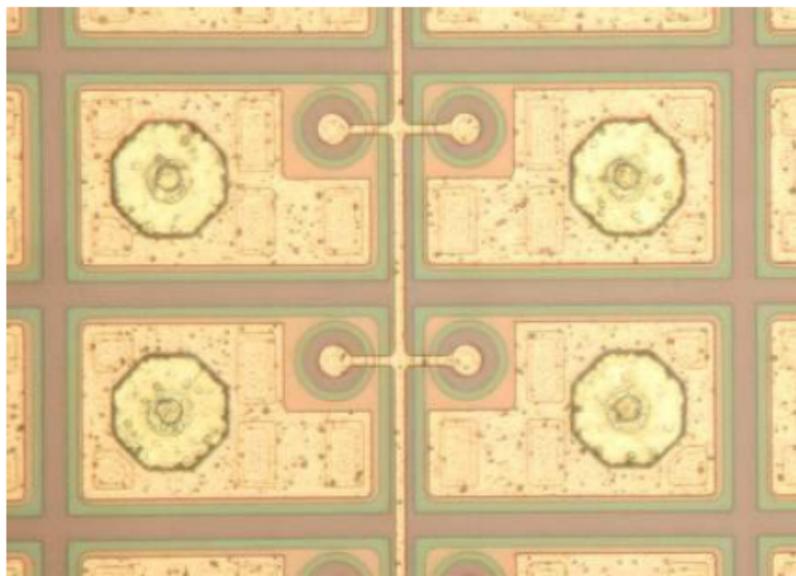


Upgrade:
factor 2 less in center
factor 4 less in endcaps

Pixel sensors



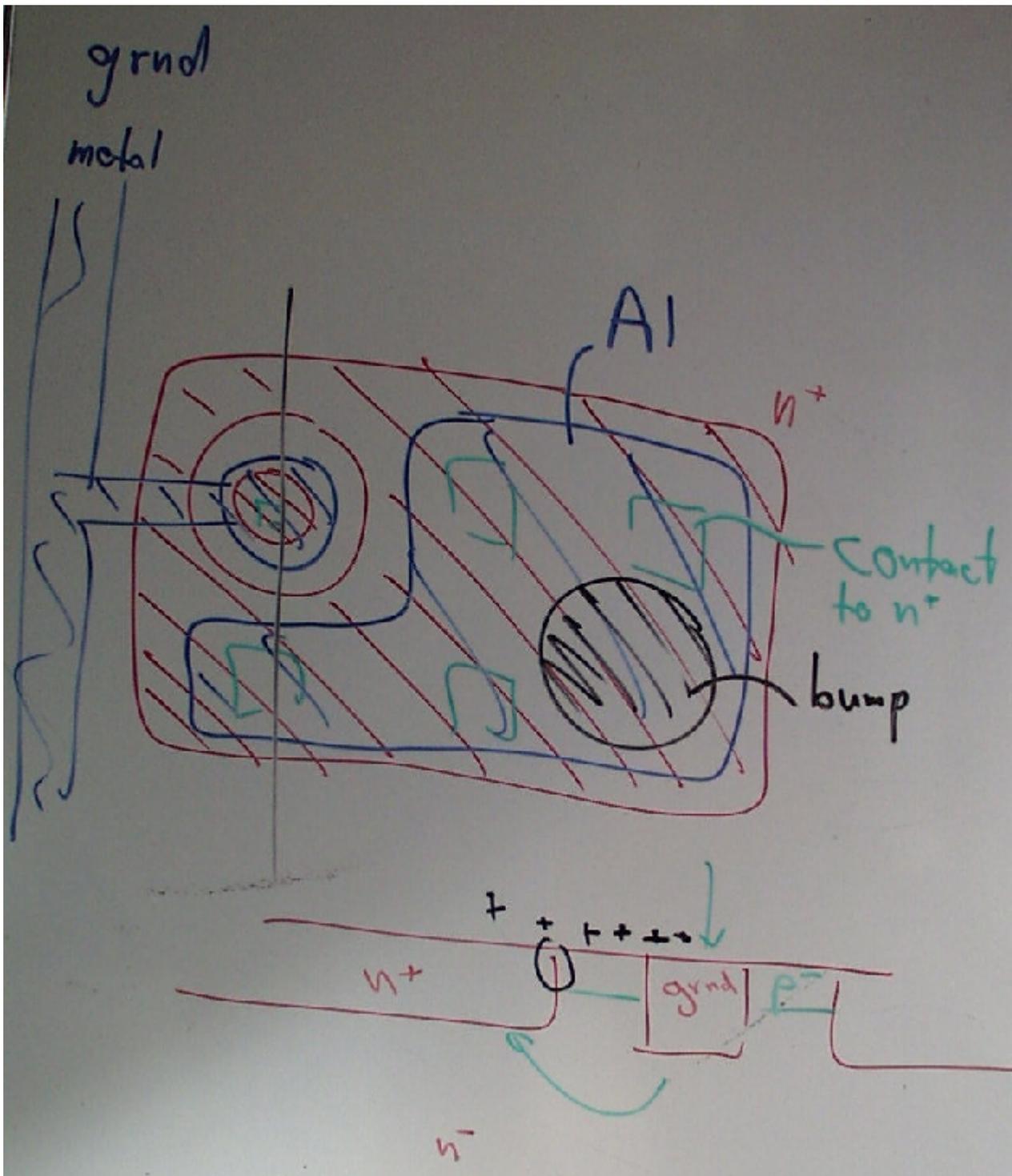
- Planar sensors, CiS Erfurt.
- 111-oxygenated float zone.
- n-in-n, p-spray insulation.
- collecting faster electrons:
 - ▶ larger Lorentz angle,
 - ▶ less trapping.
- pn-junction on back side (initially):
 - ▶ edges at ground,
 - ▶ double sided processing.



100 μm (rφ) x 150 μm (z)

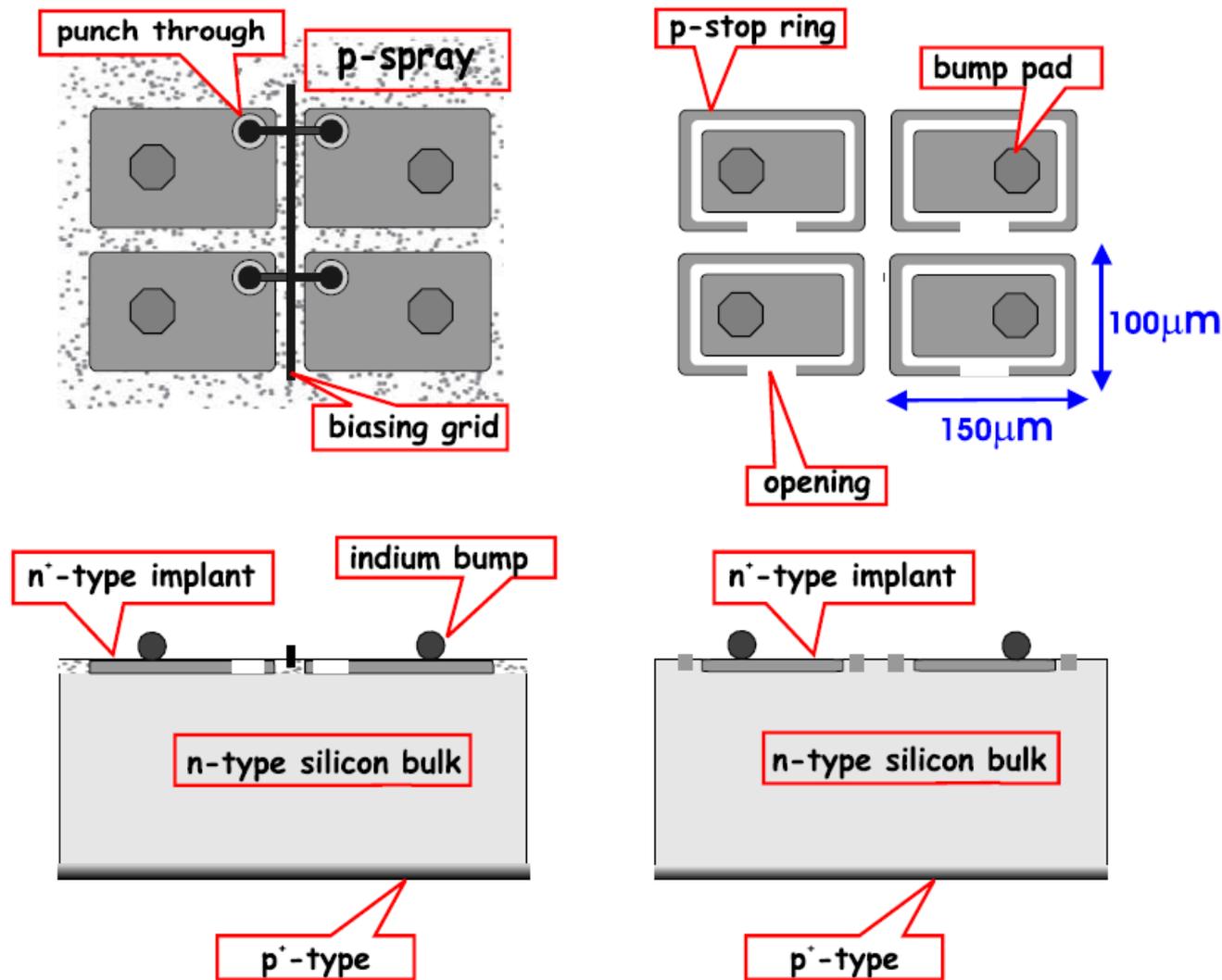
Grounding grid for testing
before bump bonding

1 pixel



T. Rohe, PSI
2.11.2009
pic73.jpg

CMS Barrel and Forward pixel sensors



A. Dorokhov
Uni Zurich
2005

Figure 1.11. Sensor designs for the CMS barrel detector (left) and end-caps (right).

CMS Barrel pixel sensor design

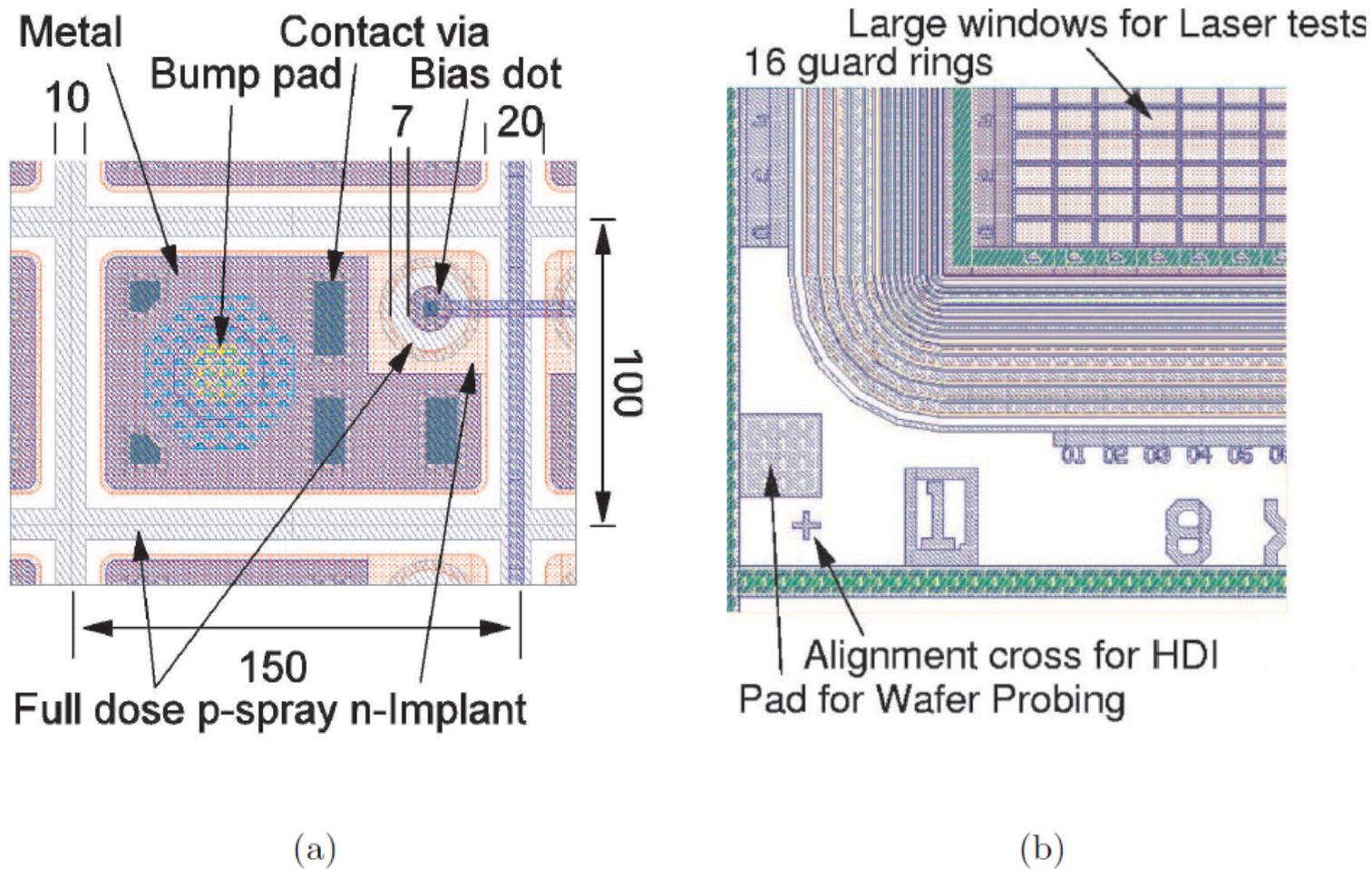
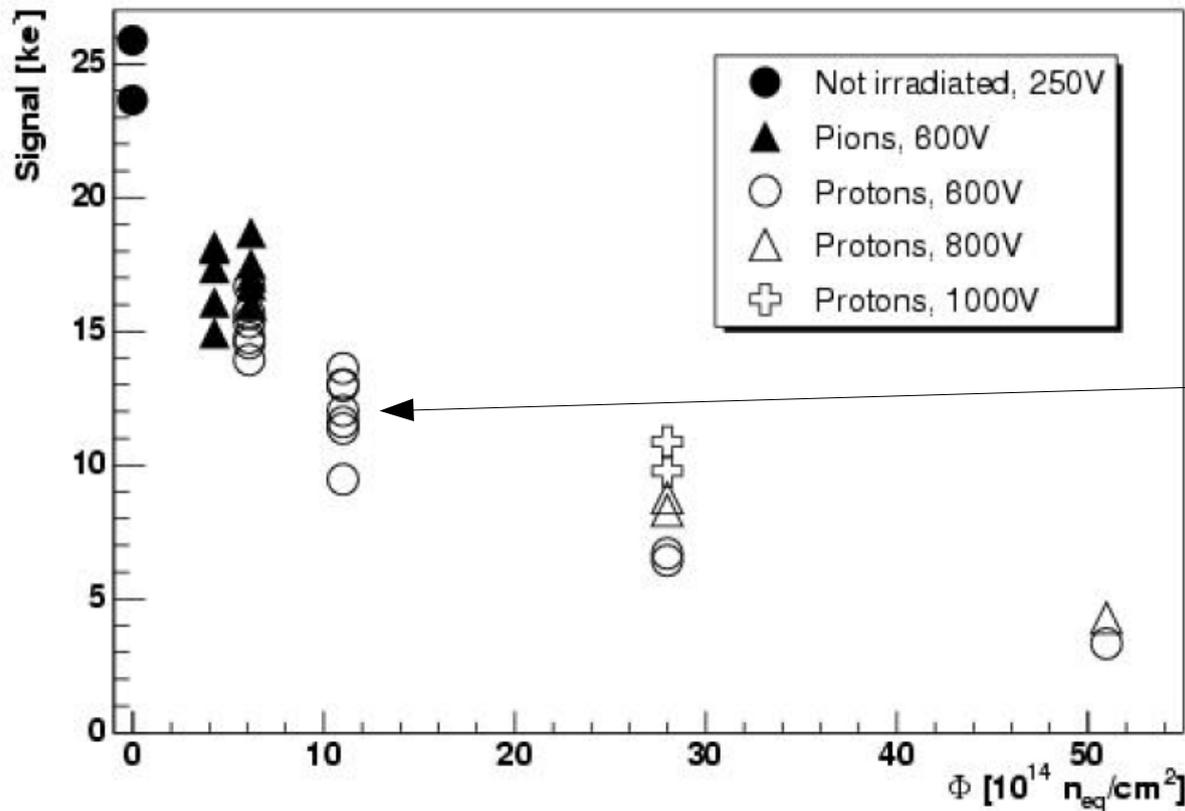


Figure 1.12. The masks for the p-spray design. Left: The mask layout of the pixel side. The distances are in μm . Right: The mask layout of the backside.

Sensor radiation damage

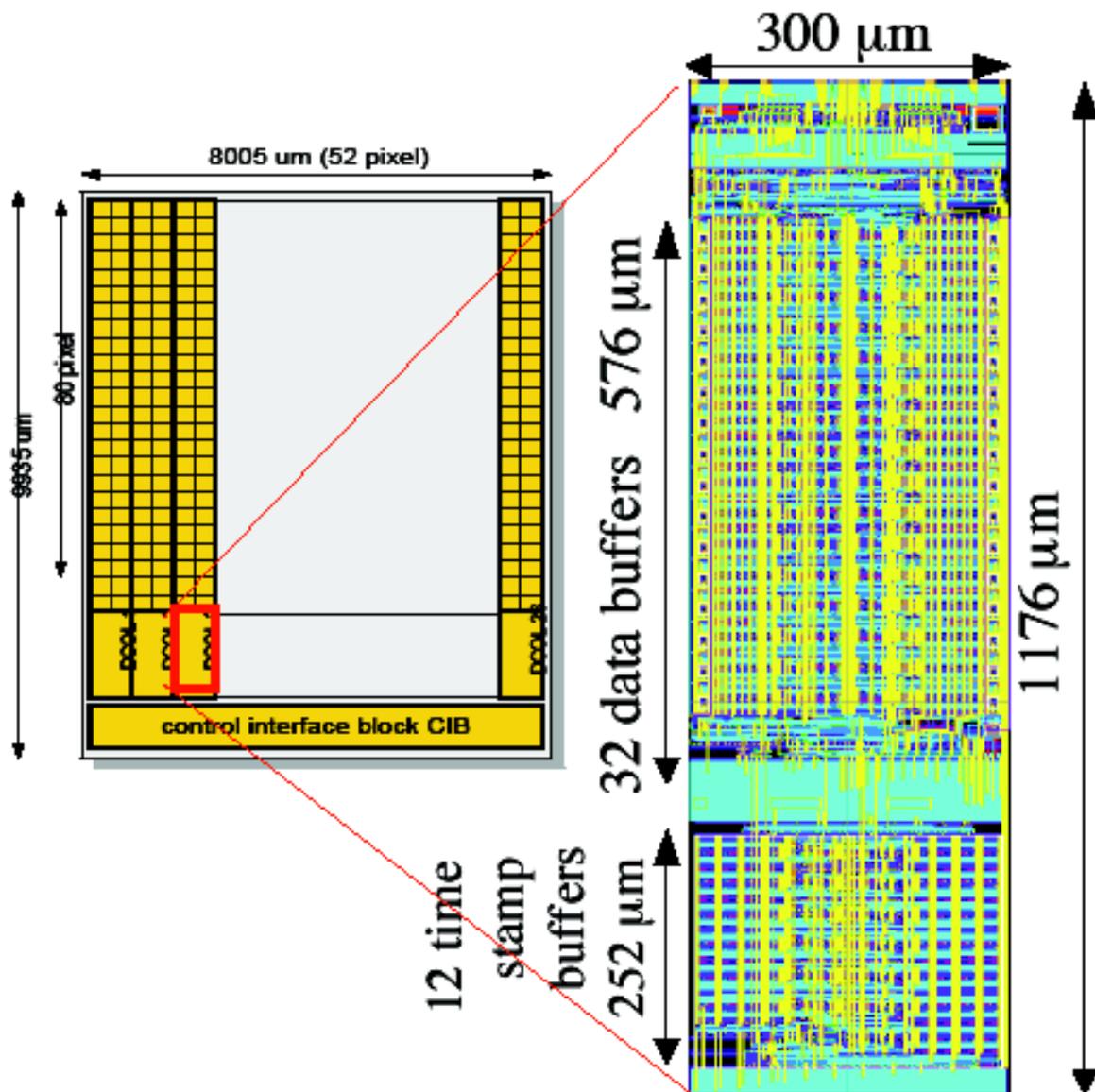
Signal collection in CMS pixel sensors



T. Rohe, Pixel2010

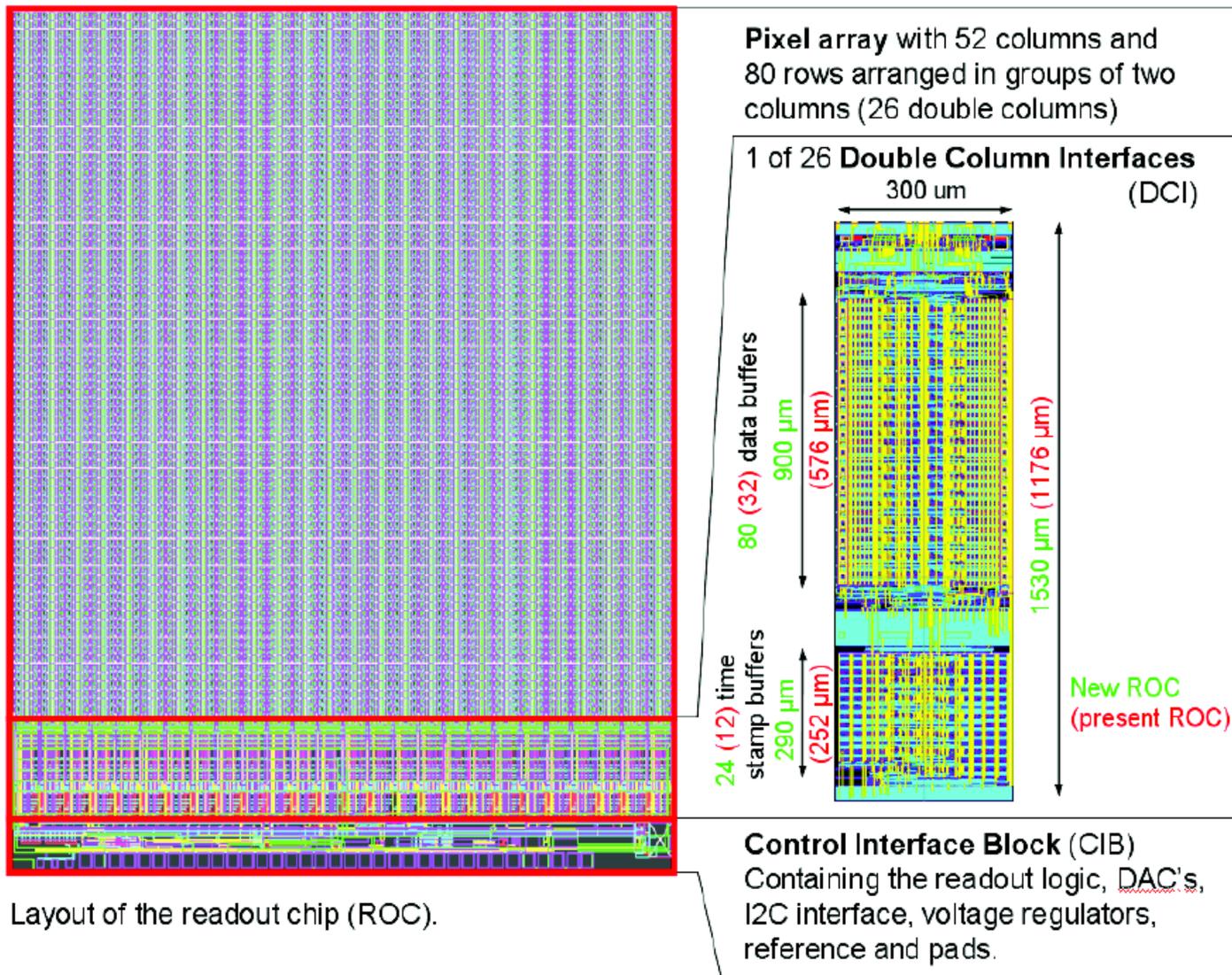
- Inner barrel layer:
 - ▶ $70 \text{ fb}^{-1} = 4 \cdot 10^{14} \text{ n/cm}^2$
 - ▶ $250 \text{ fb}^{-1} = 13 \cdot 10^{14} \text{ n/cm}^2$
- 50% signal loss after 250 fb-1.
- Also leads to factor 2 degradation of the hit resolution (less charge sharing and Lorentz angle)
- Bias voltages above 600 V not possible with the present CMS HV system.
- MCz being considered.

Enlarged on-chip buffer



- **Dominant data loss mechanism \rightarrow larger buffers needed**
- **Data loss simulations performed**
 - Data buffer from 32 to 80 cells
 - Timestamp buffer from 12 to 24 cells
- **Simple scaling would increase ROC size by $>1.1\text{mm}$**
- **800 μm more space allowed with new detector mechanics**
 - \rightarrow Need more compact buffer layout

Enlarged on-chip buffer



B. Meier (PSI)
Nov 2010
JINST 6 C01011

Figure 1. Layout of the existing readout chip (ROC). A detailed view of the double column interface with size of the new chip compared to the old one.

Karlsruhe and Aachen

- Karlsruhe:
 - ▶ Ulrich Husemann, Thomas Müller, professors
 - ▶ Marc Weber, professor, director IPE
 - ▶ Thomas Blank, staff AVT
 - ▶ Michele Caselle, Alexander Dierlamm, Frank Hartmann, Thomas Weiler, staff
 - ▶ Stefan Heindl, phd student
 - ▶ Tobias Barvich, technical support
- Aachen:
 - ▶ Lutz Feld, professor
 - ▶ Katja Klein, staff
 - ▶ Jan Sammet, phd student
 - ▶ technical support



Switzerland

- Roland Horisberger, Wolfram Erdmann, Hans-Christian Kästli, Tilman Rohe, Beat Meier, Silvan Streuli, Willi Bertl, Urs Langenegger, Danek Kotlinski
- Rainer Wallny, Andrei Starodumov
- Peter Robmann

